Shanghai Fudan Microelectronics Group Company Limited

FM25LQ64I3

64M-BIT SERIAL FLASH MEMORY

Datasheet

Nov.2025

Trademarks

1. Description

The FM25LQ64I3 is a 64M-bit (8M-byte) Serial Flash memory, with advanced write protection mechanisms. The FM25LQ64I3 supports the standard Serial Peripheral Interface (SPI), Dual/Quad I/O as well as 2-clock instruction cycle Quad Peripheral Interface (QPI). The FM25LQ64I3 also supports DTR read. They are ideal for code shadowing to RAM, executing code directly from Dual/Quad SPI (XIP) and storing voice, text and data.

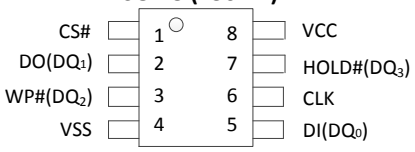
The FM25LQ64I3 can be programmed 1 to 256 bytes at a time, using the Page Program instruction. It is designed to allow either single Sector/Block at a time or full chip erase operation. The FM25LQ64I3 can be configured to protect part of the memory as the software protected mode. The device can sustain a minimum of 100K program/erase cycles on each sector or block.

2. Features

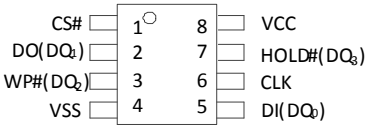
- **64Mbit of Flash memory**
  - 2048 uniform sectors with 4K-byte each
  - 128 uniform blocks with 64K-byte each or
  - 256 uniform blocks with 32K-byte each
  - 256 bytes per programmable page
- **Supply Voltage: 1.65V to 2.0V**
- **Serial Interface**
  - Standard SPI:CLK,CS#,DI,DO,WP#, HOLD#
  - Dual SPI: CLK,CS#,DQ_0,DQ_1,WP#,HOLD#
  - Quad SPI: CLK, CS#, DQ_0, DQ_1, DQ_2, DQ_3
  - QPI: CLK, CS#, DQ_0, DQ_1, DQ_2, DQ_3
  - DTR (Double Transfer Rate) Read
  - Continuous READ mode support
  - Program/Erase Suspend and Resume support
  - Allow true XIP (execute in place) operation
- **High Performance**
  - Max FAST_READ clock frequency: 133MHz
  - Max DTR FASTREAD clock frequency: 104MHz
  - Typical page program time: 0.4ms
  - Typical sector erase time: 30ms
  - Typical block erase time: 150/200ms
  - Typical chip erase time: 18s
- **Security**
  - Software and hardware write protection
  - Lockable 3X1024-Byte security Registers
  - 64-Bit Unique ID for each device
  - Discoverable parameters(SFDP) register
- **Industrial Temperature Range**
- **High Reliability**
  - Endurance: 100,000 program/erase cycles
  - Data retention: 20 years
- **Green Package**
  - 8-pin SOP (150mil)
  - 8-pin SOP (208mil)
  - 8-pin TDFN(5×6mm)
  - All Packages are RoHS Compliant and Halogen-free

3. Packaging Type

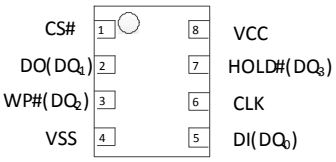
SOP 8 (150mil)



SOP 8 (208mil)



TDFN 8(5X6mm)



4. Pin Configurations

PIN NO.	PIN NAME	I/O	FUNCTION
1	CS#	I	Chip Select Input
2	DO (DQ_1)	I/O	Data Output (Data Input Output 1)(1)
3	WP# (DQ_2)	I/O	Write Protect Input (Data Input Output 2)(2)
4	VSS		Ground
5	DI (DQ_0)	I/O	Data Input (Data Input Output 0)(1)
6	CLK	I	Serial Clock Input
7	HOLD# (DQ_3)	I/O	Hold Input (Data Input Output 3)(2)
8	VCC		Power Supply

Note:
1 DQ_0 and DQ_1 are used for Dual SPI instructions.
2 DQ_0 – DQ_3 are used for Quad SPI and QPI instructions.

5. Block Diagram

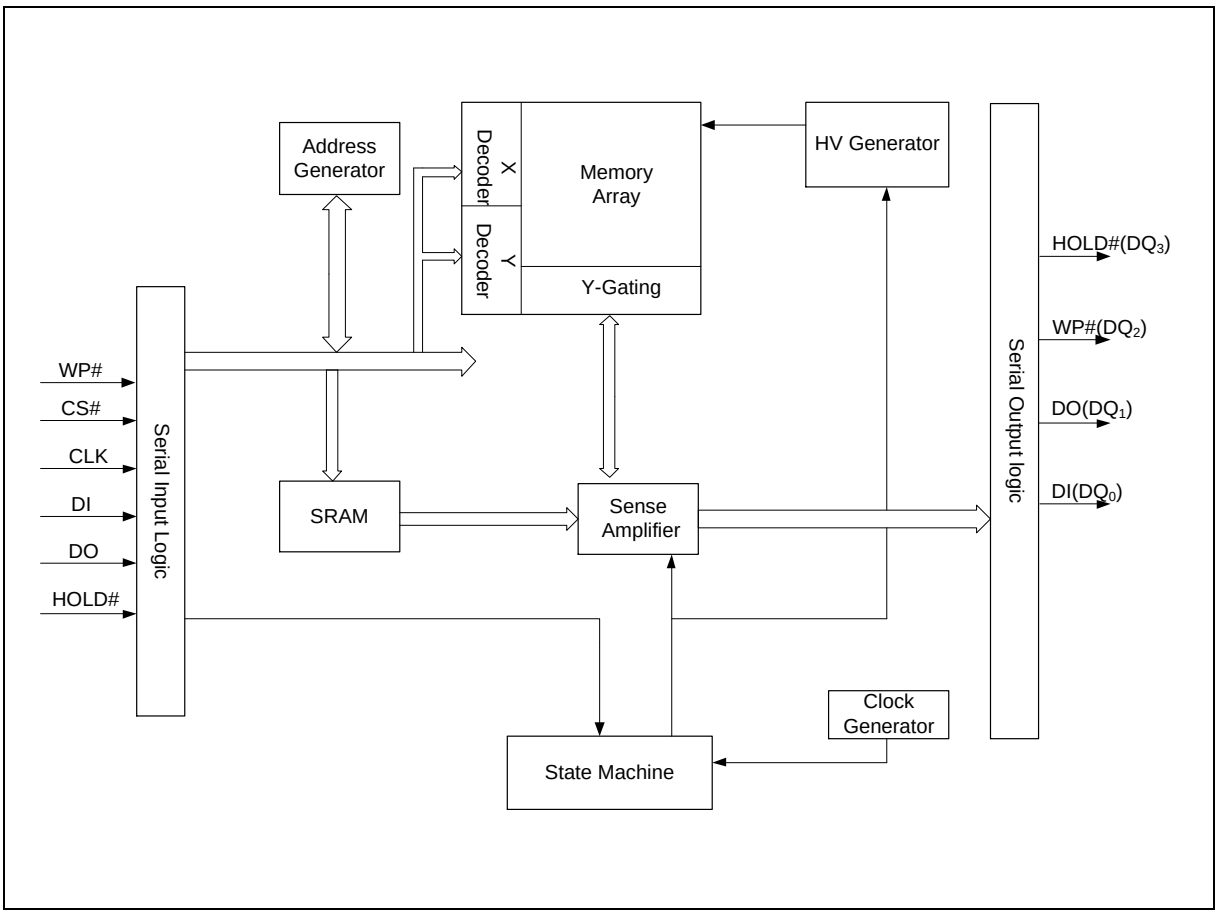


Figure 1 FM25LQ64I3 Serial Flash Memory Block Diagram

6. Pin Descriptions

Serial Clock (CLK): The SPI Serial Clock Input (CLK) pin provides the timing for serial input and output operations.

Serial Data Input, Output and I/Os (DI, DO and DQ_0, DQ_1, DQ_2, DQ_3): The FM25LQ64I3 supports standard SPI, Dual SPI, Quad SPI and QPI operation. Standard SPI instructions use the unidirectional DI (input) pin to serially write instructions, addresses or data to the device on the rising edge of the Serial Clock (CLK) input pin. Standard SPI also uses the unidirectional DO (output) to read data or status from the device on the falling edge of CLK.

Dual/Quad SPI and QPI instructions use the bidirectional DQ pins to serially write instructions, addresses or data to the device on the rising edge of CLK and read data or status from the device on the falling edge of CLK. Quad SPI and QPI instructions require the non-volatile Quad Enable bit (QE) in Status Register-2 to be set. When QE=1, the WP# pin becomes DQ_2 and HOLD# pin becomes DQ_3. The FM25LQ64I3 also supports DTR read.

Chip Select (CS#): The SPI Chip Select (CS#) pin enables and disables device operation. When CS# is high, the device is deselected and the Serial Data Output (DO, or DQ_0, DQ_1, DQ_2, DQ_3) pins are at high impedance. When deselected, the devices power consumption will be at standby levels unless an internal erase, program or write status register cycle is in progress. When CS# is brought low, the device will be selected, power consumption will increase to active levels and instructions can be written to and data read from the device. After power-up, CS# must transition from high to low before a new instruction will be accepted. The CS# input must track the VCC supply level at power-up (see “9Write Protection” and Figure 76). If needed a pull-up resister on CS# can be used to accomplish this. The CS # input must be pulled up in standby mode.

HOLD (HOLD#): The HOLD# pin allows the device to be paused while it is actively selected. When HOLD# is brought low, while CS# is low, the DO pin will be at high impedance and signals on the DI and CLK pins will be ignored (don’t care). When HOLD**#** is brought high, device operation can resume. The HOLD# function can be useful when multiple devices are sharing the same SPI signals. The HOLD# pin is active low. When the QE bit of Status Register-2 is set for Quad I/O, the HOLD# pin function is not available since this pin is used for DQ_3.

Write Protect (WP#): The Write Protect (WP#) pin can be used to prevent the Status Registers from being written. Used in conjunction with the Status Register’s Block Protect (CMP, SEC, TB, BP2, BP1 and BP0) bits and Status Register Protect (SRP) bits, a portion as small as a 4KB sector or the entire memory array can be hardware protected. The WP# pin is active low. However, when the QE bit of Status Register-2 is set for Quad I/O, the WP# pin function is not available since this pin is used for DQ_2.

7. Memory Organization

The FM25LQ64I3 array is organized into 32,768 programmable pages of 256-bytes each. Up to 256 bytes can be programmed (bits are programmed from 1 to 0) at a time. Pages can be erased in groups of 16 (4KB sector erase), groups of 128 (32KB block erase), groups of 256 (64KB block erase) or the entire chip (chip erase).The FM25LQ64I3 has 2,048 erasable sectors, 256 erasable 32-k byte blocks and 128 erasable 64-k byte blocks respectively. The small 4KB sectors allow for greater flexibility in applications that require data and parameter storage.

Table 1Memory Organization

Block (64KB)	Block (32KB)	Sector (4KB)	Address Range	
127	255 | 254	2047	7FF000h	7FFFFFh
		…	…	…
		2032	7F0000h	7F0FFFh
126	253 | 252	2031	7EF000h	7EFFFFh
		…	…	…
		2016	7E0000h	7E0FFFh
…	…	…	…	…
		…	…	…
		…	…	…
…	…	…	…	…
		…	…	…
		…	…	…
4	9 | 8	79	04F000h	04FFFFh
		…	…	…
		64	040000h	040FFFh
3	7 | 6	63	03F000h	03FFFFh
		…	…	…
		48	030000h	030FFFh
2	5 | 4	47	02F000h	02FFFFh
		…	…	…
		32	020000h	020FFFh
1	3 | 2	31	01F000h	01FFFFh
		…	…	…
		16	010000h	010FFFh
0	1 | 0	15	00F000h	00FFFFh
		…	…	…
		2	002000h	002FFFh
		1	001000h	001FFFh
		0	000000h	000FFFh

8. Device Operations

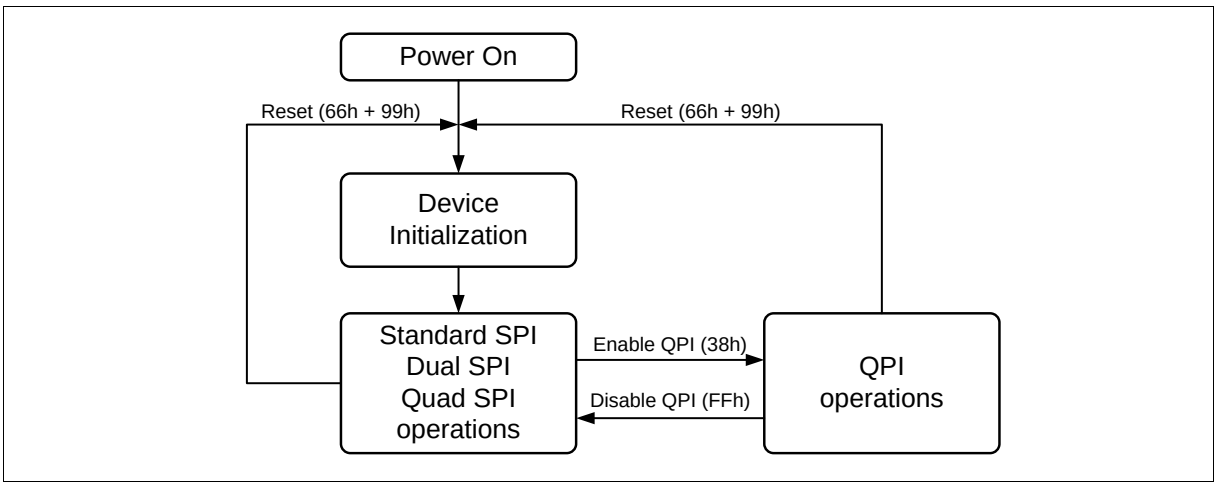


Figure 2 FM25LQ64I3 Serial Flash Memory Operation Diagram

8.1. Standard SPI

The FM25LQ64I3 is accessed through an SPI compatible bus consisting of four signals: Serial Clock (CLK), Chip Select (CS#), Serial Data Input (DI) and Serial Data Output (DO). Standard SPI instructions use the DI input pin to serially write instructions, addresses or data to the device on the rising edge of CLK. The DO output pin is used to read data or status from the device on the falling edge of CLK.

SPI bus operation Mode 0 (0,0) and 3 (1,1) are supported. The primary difference between Mode 0 and Mode 3 concerns the normal state of the CLK signal when the SPI bus master is in standby and data is not being transferred to the Serial Flash. For Mode 0, the CLK signal is normally low on the falling and rising edges of CS#. For Mode 3, the CLK signal is normally high on the falling and rising edges of CS#.

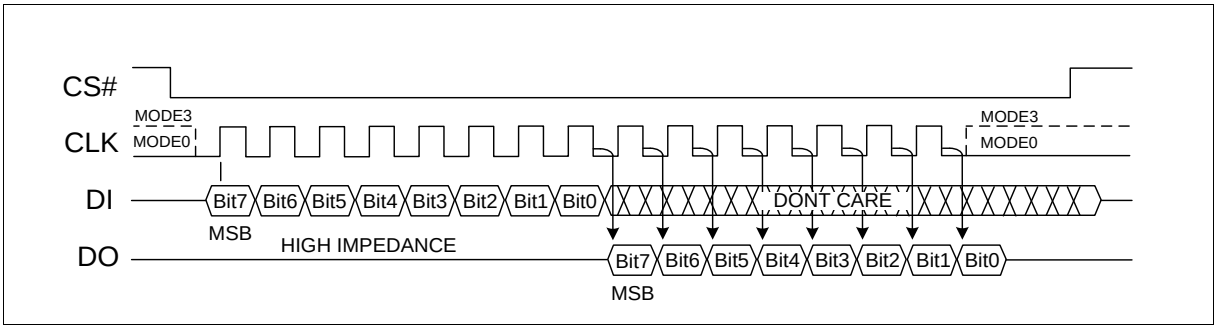


Figure 3 The difference between Mode 0 and Mode 3

8.2. Dual SPI

The FM25LQ64I3 supports Dual SPI operation when using instructions such as “Fast Read Dual Output (3Bh)” and “Fast Read Dual I/O (BBh)”. These instructions allow data to be transferred to or from the device at twice the rate of ordinary Serial Flash devices. The Dual SPI Read instructions are ideal for quickly downloading code to RAM upon power-up (code-shadowing) or for executing non-speed-critical code directly from the SPI bus (XIP). When using Dual SPI instructions, the DI and DO pins become bidirectional I/O pins: DQ_0 and DQ_1.

8.3. Quad SPI

The FM25LQ64I3 supports Quad SPI operation when using instructions such as “Fast Read Quad Output (6Bh)”, “Fast Read Quad I/O (EBh)”. These instructions allow data to be transferred to or from the device at four times the rate of the standard SPI. The Quad Read instructions offer a significant improvement in continuous and random access transfer rates allowing fast code-shadowing to RAM or execution directly from the SPI bus (XIP). When using Quad SPI instructions the DI and DO pins become bidirectional DQ_0 and DQ_1 and the WP # and HOLD# pins become DQ_2 and DQ_3 respectively. Quad SPI instructions require the non-volatile Quad Enable bit (QE) in Status Register-2 to be set.

8.4. QPI

The FM25LQ64I3 supports Quad Peripheral Interface (QPI) operations only when the device is switched from Standard/Dual/Quad SPI mode to QPI mode using the “Enable QPI (38h)” instruction. The typical SPI protocol requires that the byte-long instruction code being shifted into the device only via DI pin in eight serial clocks. The QPI mode utilizes all four DQ pins to input the instruction code, thus only two serial clocks are required. This can significantly reduce the SPI instruction overhead and improve system performance in an XIP environment. Standard/Dual/Quad SPI mode and QPI mode are exclusive. Only one mode can be active at any given time. “Enable QPI (38h)” and “Disable QPI (FFh)” instructions are used to switch between these two modes. Upon power-up or after a software reset using “Reset (66-99h)” instruction, the default state of the device is Standard/Dual/Quad SPI mode. To enable QPI mode, the non-volatile Quad Enable bit (QE) in Status Register-2 is required to be set. When using QPI instructions, the DI and DO pins become bidirectional DQ_0 and DQ_1, and the WP# and HOLD# pins become DQ_2 and DQ_3 respectively. See Figure 2 for the device operation modes.

8.5. SPI/QPI DTR Read Instruction

The FM25LQ64I3 supports multiple DTR (Double Transfer Rate) Read instructions that operate in Quad SPI and QPI modes to effectively improve the read operation throughput without increasing the serial clock frequency. The byte-long instruction code is still latched into the device on the rising edge of the serial clock similar to all other SPI/QPI instructions. Once a DTR instruction code is accepted by the device, the address input and data output will be latched on both rising and falling edges of the serial clock.

8.6. Hold

For Standard SPI and Dual SPI operations, the HOLD# signal allows the FM25LQ64I3 operation to be paused while it is actively selected (when CS# is low). The HOLD# function may be useful in cases where the SPI data and clock signals are shared with other devices. For example, consider if the page buffer was only partially written when a priority interrupt requires use of the SPI bus. In this case the HOLD# function can save the state of the instruction and the data in the buffer so programming can resume where it left off once the bus is available again. The HOLD# function is only available for standard SPI and Dual SPI operation, not during Quad SPI or QPI.

To initiate a HOLD# condition, the device must be selected with CS# low. A HOLD# condition will activate on the falling edge of the HOLD# signal if the CLK signal is already low. If the CLK is not already low the HOLD# condition will activate after the next falling edge of CLK. The HOLD# condition will terminate on the rising edge of the HOLD# signal if the CLK signal is already low. If the CLK is not already low the HOLD# condition will terminate after the next falling edge of CLK. During a HOLD# condition, the Serial Data Output (DO) is high impedance, and Serial Data Input (DI) and Serial Clock (CLK) are ignored. The Chip Select (CS#) signal should be kept active (low) for the full duration of the HOLD# operation to avoid resetting the internal logic state of the device.

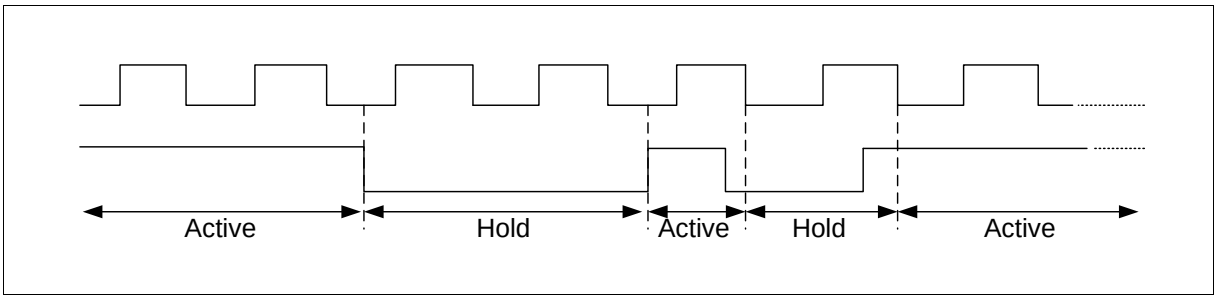


Figure 4 HoldCondition Waveform

9. Write Protection

Applications that use non-volatile memory must take into consideration the possibility of noise and other adverse system conditions that may compromise data integrity. To address this concern, the FM25LQ64I3 provides several means to protect the data from inadvertent writes.

Write Protect Features

- Device resets when VCC is below threshold
- Time delay write disable after Power-up
- Write enable/disable instructions and automatic write disable after erase or program
- Software and Hardware (WP# pin) write protection using Status Register
- Write Protection using Power-down instruction
- Lock Down write protection for Status Register until the next power-up
- One Time Program (OTP) write protection for array and Security Sectors using Status Register.

Upon power-up or at power-down, the FM25LQ64I3 will maintain a reset condition while VCC is below the threshold value of VWI, (See “12.3Power-up Timing” and Figure 76). While reset, all operations are disabled and no instructions are recognized. During power-up and after the VCC voltage exceeds VWI, all program and erase related instructions are further disabled for a time delay of t_{PUW}. This includes the Write Enable, Page Program, Sector Erase, Block Erase, Chip Erase and the Write Status Register instructions. Note that the chip select pin (CS#) must track the VCC supply level at power-up until the VCC-min level and t_{VSL} time delay is reached. If needed a pull-up resister on CS# can be used to accomplish this.

After power-up the device is automatically placed in a write-disabled state with the Status Register Write Enable Latch (WEL) set to “0”. A Write Enable instruction must be issued before a Page Program, Sector Erase, Block Erase, Chip Erase or Write Status Register instruction will be accepted. After completing a program, erase or write instruction the Write Enable Latch (WEL) is automatically cleared to a write-disabled state of “0”.

Software controlled write protection is facilitated using the Write Status Register instruction and setting the Status Register Protect (SRP0, SRP1) and Block Protect (CMP, SEC, TB, BP[2:0]) bits. These settings allow a portion as small as a 4KB sector or the entire memory array to be configured as read only. Used in conjunction with the Write Protect (WP#) pin, changes to the Status Register can be enabled or disabled under hardware control. See Status Register section for further information. Additionally, the Power-down instruction offers an extra level of write protection as all instructions are ignored except for the Release Power-down instruction and the Software Reset instruction.

The FM25LQ64I3 also provides another Write Protect method using the individual Block Locks. Each 64KB block (except the top and bottom blocks, total of 30 blocks) and each 4KB sector within the top/bottom blocks (total of 32 sectors) are equipped with an Individual Block Lock bit. When the lock bit is 0, the corresponding sector or block can be erased or programmed; when the lock bit is set to 1, Erase or Program commands issued to the corresponding sector or block will be ignored. When the device is powered on, all individual Block Lock bits will be 1, so the entire memory array is protected from Erase/Program. An “Individual Block Unlock (39h)” instruction must be issued to unlock any specific sector or block. The WPS bit in Status Register-2 is used to decide which Write Protect scheme should be used. When WPS=0(factory default), the device will only utilize CMP,SEC,TB, BP[2:0] to protect specific areas of the array; when WPS=1, the device will utilize the Individual Block Locks for write protection, each protect scheme for the corresponding is available.
Note: If power-down occurs while a WRITE, PROGRAM, or ERASE cycle is in progress, data corruption may result.

10. Status Register

The Read Status Register instructions can be used to provide status on the availability of the Flash memory array, if the device is write enabled or disabled, the state of write protection, Quad SPI setting, Security Sector lock status. The Write Status Register instruction can be used to configure the device write protection features, Quad SPI setting and Security Sector OTP locks. Write access to the Status Register is controlled by the state of the non-volatile Status Register Protect bits (SRP0, SRP1), the Write Enable instruction, and during Standard/Dual SPI operations, the WP# pin.

Factory default for all Status Register bits are 0.

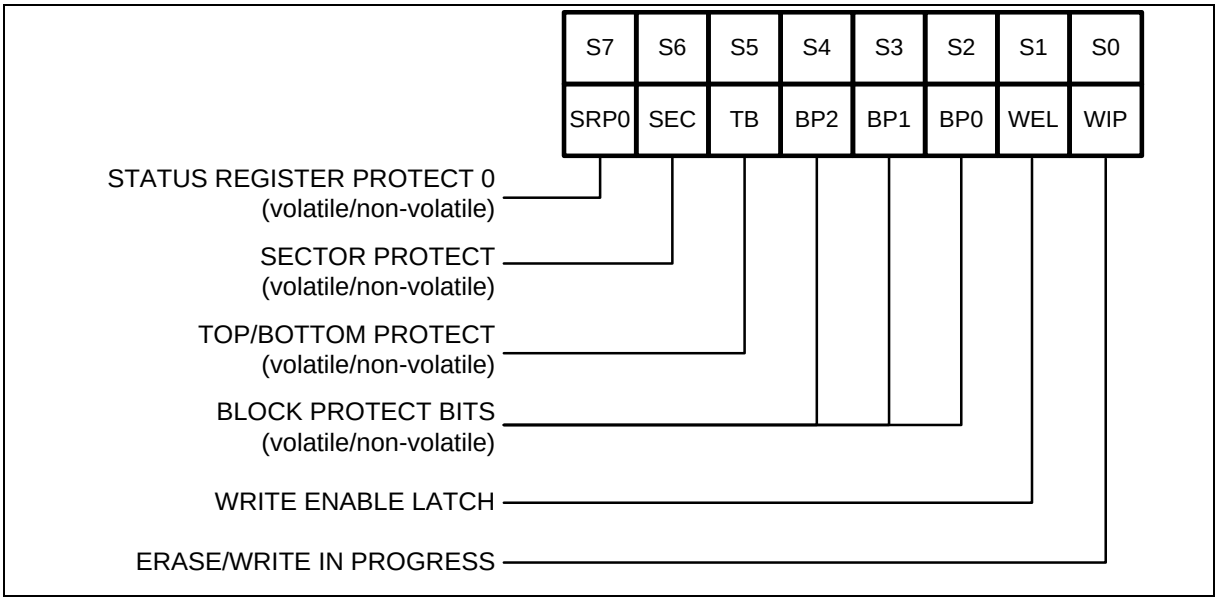


Figure 5 Status Register-1

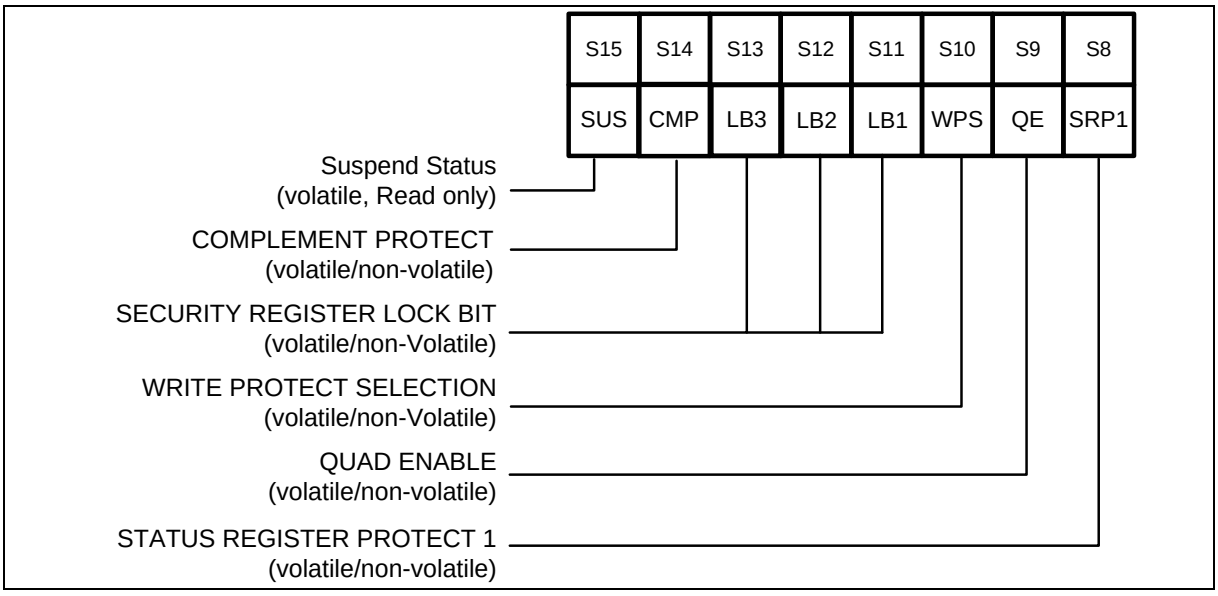


Figure 6 Status Register-2

10.1. WIP Bit

WIP is a read only bit in the status register (S0) that is set to a 1 state when the device is executing a Page Program, Quad Page Program, Sector Erase, Block Erase, Chip Erase, Write Status Register or Erase/Program Security Sector instruction. During this time the device will ignore further instructions except for the Read Status Register instruction (see t_W, t_{PP}, t_{SE}, t_{BE}, and t_{CE} in "12.6 AC Electrical Characteristics"). When the program, erase or write status register(or security sector) instruction has completed, the WIP bit will be cleared to a 0 state indicating the device is ready for further instructions.

10.2. Write Enable Latch (WEL)

Write Enable Latch (WEL) is a read only bit in the status register (S1) that is set to 1 after executing a Write Enable Instruction. The WEL status bit is cleared to 0 when the device is write disabled. A write disable state occurs up on power-up or after any of the following instructions: Write Disable, Page Program, Quad Page Program, Sector Erase, Block Erase, Chip Erase, Write Status Register, Erase Security Sector and Program Security Sector.

10.3. Block Protect Bits (BP2, BP1, BP0)

The Block Protect Bits (BP2, BP1, BP0) are non-volatile read/write bits in the status register (S4, S3, and S2) that provide Write Protection control and status. Block Protect bits can be set using the Write Status Register Instruction (see t_W in "12.6 AC Electrical Characteristics"). All, none or a portion of the memory array can be protected from Program and Erase instructions (see Table 3 Status Register Memory Protection). The factory default setting for the Block Protection Bits is 0, none of the array protected.

10.4. Top/Bottom Block Protect (TB)

The non-volatile Top/Bottom bit (TB) controls if the Block Protect Bits (BP2, BP1, BP0) protect from the Top (TB=0) or the Bottom (TB=1) of the array as shown in Table 3 Status Register Memory Protection table. The factory default setting is TB=0. The TB bit can be set with the Write Status Register Instruction depending on the state of the SRP0, SRP1 and WEL bits.

10.5. Sector/Block Protect (SEC)

The non-volatile Sector/Block Protect bit (SEC) controls if the Block Protect Bits (BP2, BP1, BP0) protect either 4KB Sectors (SEC=1) or 64KB Blocks (SEC=0) in the Top (TB=0) or the Bottom (TB=1) of the array as shown in Table 3 Status Register Memory Protection table. The default setting is SEC=0.

10.6. Complement Protect (CMP)

The Complement Protect bit (CMP) is a non-volatile read/write bit in the status register (S14). It is used in conjunction with SEC, TB, BP2, BP1 and BP0 bits to provide more flexibility for the array protection. Once CMP is set to 1, previous array protection set by SEC, TB, BP2, BP1 and BP0 will be reversed. For instance, when CMP=0, a top 4KB sector can be protected while the rest of the array is not; when CMP=1, the top 4KB sector will become unprotected while the rest of the array become read-only. Please refer to Table 3 Status Register Memory Protection table for details. The default setting is CMP=0.

10.7. Status Register Protect (SRP1, SRP0)

The Status Register Protect bits (SRP1 and SRP0) are non-volatile read/write bits in the status register (S8 and S7).The SRP bits control the method of write protection: software protection, hardware protection, power supply lock-down or one time programmable (OTP) protection.

Table 2 Status Register Protect bits

SRP1	SRP0	WP#	Status Register	Description
0	0	X	Software Protection	WP# pin has no control. The Status register can be written to after a Write Enable instruction, WEL=1. (Factory Default)
0	1	0	Hardware Protected	When WP# pin is low the Status Register locked and can not be written to.
0	1	1	Hardware Unprotected	When WP# pin is high the Status register is unlocked and can be written to after a Write Enable instruction, WEL=1.
1	0	X	Power Supply Lock-Down	Status Register is protected and can not be written to again until the next power-down, power-up cycle.(1)
1	1	X	One Time Program	Status Register is permanently protected and can not be written to.

Note:

1. When SRP1, SRP0 = (1, 0), a power-down, power-up cycle will change SRP1, SRP0 to (0, 0) state.

10.8. Erase/Program Suspend Status (SUS)

The Suspend Status bit is a read only bit in the status register (S15) that is set to 1 after executing a Erase/Program Suspend (75h) instruction. The SUS status bit is cleared to 0 by Erase/Program Resume (7Ah) instruction as well as a power-down, power-up cycle.

10.9. Security Sector Lock Bits (LB3, LB2, LB1)

The Security Register Lock Bits (LB3, LB2, LB1) are non-volatile One Time Program (OTP) bits in Status Register (S13, S12, S11) that provide the write protect control and status to the Security Registers. The default state of LB Bits are 0, Security Registers are unlocked. LB Bits can be set to 1 individually using the Write Status Register instruction. LB bits are One Time Programmable (OTP), once they are set to 1, the Security Registers will become read-only permanently.

10.10. Write Protect Selection (WPS)

The WPS bit is used to select which Write Protect scheme should be used. When WPS=0, the device will use the combination of CMP, TB, SEC, BP[2:0] to protect a specific area of the memory array. When WPS=1, the device will utilize the Individual Block Locks to protect any individual sector or blocks. The default value for all Individual Block Lock bits is 1 upon device power on or after reset.

10.11. Quad Enable (QE)

The Quad Enable (QE) bit is a non-volatile read/write bit in the status register (S9) that allows Quad SPI and QPI operation. When the QE bit is set to a 0 state (factory default), the WP# pin and HOLD# are enabled. When the QE bit is set to a 1, the Quad DQ_2 and DQ_3 pins are enabled, and WP# and HOLD# functions are disabled.

QE bit is required to be set to a 1 before issuing an “Enable QPI (38h)” to switch the device from Standard/Dual/Quad SPI to QPI, otherwise the command will be ignored. When the device is in QPI mode, QE bit will remain to be 1. A “Write Status Register” command in QPI mode cannot change QE bit from a “1” to a “0”.

WARNING: If the WP# or HOLD# pins are tied directly to the power supply or ground during standard SPI or Dual SPI operation, the QE bit should never be set to a 1.

10.12. Status Register Memory Protection (WPS=0)

Table 3 Status Register Memory Protection

STATUS REGISTER						FM25Q64AI3 (64M-BIT) MEMORY PROTECTION			
CMP	SEC	TB	BP2	BP1	BP0	PROTECTED BLOCK(S)	PROTECTED ADDRESSES	PROTECTED DENSITY	PROTECTED PORTION
0	X	X	0	0	0	NONE	NONE	NONE	NONE
0	0	0	0	0	1	126 and 127	7E0000h – 7FFFFFh	128KB	Upper 1/64
0	0	0	0	1	0	124 thru127	7C0000h – 7FFFFFh	256KB	Upper 1/32
0	0	0	0	1	1	120 thru 127	780000h – 7FFFFFh	512KB	Upper 1/16
0	0	0	1	0	0	112 thru 127	700000h – 7FFFFFh	1MB	Upper 1/8
0	0	0	1	0	1	96 thru 127	600000h – 7FFFFFh	2MB	Upper 1/4
0	0	0	1	1	0	64 thru 127	400000h – 7FFFFFh	4MB	Upper 1/1
0	0	1	0	0	1	0 and 1	000000h – 01FFFFh	128KB	Lower 1/64
0	0	1	0	1	0	0 thru 3	000000h – 03FFFFh	256KB	Lower 1/32
0	0	1	0	1	1	0 thru 7	000000h – 07FFFFh	512KB	Lower 1/16
0	0	1	1	0	0	0 thru 15	000000h – 0FFFFFh	1MB	Lower 1/8
0	0	1	1	0	1	0 thru 31	000000h – 1FFFFFh	2MB	Lower 1/4
0	0	1	1	1	0	0 thru 63	000000h – 3FFFFFh	4MB	Lower 1/2
0	X	X	1	1	1	0 thru 127	000000h – 7FFFFFh	8MB	ALL
0	1	0	0	0	1	127	7FF000h – 7FFFFFh	4KB	U - 1/2048
0	1	0	0	1	0	127	7FE000h – 7FFFFFh	8KB	U - 1/1024
0	1	0	0	1	1	127	7FC000h – 7FFFFFh	16KB	U - 1/512
0	1	0	1	0	X	127	7F8000h – 7FFFFFh	32KB	U - 1/256
0	1	0	1	1	0	127	7F8000h – 7FFFFFh	32KB	U - 1/256
0	1	1	0	0	1	0	000000h – 000FFFh	4KB	L - 1/2048
0	1	1	0	1	0	0	000000h – 001FFFh	8KB	L - 1/1024
0	1	1	0	1	1	0	000000h – 003FFFh	16KB	L - 1/512
0	1	1	1	0	X	0	000000h – 007FFFh	32KB	L - 1/256
0	1	1	1	1	0	0	000000h – 007FFFh	32KB	L - 1/256
1	X	X	0	0	0	ALL	000000h – 7FFFFFh	ALL	ALL
1	0	0	0	0	1	0 thru 125	000000h – 7DFFFFh	8,064KB	Lower 63/64
1	0	0	0	1	0	0 thru 123	000000h – 7BFFFFh	7,936KB	Lower 31/32
1	0	0	0	1	1	0 thru 119	000000h – 77FFFFh	7,680KB	Lower 15/16
1	0	0	1	0	0	0 thru 111	000000h – 6FFFFFh	7MB	Lower 7/8
1	0	0	1	0	1	0 thru 95	000000h – 5FFFFFh	6MB	Lower 3/4

STATUS REGISTER						FM25Q64AI3 (64M-BIT) MEMORY PROTECTION			
CMP	SEC	TB	BP2	BP1	BP0	PROTECTED BLOCK(S)	PROTECTED ADDRESSES	PROTECTED DENSITY	PROTECTED PORTION
1	0	0	1	1	0	0 thru 63	000000h – 3FFFFFh	4MB	Lower 1/2
1	0	1	0	0	1	2 thru 127	020000h – 7FFFFFh	8,064KB	Upper 63/64
1	0	1	0	1	0	4 thru 127	040000h – 7FFFFFh	7,936KB	Upper 31/32
1	0	1	0	1	1	8 thru 127	080000h – 7FFFFFh	7,680KB	Upper 15/16
1	0	1	1	0	0	16 thru 127	100000h – 7FFFFFh	7MB	Upper 7/8
1	0	1	1	0	1	32 thru 127	200000h – 7FFFFFh	6MB	Upper 3/4
1	0	1	1	1	0	64 thru 127	400000h – 7FFFFFh	4MB	Upper 1/2
1	X	X	1	1	1	NONE	NONE	NONE	NONE
1	1	0	0	0	1	0 thru 127	000000h – 7FEFFFh	8,188KB	L - 2047/2048
1	1	0	0	1	0	0 thru 127	000000h – 7FDFFFh	8,184KB	L - 1023/1024
1	1	0	0	1	1	0 thru 127	000000h – 7FBFFFh	8,176KB	L - 511/512
1	1	0	1	0	X	0 thru 127	000000h – 7F7FFFh	8,160KB	L - 255/256
1	1	0	1	1	0	0 thru 127	000000h – 7F7FFFh	8,160KB	L - 255/256
1	1	1	0	0	1	0 thru 127	001000h – 7FFFFFh	8,188KB	U - 2047/2048
1	1	1	0	1	0	0 thru 127	002000h –7FFFFFh	8,184KB	U - 1023/1024
1	1	1	0	1	1	0 thru 127	004000h –7FFFFFh	8,176KB	U - 511/512
1	1	1	1	0	X	0 thru 127	008000h –7FFFFFh	8,160KB	U - 255/256
1	1	1	1	1	0	0 thru 127	008000h –7FFFFFh	8,160KB	U - 255/256

10.13. Status Register Memory Protection (WPS=1)

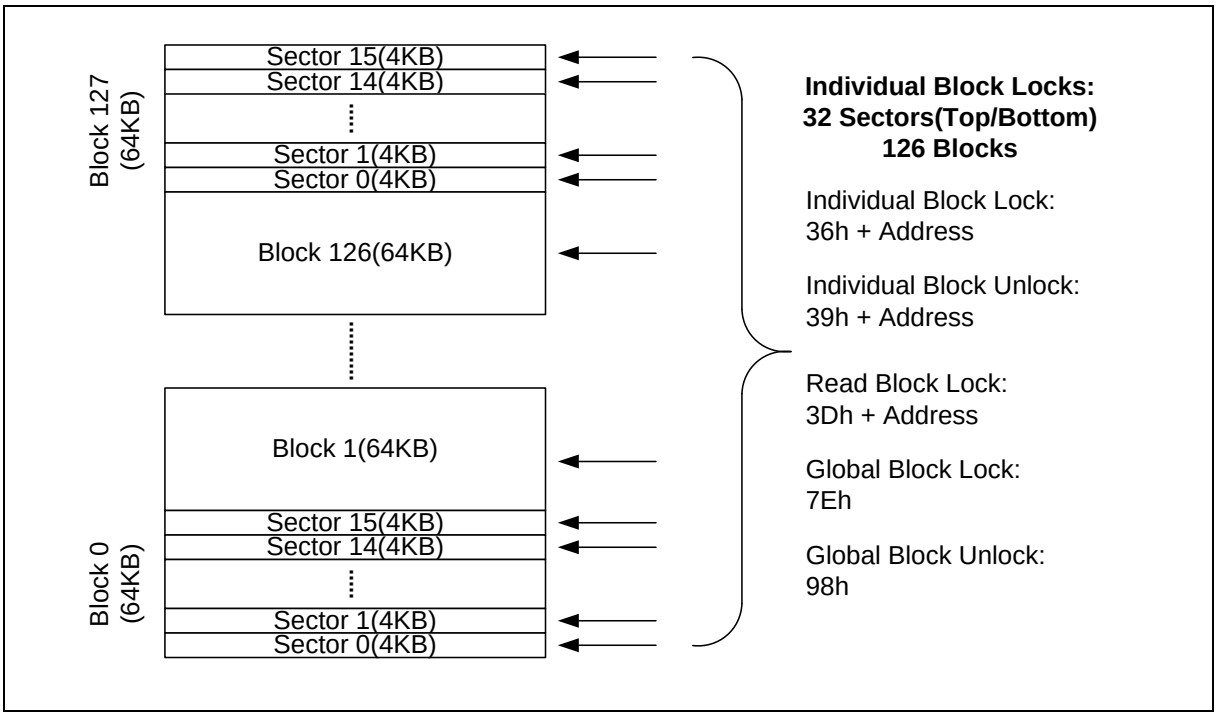


Figure 7 Individual Sector/Block Locks

11. Instructions

The Standard/Dual/Quad SPI instruction set of the FM25LQ64I3 consists of 43 basic instructions that are fully controlled through the SPI bus (see Table 5 Standard SPI Instructions Set (1)~ Table 7 Quad SPI Instructions Set). Instructions are initiated with the falling edge of Chip Select (CS#). The first byte of data clocked into the DI input provides the instruction code. Data on the DI input is sampled on the rising edge of clock with most significant bit (MSB) first.

The QPI instruction set of the FM25LQ64I3 consists of 30 basic instructions that are fully controlled through the SPI bus (see Table 8 QPI Instructions Set (14)). Instructions are initiated with the falling edge of Chip Select (CS#). The first byte of data clocked through DQ[3:0] pins provides the instruction code. Data on all four DQ pins are sampled on the rising edge of clock with most significant bit (MSB) first. All QPI instructions, addresses, data and dummy bytes are using all four DQ pins to transfer every byte of data with every two serial clocks (CLK).

Instructions vary in length from a single byte to several bytes and may be followed by address bytes, data bytes, dummy bytes (don't care), and in some cases, a combination. Instructions are completed with the rising edge of CS#. Clock relative timing diagrams for each instruction are included in Figure 8 Through Figure 73. All read instructions can be completed after any clocked bit. However, all instructions that Write, Program or Erase must complete on a byte boundary (CS# driven high after a full 8-bits have been clocked) otherwise the instruction will be ignored. This feature further protects the device from inadvertent writes. Additionally, while the memory is being programmed or erased, or when the Status Register is being written, all instructions except for Read Status Register will be ignored until the program or erase cycle has completed.

11.1. Device ID and Instruction Set Tables

11.1.1. Manufacturer and Device Identification

Table 4 Manufacturer and Device Identification

OP Code	MF7-MF0	ID15-ID0	ID7-ID0
ABh			16h
90h,92h,94h	A1h		16h
9Fh	A1h	6017h	

11.1.2. Standard SPI Instructions Set

Table 5 Standard SPI Instructions Set (1)

INSTRUCTION NAME	BYTE 1	BYTE 2	BYTE 3	BYTE 4	BYTE 5	BYTE 6
CLOCK NUMBER	*(0-7)*	*(8-15)*	*(16-23)*	*(24-31)*	*(32-39)*	*(40-47)*
Write Enable	**06h**					
Volatile SR Write Enable	**50h**					
Write Disable	**04h**					
Read Status Register-1	**05h**	(S7-S0)(2)				
Write Status Register-1(3)	**01h**	(S7-S0) (3)				
Write Status Register-1&2	**01h**	(S7-S0)	(S15-S8)			
Read Status Register-2	**35h**	(S15-S8)(2)				
Write Status Register-2	**31h**	(S15-S8)				
Page Program	**02h**	A23-A16	A15-A8	A7-A0	D7-D0	D7-D0(4)
Sector Erase (4KB)	**20h**	A23-A16	A15-A8	A7-A0		
Block Erase (32KB)	**52h**	A23-A16	A15-A8	A7-A0		
Block Erase (64KB)	**D8h**	A23-A16	A15-A8	A7-A0		
Chip Erase	**C7h/60h**					
Erase / Program Suspend	**75h**					
Erase / Program Resume	**7Ah**					
Power-down	**B9h**					
Read Data	**03h**	A23-A16	A15-A8	A7-A0	(D7-D0)	
Fast Read	**0Bh**	A23-A16	A15-A8	A7-A0	dummy	(D7-D0)
Release Powerdown / ID(5)	**ABh**	dummy	dummy	Dummy	(ID7-ID0)(2)	
Manufacturer/Device ID(5)(6)	**90h**	dummy	dummy	00h	(MF7-MF0)	(ID7-ID0)
JEDEC ID(6)	**9Fh**	(MF7-MF0) Manufacturer	(ID15-ID8) Memory Type	(ID7-ID0) Capacity		
Read SFDP Register	**5Ah**	00h	00h	A7-A0	dummy	(D7-D0)
Read Unique ID(6)	**4Bh**	dummy	dummy	dummy	dummy	(UID63-UID0)
Erase Security Sectors(7)	**44h**	A23-A16	A15-A8	A7-A0		
Program Security Sectors(7)	**42h**	A23-A16	A15-A8	A7-A0	D7-D0	D7-D0
Read Security Sectors(7)	**48h**	A23-A16	A15-A8	A7-A0	dummy	(D7-D0)
Enable QPI	**38h**					
Enable Reset	**66h**					
Reset	**99h**					
Individual Block Lock	**36h**	A23-A16	A15-A8	A7-A0		
Individual Block Unlock	**39h**	A23-A16	A15-A8	A7-A0		
Read Block Lock	**3Dh**	A23-A16	A15-A8	A7-A0	(D7-D0)	
Global Block Lock	**7Eh**	A23-A16	A15-A8	A7-A0		
Global Block Unlock	**98h**	A23-A16	A15-A8	A7-A0		

11.1.3. Dual SPI Instructions Set

Table 6 Dual SPI Instructions Set

INSTRUCTION NAME	BYTE 1	BYTE 2	BYTE 3	BYTE 4	BYTE 5	BYTE 6
CLOCK NUMBER	*(0-7)*	*(8-15)*	*(16-23)*	*(24-31)*	*(32-39)*	*(40-47)*
Fast Read Dual Output	**3Bh**	A23-A16	A15-A8	A7-A0	Dummy	(D7-D0, …)(9)
Fast Read Dual I/O	**BBh**	A23-A8(8)	A7-A0, M7-M0 (8)	Dummy	(D7-D0, …)(9)	
Manufacturer/Device ID by Dual I/O(5)(6)	**92h**	A23-A8(8)	A7-A0, M7-M0(8)	(MF7-MF0, ID7-ID0)		

11.1.4. Quad SPI Instructions Set

Table 7 Quad SPI Instructions Set

INSTRUCTION NAME	BYTE 1	BYTE 2	BYTE 3	BYTE 4	BYTE 5	BYTE 6
CLOCK NUMBER	*(0-7)*	*(8-15)*	*(16-23)*	*(24-31)*	*(32-39)*	*(40-47)*
Quad Page Program	**32h**	A23-A16	A15-A8	A7-A0	D7-D0, …(11)	D7-D0, …(11)
Fast Read Quad Output	**6Bh**	A23-A16	A15-A8	A7-A0	Dummy	(D7-D0, …)(11)
Fast Read Quad I/O	**EBh**	A23-A0, M7-M0(10)	Dummy	(D7-D0, …)(11)		
Set Burst with Wrap	**77h**	xxxxx, W6-W4(10)				
Manufacture/Device ID by Quad I/O(5)(6)	**94h**	A23-A0, M7-M0(10)	xxxx, (MF7-MF0, ID7-ID0)	(MF7-MF0, ID7-ID0, …)		

11.1.5. QPI Instructions Set

Table 8 QPI Instructions Set [14]

INSTRUCTION NAME	BYTE 1	BYTE 2	BYTE 3	BYTE 4	BYTE 5	BYTE 6
CLOCK NUMBER	*(0,1)*	*(2,3)*	*(4,5)*	*(6,7)*	*(8,9)*	*(10,11)*
Write Enable	**06h**					
Volatile SR Write Enable	**50h**					
Write Disable	**04h**					
Read Status Register-1	**05h**	(S7-S0)[2]				
Write Status Register-1[3]	**01h**	(S7-S0)[3]				
Write Status Register-1&2	**01h**	(S7-S0)	(S15-S8)			
Read Status Register-2	**35h**	(S15-S8)[2]				
Write Status Register-2	**31h**	(S15-S8)				
Chip Erase	**C7h/60h**					
Erase / Program Suspend	**75h**					
Erase / Program Resume	**7Ah**					
Power-down	**B9h**					
Set Read Parameters	**C0h**	P7-P0				
Enable Reset	**66h**					
Reset	**99h**					
Disable QPI	**FFh**					
Fast Read	**0Bh**	A23-A16	A15-A8	A7-A0	dummy[13]	
Burst Read with Wrap	**0Ch**	A23-A16	A15-A8	A7-A0	dummy[13]	
Fast Read Quad I/O	**EBh**	A23-A16	A15-A8	A7-A0	M7-M0[13]	dummy[13]
Release Powerdown / ID[5]	**ABh**	dummy	dummy	dummy	(ID7-ID0)[2]	
Manufacturer/Device ID[5][6]	**90h**	dummy	dummy	00h	(MF7-MF0)	(ID7-ID0)
JEDEC ID[5][6]	**9Fh**	(MF7-MF0) Manufacturer	(ID15-ID8) Memory Type	(ID7-ID0) Capacity		
Page Program	**02h**	A23-A16	A15-A8	A7-A0	D7-D0[11]	D7-D0[4]
Sector Erase (4KB)	**20h**	A23-A16	A15-A8	A7-A0		
Block Erase (32KB)	**52h**	A23-A16	A15-A8	A7-A0		
Block Erase (64KB)	**D8h**	A23-A16	A15-A8	A7-A0		
Read SFDP Register (5A)	**5Ah**	A23-A16	A15-A8	A7-A0	dummy[13]	
Individual Block Lock	**36h**	A23-A16	A15-A8	A7-A0		
Individual Block Unlock	**39h**	A23-A16	A15-A8	A7-A0		
Read Block Lock	**3Dh**	A23-A16	A15-A8	A7-A0	(D7-D0) [2]	
Global Block Lock	**7Eh**	A23-A16	A15-A8	A7-A0		
Global Block Unlock	**98h**	A23-A16	A15-A8	A7-A0		

11.1.6. DTR Instructions Set

Table 9 DTR Instructions Set (Quad SPI, QPI)

DTR Fast Read Quad I/O	BYTE 1	BYTE 2	BYTE 3	BYTE 4	BYTE 5	BYTE 6
CLOCK NUMBER	*(0-7)*	*(8)*	*(9)*	*(10)*	*(11)*	*(12-20)*
Quad SPI	EDh	A23-A16	A15-A8	A7-A0	M7-M0	dummy
CLOCK NUMBER	*(0,1)*	*(2)*	*(3)*	*(4)*	*(5)*	*(6-n)*[15]
QPI	EDh	A23-A16	A15-A8	A7-A0	M7-M0	dummy

Notes:

1. Data bytes are shifted with Most Significant Bit first. Byte fields with data in parenthesis "( )" indicate data output from the device on either 1, 2 or 4 DQ pins.
2. The Status Register contents and Device ID will repeat continuously until CS# terminates the instruction.
3. Write Status Register-1(01h) can also be used to program Status Register-1&2, see section 11.2.5.
4. At least one byte of data input is required for Page Program, Quad Page Program and Program Security Sectors, up to 256 bytes of data input. If more than 256 bytes of data are sent to the device, the addressing will wrap to the beginning of the page and overwrite previously sent data.
5. See Table 4 Manufacturer and Device Identification table for device ID information.
6. Please contact Shanghai Fudan Microelectronics Group Co., Ltd for details.
7. Security Sector Address:
   Security Sector 1: A23-A16 = 00h; A15-A12 = 0001h; A9-A0 = byte address
   Security Sector 2: A23-A16 = 00h; A15-A12 = 0010h; A9-A0 = byte address
   Security Sector 3: A23-A16 = 00h; A15-A12 = 0011h; A9-A0 = byte address
8. Dual SPI address input format:
   DQ_0 = A22, A20, A18, A16, A14, A12, A10, A8 A6, A4, A2, A0, M6, M4, M2, M0
   DQ_1 = A23, A21, A19, A17, A15, A13, A11, A9 A7, A5, A3, A1, M7, M5, M3, M1
9. Dual SPI data output format:
   DQ_0 = (D6, D4, D2, D0)
   DQ_1 = (D7, D5, D3, D1)
10. Quad SPI address input format:
    DQ_0 = A20, A16, A12, A8, A4, A0, M4, M0
    DQ_1 = A21, A17, A13, A9, A5, A1, M5, M1
    DQ_2 = A22, A18, A14, A10, A6, A2, M6, M2
    DQ_3 = A23, A19, A15, A11, A7, A3, M7, M3

    Set Burst with Wrap input format:
    DQ_0 = x, x, x, x, x, x, W4, x
    DQ_1 = x, x, x, x, x, x, W5, x
    DQ_2 = x, x, x, x, x, x, W6, x
    DQ_3 = x, x, x, x, x, x, x, x
11. Quad SPI data input/output format:
    DQ_0 = (D4, D0 …)
    DQ_1 = (D5, D1…)
    DQ_2 = (D6, D2…)
    DQ_3 = (D7, D3…)
12. QPI Command Address, Data input/output format:

CLK#	0	1	2	3	4	5	6	7	8	9	10	11
DQ_0	C4	C0	A20	A16	A12	A8	A4	A0	D4	D0	D4	D0
DQ_1	C5	C1	A21	A17	A13	A9	A5	A1	D5	D1	D5	D1
DQ_2	C6	C2	A22	A18	A14	A10	A6	A2	D6	D2	D6	D2
DQ_3	C7	C3	A23	A19	A15	A11	A7	A3	D7	D3	D7	D3

13. The number of dummy clocks is controlled by read parameter P5-P4.
14. The wrap around length for QPI Burst Read with Wrap is controlled by read parameter P1-P0

11.2. Instruction Description

11.2.1. Write Enable (WREN) (06h)

The Write Enable (WREN) instruction (Figure 8) sets the Write Enable Latch (WEL) bit in the Status Register to a 1. The WEL bit must be set prior to every Page Program, Quad Page Program, Sector Erase, Block Erase, Chip Erase, Write Status Register, Erase/Program Security Sectors and Block/Sector Lock/Unlock instruction. The Write Enable **(**WREN**)** instruction is entered by driving CS# low, shifting the instruction code “06h” into the Data Input (DI) pin on the rising edge of CLK, and then driving CS# high.

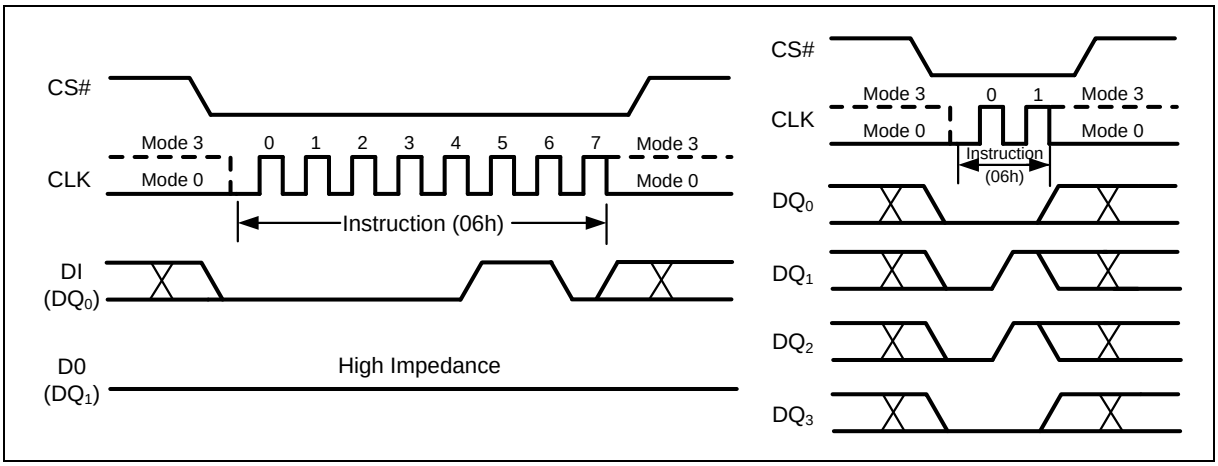


Figure 8 Write Enable Instruction for SPI Mode (left) or QPI Mode (right)

11.2.2. Write Enable for Volatile Status Register (50h)

The non-volatile Status Register bits described in section 10 can also be written to as volatile bits. This gives more flexibility to change the system configuration and memory protection schemes quickly without waiting for the typical non-volatile bit write cycles or affecting the endurance of the Status Register non-volatile bits. To write the volatile values into the Status Register bits, the Write Enable for Volatile Status Register (50h) instruction must be issued prior to a Write Status Register (01h/31h) instruction. Write Enable for Volatile Status Register instruction (Figure 9) will not set the Write Enable Latch (WEL) bit, it is only valid for the Write Status Register instruction to change the volatile Status Register bit values.

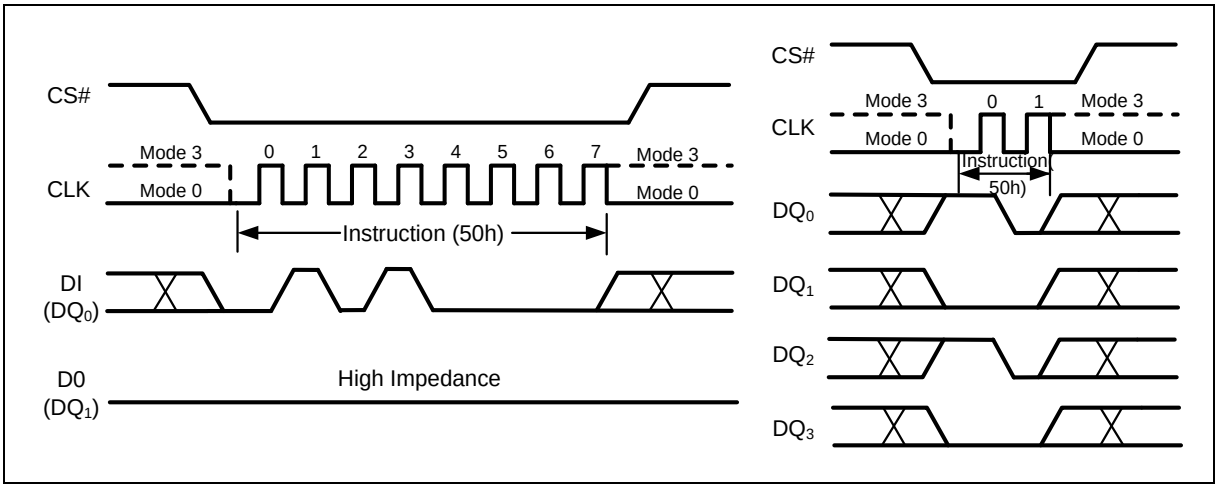


Figure 9 Write Enable for Volatile Status Register Instruction for SPI Mode (left) or QPI Mode (right)

11.2.3. Write Disable (WRDI) (04h)

The Write Disable (WRDI) instruction (Figure 10) resets the Write Enable Latch (WEL) bit in the Status Register to a 0. The Write Disable (WRDI) instruction is entered by driving CS# low, shifting the instruction code “04h” into the DI pin and then driving CS# high. Note that the WEL bit is automatically reset after Power-up and upon completion of the Write Status Register, Erase/Program Security Sectors, Page Program, Quad Page Program, Sector Erase, Block Erase, Chip Erase , Block/Sector Lock/Unlock and Reset instructions.

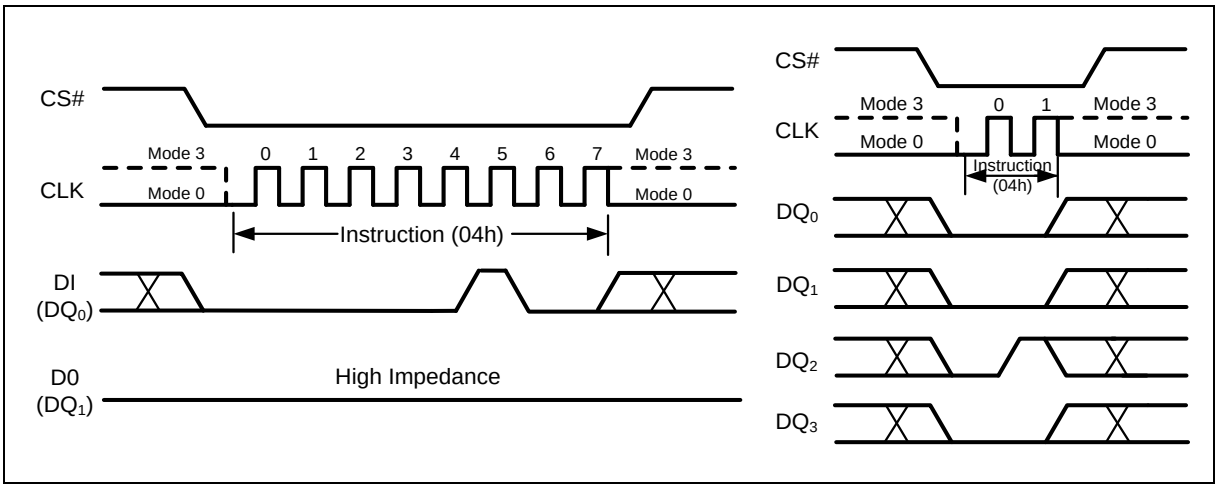


Figure 10 Write Disable Instruction for SPI Mode (left) or QPI Mode (right)

11.2.4. Read Status Register-1 (RDSR1) (05h), Status Register-2 (RDSR2) (35h)

The Read Status Register instructions allow the 8-bit Status Registers to be read. The instruction is entered by driving CS# low and shifting the instruction code “05h” for Status Register-1 or “35h” for Status Register-2 into the DI pin on the rising edge of CLK. The status register bits are then shifted out on the DO pin at the falling edge of CLK with most significant bit (MSB) first as shown in Figure 11. Refer to section 10 for Status Register description.

The Read Status Register instruction may be used at any time, even while a Program, Erase or Write Status Register cycle is in progress. This allows the WIP status bit to be checked to determine when the cycle is complete and if the device can accept another instruction. The Status Register can be read continuously, as shown in Figure 12. The instruction is completed by driving CS# high.

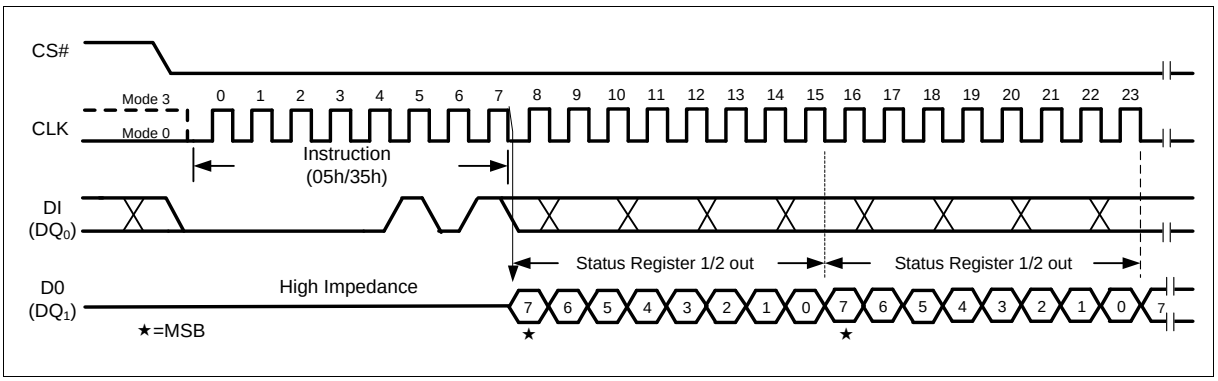


Figure 11 Read Status Register Instruction (SPI Mode)

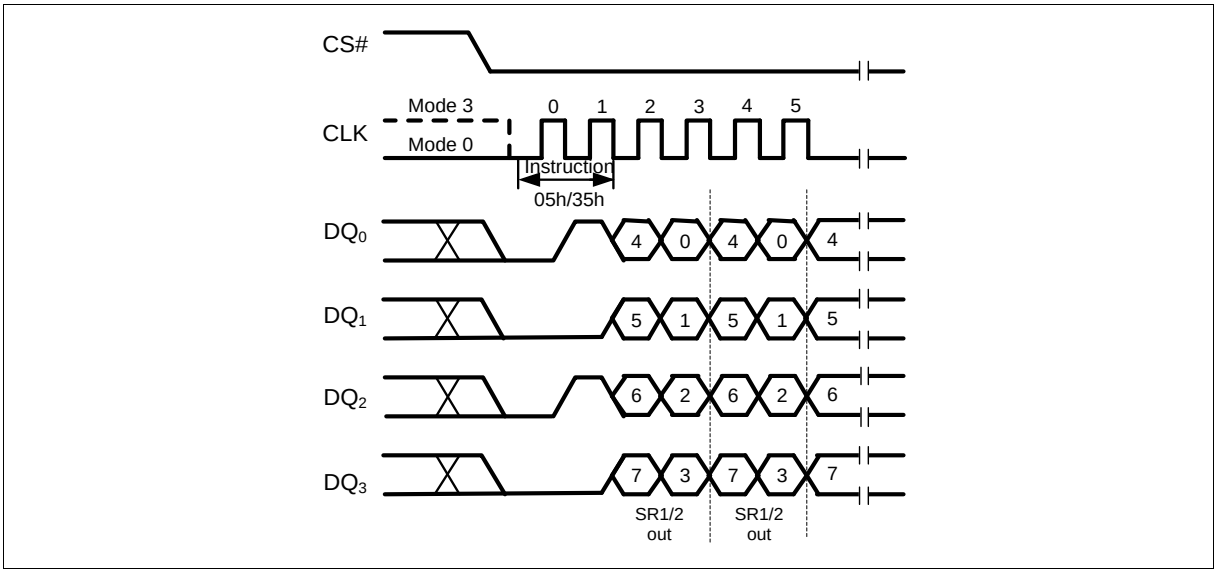


Figure 12 Read Status Register Instruction (QPI Mode)

11.2.5. Write Status Register-1 (WRSR1) (01h), Status Register-2 (WRSR2) (31h)

The Write Status Register instruction allows the Status Register to be written. The writable Status Register bits include: SRP0, TB, SEC, BP2, BP1 and BP0 in Status Register-1; CMP, LB Bits, QE, SRP1 and WPS in Status Register-2. All other Status Register bit locations are read-only and will not be affected by Write Status Register instruction. LB Bits are non-volatile OTP bits, once they are set to 1, they cannot be cleared to 0.

To write non-volatile Status Register bits, a standard Write Enable (06h) instruction must previously have been executed for the device to accept the Write Status Register instruction (Status Register bit WEL must equal 1). Once write enabled, the instruction is entered by driving CS# low, sending the instruction code “01h/31h”, and then writing the status register data byte as illustrated in Figure 13 & Figure 14.

To write volatile Status Register bits, a Write Enable for Volatile Status Register (50h) instruction must have been executed prior to the Write Status Register instruction (Status Register bit WEL remains 0). However, SRP1 and LB Bits cannot be changed from 1 to 0 because of the OTP protection for these bits. Upon power off or the execution of Software Reset, the volatile Status Register bit values will be lost, and the non-volatile Status Register bit values will be restored.

During non-volatile Status Register write operation (06h combined with 01h/31h), after CS# is driven high, the self-timed Write Status Register cycle will commence for a time duration of t_W (See “12.6 AC Electrical Characteristics”). While the Write Status Register cycle is in progress, the Read Status Register instruction may still be accessed to check the status of the WIP bit. The WIP bit is a 1 during the Write Status Register cycle and a 0 when the cycle is finished and ready to accept other instructions again. After the Write Status Register cycle has finished, the Write Enable Latch (WEL) bit in the Status Register will be cleared to 0.

During volatile Status Register write operation (50h combined with 01h/31h), after CS# is driven high, the Status Register bits will be refreshed to the new values within the time period of t_{SHSL2} (See “12.6 AC Electrical Characteristics”). WIP bit will remain 0 during the Status Register bit refresh period.

The Write Status Register instruction can be used in both SPI mode and QPI mode. However,

the QE bit cannot be written to 0 when the device is in the QPI mode, because QE=1 is required for the device to enter and operate in the QPI mode.

Refer to section 10 for Status Register description. Factory default for all status Register bits are 0.

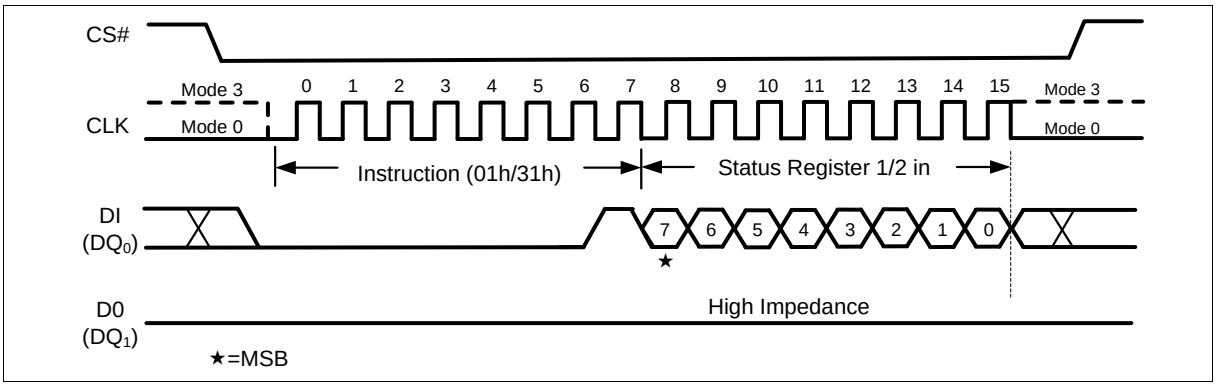


Figure 13 Write Status Register-1/2 Instruction (SPI Mode)

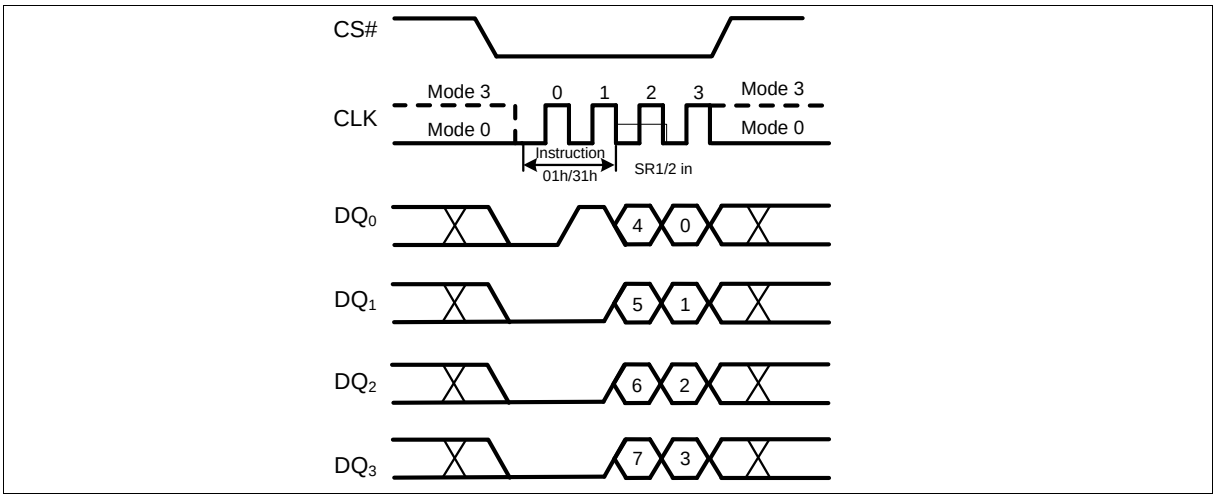


Figure 14 Write Status Register-1/2 Instruction (QPI Mode)

The FM25LQ64I3 is also backward compatible to FMSH's previous generations of serial flash memories, in which the Status Register-1&2 can be written using a single "Write Register-1(01h)" command. To complete the Write Status Register1&2, the CS# pin must be driven high after the sixteenth bit of data that is clocked in as shown in Figure 15. If CS# is driven high after the eighth clock, the Write Status Register (WRSR) instruction will only program the Status Register-1 and the Status Register-2 will not be affected.

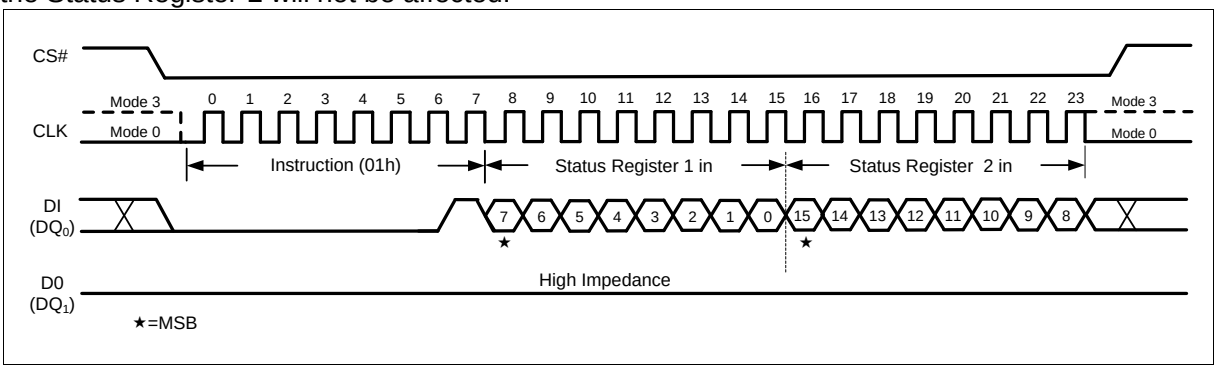


Figure 15 Write Status Register-1/2 Instruction (backward compatible, SPI Mode)

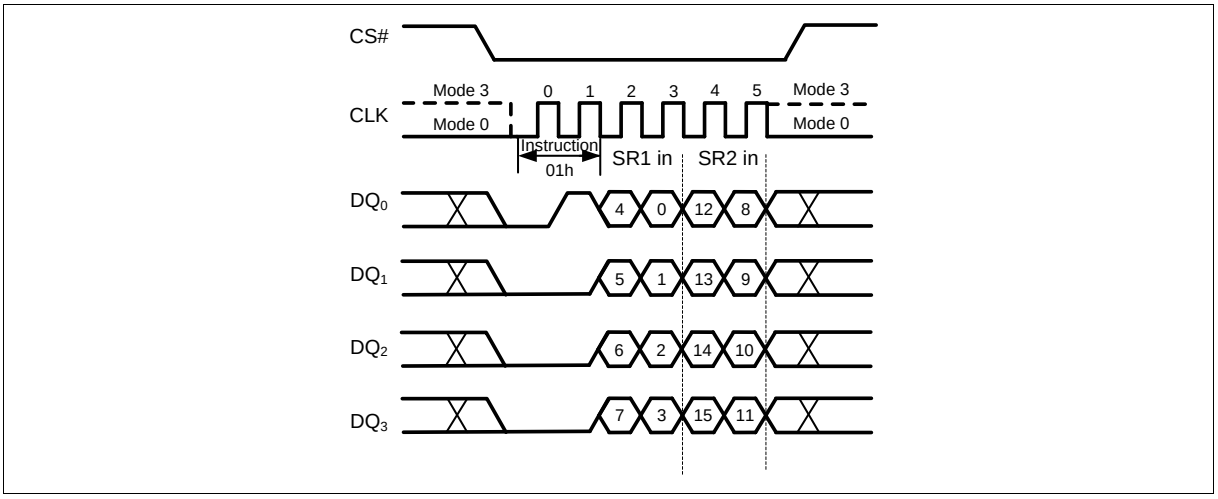


Figure 16 Write Status Register-1/2 Instruction (backward compatible, QPI Mode)

11.2.6. Read Data (03h)

The Read Data instruction allows one or more data bytes to be sequentially read from the memory. The instruction is initiated by driving the CS# pin low and then shifting the instruction code "03h" followed by a 24-bit address A23-A0 into the DI pin. The code and address bits are latched on the rising edge of the CLK pin. After the address is received, the data byte of the addressed memory location will be shifted out on the DO pin at the falling edge of CLK with most significant bit (MSB) first. The address is automatically incremented to the next higher address after each byte of data is shifted out allowing for a continuous stream of data. This means that the entire memory can be accessed with a single instruction as long as the clock continues. The instruction is completed by driving CS# high.

The Read Data instruction sequence is shown in Figure 17. If a Read Data instruction is issued while an Erase, Program or Write cycle is in process (WIP =1) the instruction is ignored and will not have any effect on the current cycle. The Read Data instruction allows clock rates from D.C. to a maximum of f_R (see "12.6 AC Electrical Characteristics").

The Read Data (03h) instruction is only supported in Standard SPI mode.

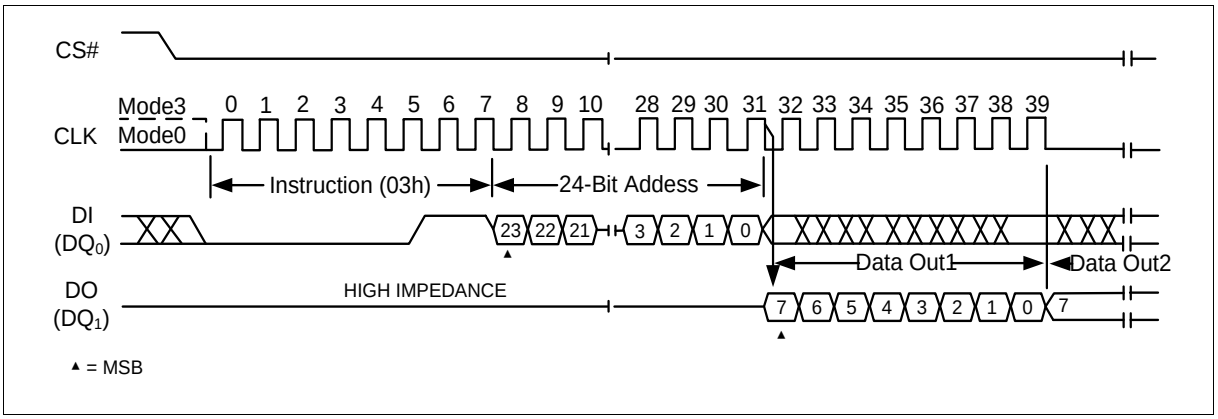


Figure 17 Read Data Instruction (SPI Mode only)

11.2.7. Fast Read (0Bh)

The Fast Read instruction is similar to the Read Data instruction except that it can operate at the highest possible frequency of F_R (see “12.6 AC Electrical Characteristics”). This is accomplished by adding eight “dummy” clocks after the 24-bit address as shown in Figure 18. The dummy clocks allow the devices internal circuits additional time for setting up the initial address. During the dummy clocks the data value on the DI pin is a “don’t care”.

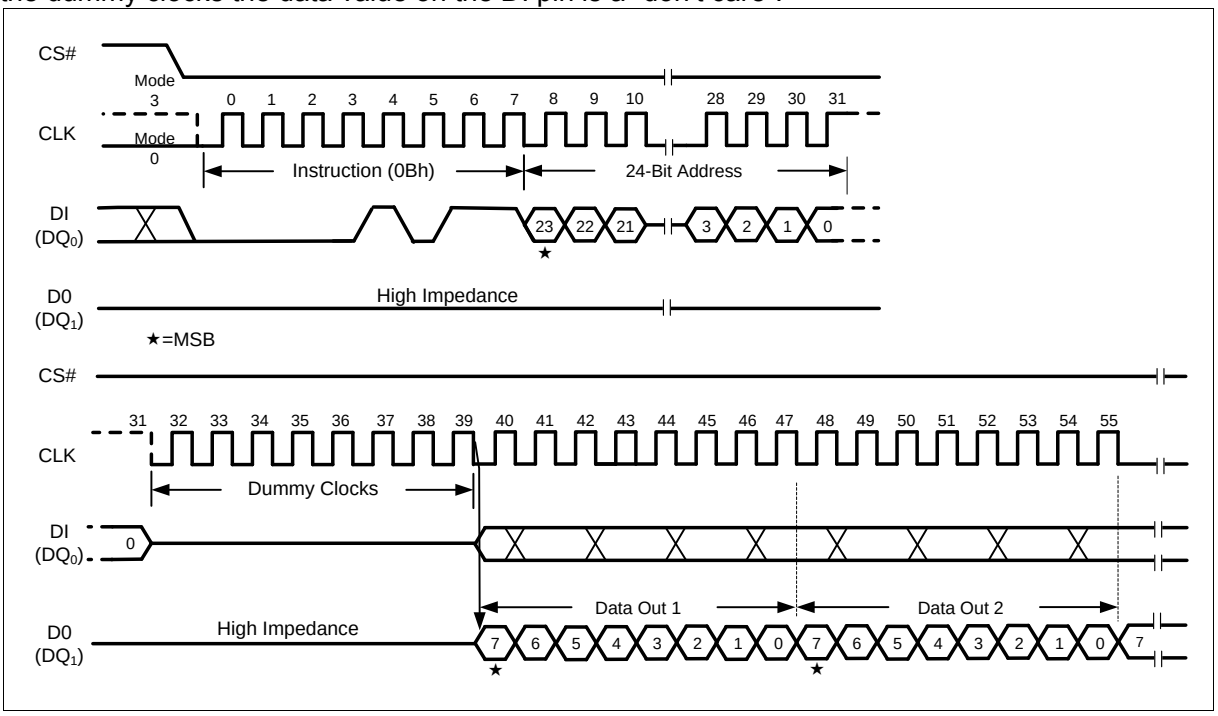


Figure 18 Fast Read Instruction (SPI Mode)

Fast Read (0Bh) in QPI Mode

The Fast Read instruction is also supported in QPI mode. When QPI mode is enabled, the number of dummy clocks is configured by the “Set Read Parameters (C0h)” instruction to accommodate wide range applications with different needs for either maximum Fast Read frequency or minimum data access latency. Depending on the Read Parameter Bits P[5:4] setting, the number of dummy clocks can be configured as either 4, 6, 8 or 10. The default number of dummy clocks upon power up or after a Reset instruction is 4.

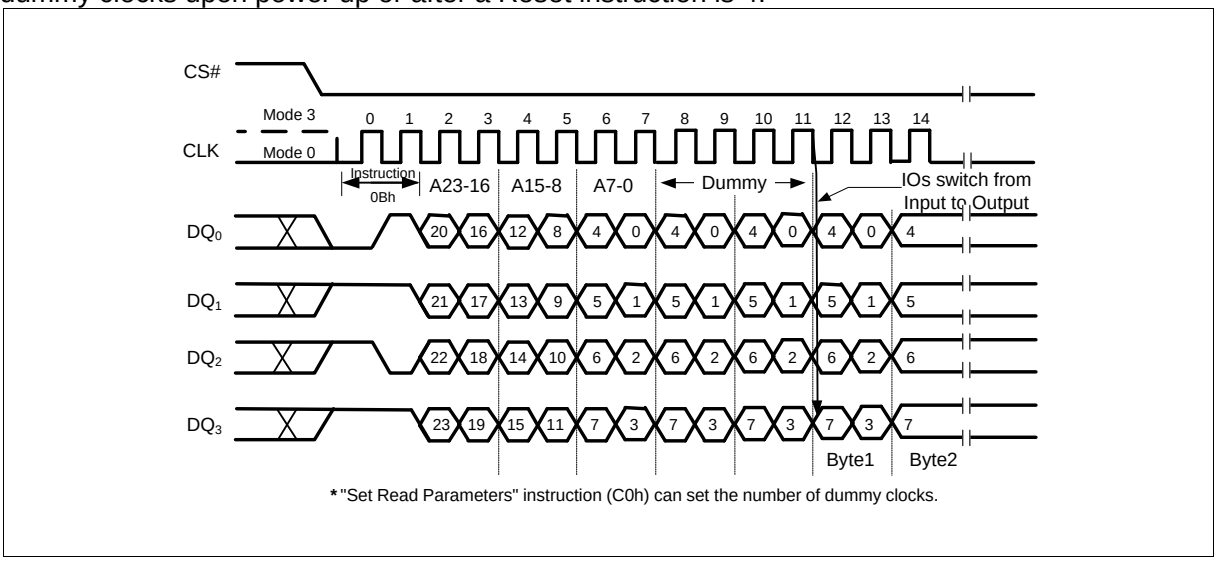


Figure 19 Fast Read Instruction (QPI Mode)

11.2.8. Fast Read Dual Output (3Bh)

The Fast Read Dual Output (3Bh) instruction is similar to the standard Fast Read (0Bh) instruction except that data is output on two pins; DQ_0 and DQ_1. This allows data to be transferred from the FM25LQ64I3 at twice the rate of standard SPI devices. The Fast Read Dual Output instruction is ideal for quickly downloading code from Flash to RAM upon power-up or for applications that cache code-segments to RAM for execution.

Similar to the Fast Read instruction, the Fast Read Dual Output instruction can operate at the highest possible frequency of F_R (see “12.6 AC Electrical Characteristics”). For Fast Read Dual Output instruction, there are eight dummy cycles required after the last address bit is shifted into DI before data begins shifting out of DQ_0 and DQ_1. The dummy clocks allow the device's internal circuits additional time for setting up the initial address. The input data during the dummy clocks is “don’t care”. However, the DQ_0 pin should be high-impedance prior to the falling edge of the first data out clock.

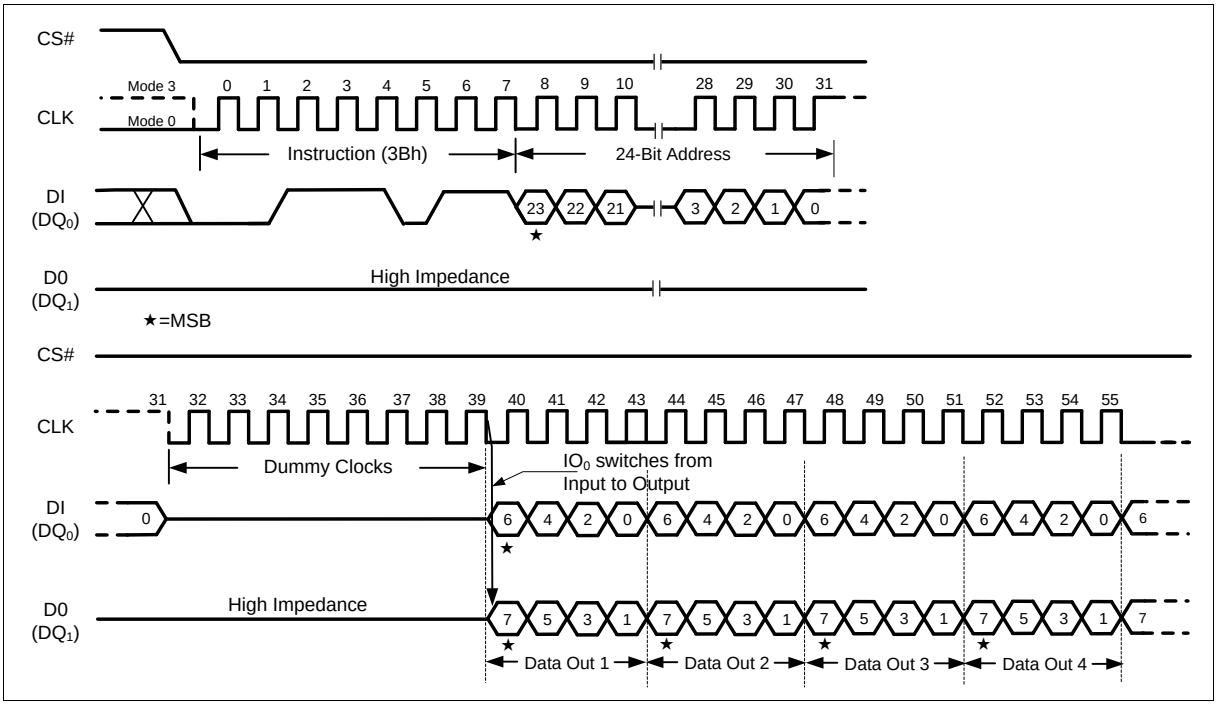


Figure 20 Fast Read Dual Output Instruction (SPI Mode only)

11.2.9. Fast Read Quad Output (6Bh)

The Fast Read Quad Output (6Bh) instruction is similar to the Fast Read Dual Output (3Bh) instruction except that data is output on four pins, DQ_0, DQ_1, DQ_2, and DQ_3. A Quad enable of Status Register-2 must be executed before the device will accept the Fast Read Quad Output Instruction (Status Register bit QE must equal 1). The Fast Read Quad Output Instruction allows data to be transferred from the FM25LQ64I3 at four times the rate of standard SPI devices.

The Fast Read Quad Output instruction can operate at the highest possible frequency of F_R (see "12.6 AC Electrical Characteristics"). For Fast Read Quad Output instruction, there are eight dummy cycles required after the last address bit is shifted into DI before data begins shifting out of DQ_0, DQ_1, DQ_2 and DQ_3. The dummy clocks allow the device's internal circuits additional time for setting up the initial address. The input data during the dummy clocks is "don't care". However, the DQ pins should be high-impedance prior to the falling edge of the first data out clock.

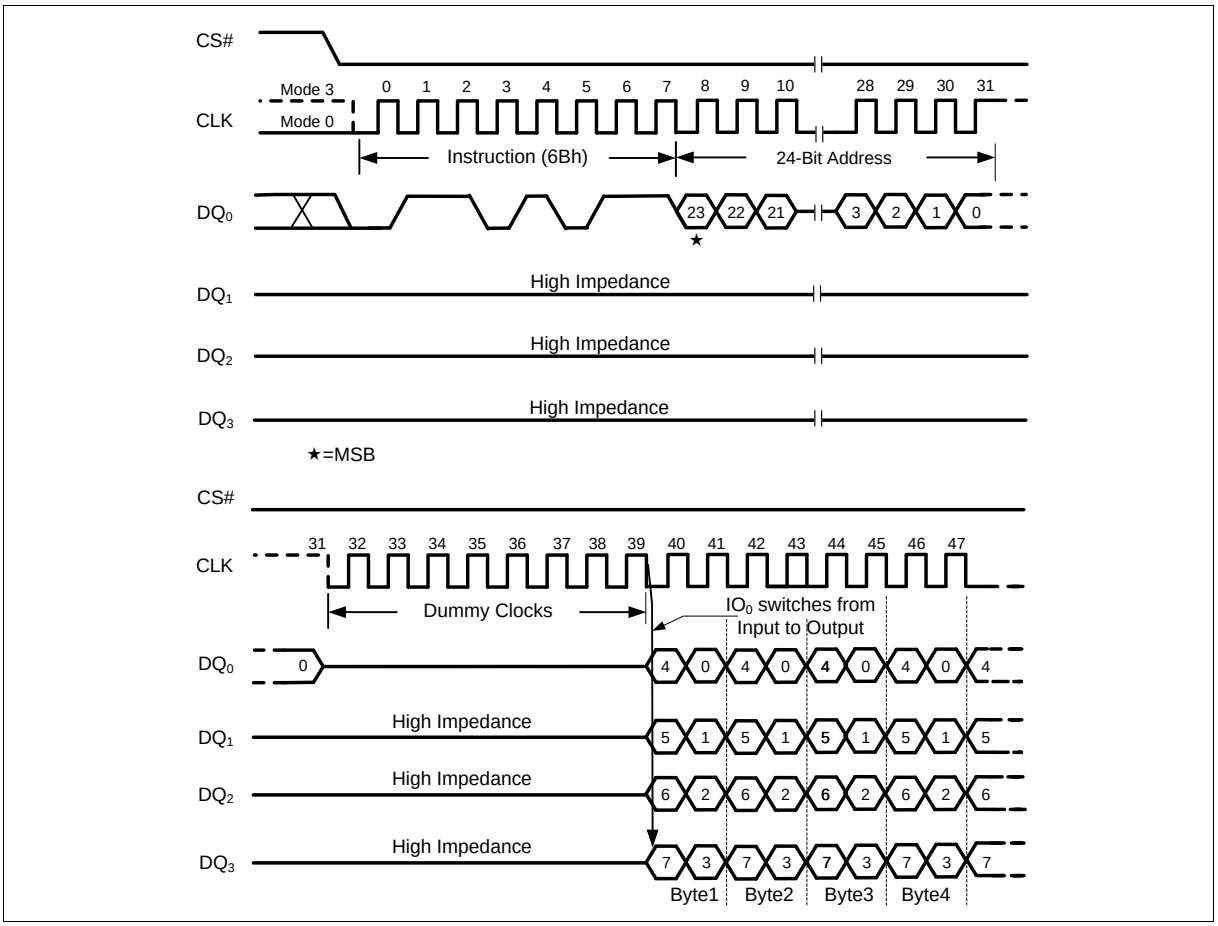


Figure 21 Fast Read Quad Output Instruction (SPI Mode only)

11.2.10. Fast Read Dual I/O (BBh)

The Fast Read Dual I/O (BBh) instruction allows for improved random access while maintaining two I/O pins, DQ_0 and DQ_1. It is similar to the Fast Read Dual Output (3Bh) instruction but with the capability to input the Address bits A23-A0 two bits per clock. This reduced instruction overhead may allow for code execution (XIP) directly from the Dual SPI in some applications.

Fast Read Dual I/O with "Continuous Read Mode"

The Fast Read Dual I/O instruction can further reduce instruction overhead through setting the "Continuous Read Mode" bits (M7-0) after the input Address bits A23-A0, as shown in Figure 22. The upper nibble of the (M7-4) controls the length of the next Fast Read Dual I/O instruction through the inclusion or exclusion of the first byte instruction code. The lower nibble bits of the (M3-0) are don't care ("x"). However, the DQ pins should be high-impedance prior to the falling edge of the first data out clock.

If the "Continuous Read Mode" bits M5-4 = (1,0), then the next Fast Read Dual I/O instruction (after CS# is raised and then lowered) does not require the BBh instruction code, as shown in Figure 23. This reduces the instruction sequence by eight clocks and allows the Read address to be immediately entered after CS# is asserted low. If the "Continuous Read Mode" bits M5-4 do not equal to (1,0), the next instruction (after CS# is raised and then lowered) requires the first byte instruction code, thus returning to normal operation. It is recommended to input FFFFh on DQ_0 for the next instruction (16 clocks), to ensure M4 = 1 and return the device to normal operation.

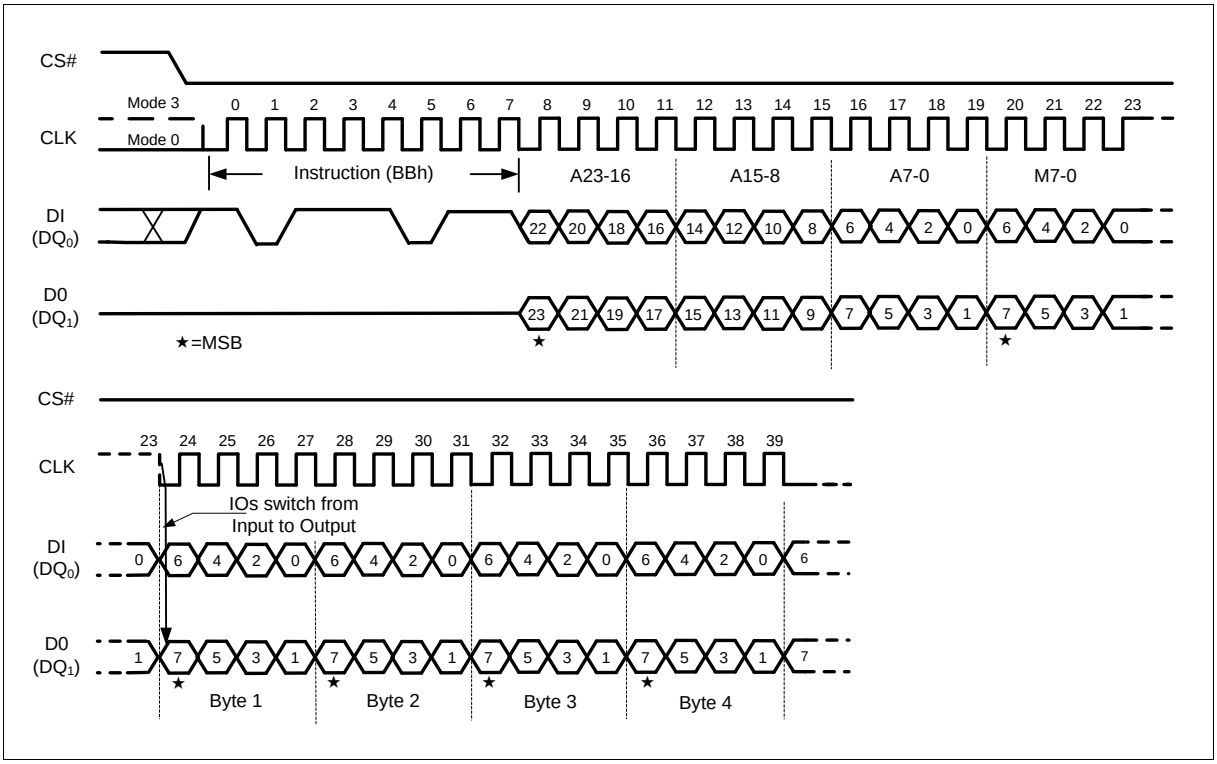


Figure 22 Fast Read Dual I/O Instruction (Initial instruction or previous M5-4 ≠ 10, SPI Mode only)

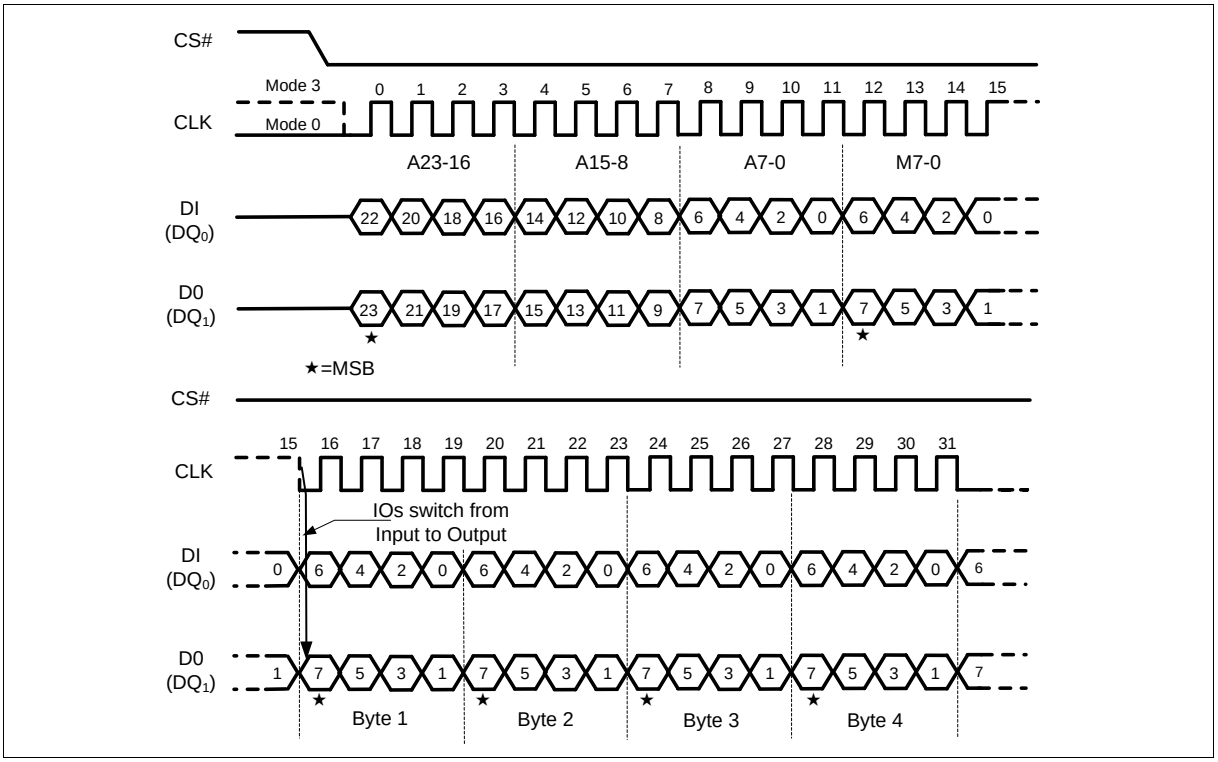


Figure 23 Fast Read Dual I/O Instruction (Previous instruction set M5-4 = 10, SPI Mode only)

11.2.11. Fast Read Quad I/O (EBh)

The Fast Read Quad I/O (EBh) instruction is similar to the Fast Read Dual I/O (BBh) instruction except that address and data bits are input and output through four pins DQ_0, DQ_1, DQ_2 and DQ_3 and four Dummy clocks are required in SPI mode prior to the data output. The Quad I/O dramatically reduces instruction overhead allowing faster random access for code execution (XIP) directly from the Quad SPI. The Quad Enable bit (QE) of Status Register-2 must be set to enable the Fast Read Quad I/O Instruction.

Fast Read Quad I/O with "Continuous Read Mode"

The Fast Read Quad I/O instruction can further reduce instruction overhead through setting the "Continuous Read Mode" bits (M7-0) after the input Address bits A23-A0, as shown in Figure 24. The upper nibble of the (M7-4) controls the length of the next Fast Read Quad I/O instruction through the inclusion or exclusion of the first byte instruction code. The lower nibble bits of the (M3-0) are don't care ("x"). However, the DQ pins should be high-impedance prior to the falling edge of the first data out clock.

If the "Continuous Read Mode" bits M5-4 = (1,0), then the next Fast Read Quad I/O instruction (after CS# is raised and then lowered) does not require the EBh instruction code, as shown in Figure 25. This reduces the instruction sequence by eight clocks and allows the Read address to be immediately entered after CS# is asserted low. If the "Continuous Read Mode" bits M5-4 do not equal to (1, 0), the next instruction (after CS# is raised and then lowered) requires the first byte instruction code, thus returning to normal operation. It is recommended to input FFh on DQ_0 for the next instruction (8 clocks), to ensure M4 = 1 and return the device to normal operation.

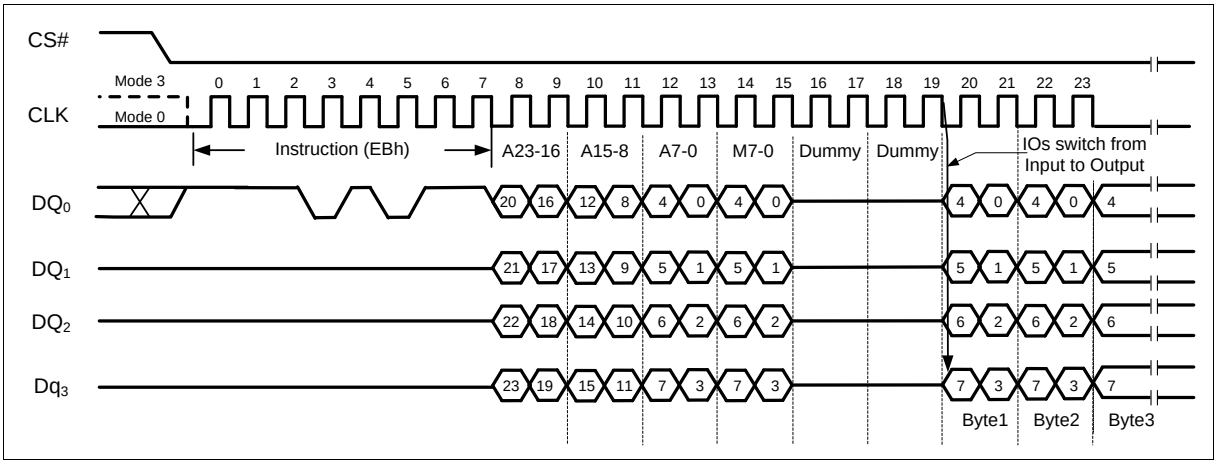


Figure 24 Fast Read Quad I/O Instruction (Initial instruction or previous M5-4≠10, SPI Mode)

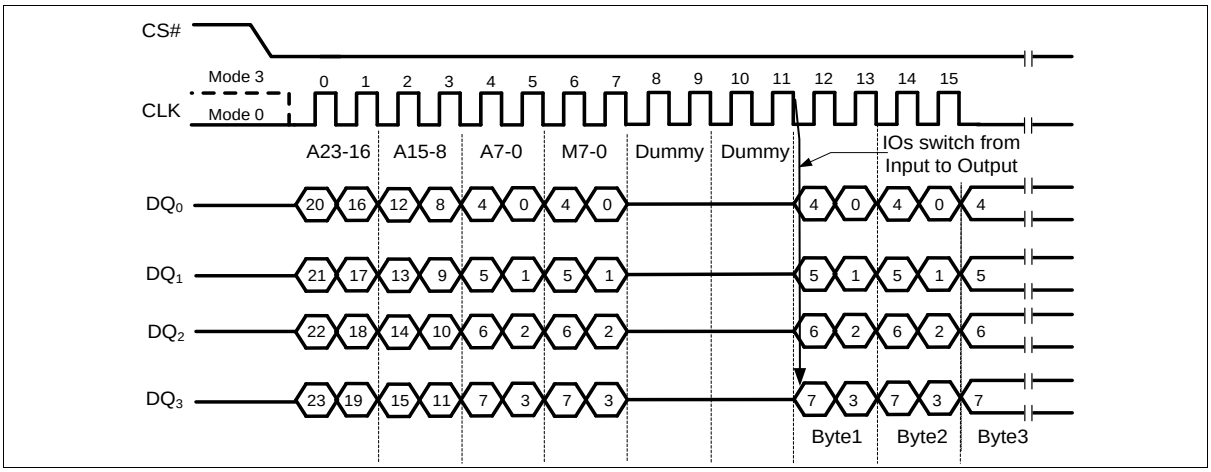


Figure 25 Fast Read Quad I/O Instruction (Previous instruction set M5-4 = 10, SPI Mode)

Fast Read Quad I/O with "8/16/32/64-Byte Wrap Around" in Standard SPI mode

The Fast Read Quad I/O instruction can also be used to access a specific portion within a page by issuing a "Set Burst with Wrap" (77h) command prior to EBh. The "Set Burst with Wrap" (77h) command can either enable or disable the "Wrap Around" feature for the following EBh commands. When "Wrap Around" is enabled, the data being accessed can be limited to either a 8, 16, 32 or 64-byte section of a 256-byte page. The output data starts at the initial address specified in the instruction, once it reaches the ending boundary of the 8/16/32/64-byte section, the output will wrap around to the beginning boundary automatically until CS# is pulled high to terminate the command.

The Burst with Wrap feature allows applications that use cache to quickly fetch a critical address and then fill the cache afterwards within a fixed length (8/16/32/64-byte) of data without issuing multiple read commands.

The "Set Burst with Wrap" instruction allows three "Wrap Bits", W6-4 to be set. The W4 bit is used to enable or disable the "Wrap Around" operation while W6-5 are used to specify the length of the wrap around section within a page. See "11.2.13 Set Burst with Wrap (77h)" for detail descriptions.

Fast Read Quad I/O (EBh) in QPI Mode

The Fast Read Quad I/O instruction is also supported in QPI mode, as shown in Figure 26. When QPI mode is enabled, the number of dummy clocks can be configured as either 4, 6, 8 or 10. In QPI mode, the "Continuous Read Mode" bits M7-M0 are also considered as dummy clocks. The default number of dummy clocks upon power up or after a Reset instruction is 4.

"Continuous Read Mode" feature is also available in QPI mode for Fast Read Quad I/O instruction. Please refer to the description on previous pages for details.

"Wrap Around" feature is not available in QPI mode for Fast Read Quad I/O instruction. To perform a read operation with fixed data length wrap around in QPI mode, a dedicated "Burst Read with Wrap" (0CH) command must be used.

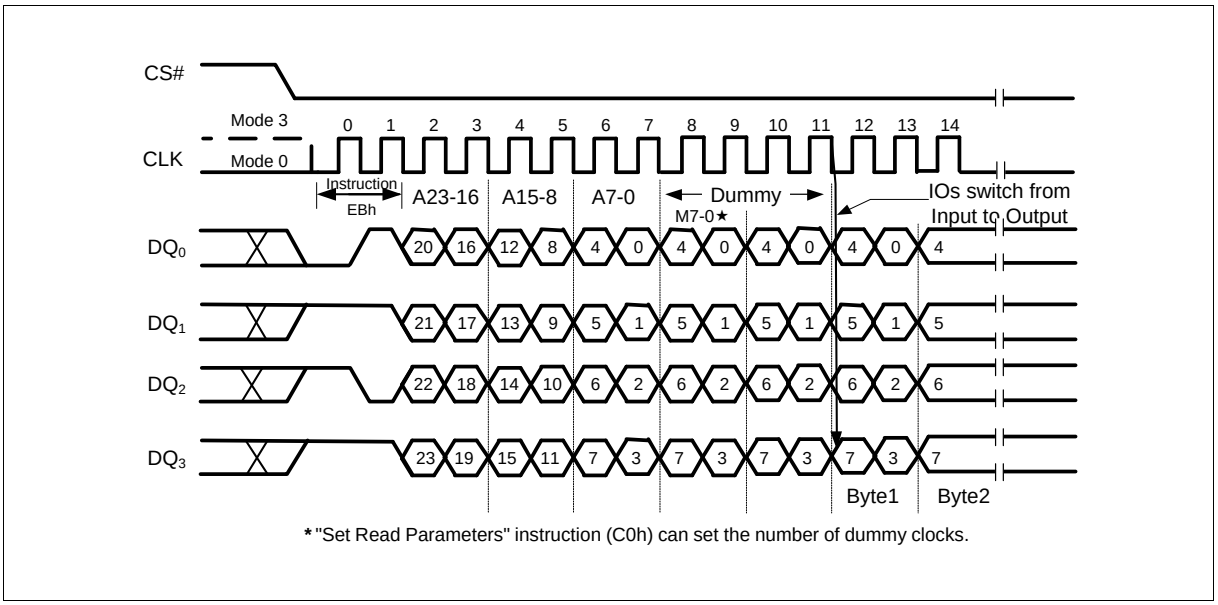


Figure 26 Fast Read Quad I/O Instruction (Initial instruction or previous M5-4≠10, QPI Mode)

11.2.12. DTR Fast Read Quad I/O (EDh)

The DTR Fast Read Quad I/O (EDh) instruction is similar to the Fast Read Quad I/O (EBh) instruction except that the address input and the data output require DTR (Double Transfer Rate) operation. The address is latched on both rising and falling edge of CLK, and data shift out on both rising and falling edge of CLK. Quad Enable bit (QE) of Status Register-2 must be set to enable the Fast Read Quad I/O Instruction.10 Dummy clocks are required in SPI mode prior to the data output for EDh instruction. In QPI mode, the Dummy clocks can be configured by C0h instruction.

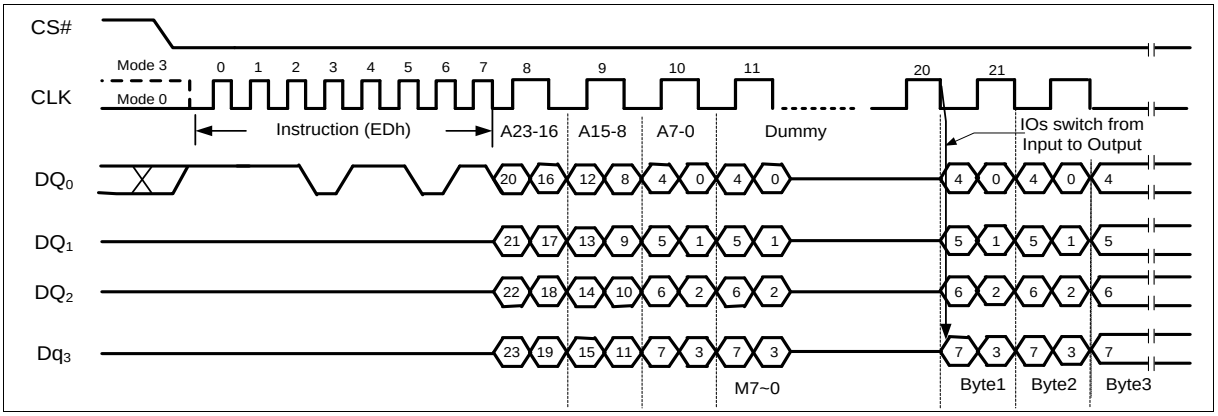


Figure 31 DTR Fast Read Quad I/O Instruction

Quad I/O DTR Read with "Continuous Read Mode"

The Quad I/O DTR Read command can further reduce command overhead through setting the "Continuous Read Mode" bits (M7-0) after the input address. If the "Continuous Read Mode" bits (M5-4) = (1, 0), then the next Quad I/O DTR Read command (after CS# is raised and then lowered) does not require the EDH command code. If the "Continuous Read Mode" bits (M5-4) do not equal to (1, 0), the next command requires the first EDH command code, thus returning to normal operation. The only way to quit the Quad I/O DTR Continuous Read Mode" is to set the "Continuous Read Mode" bits (M5-4) not equal to (1, 0).

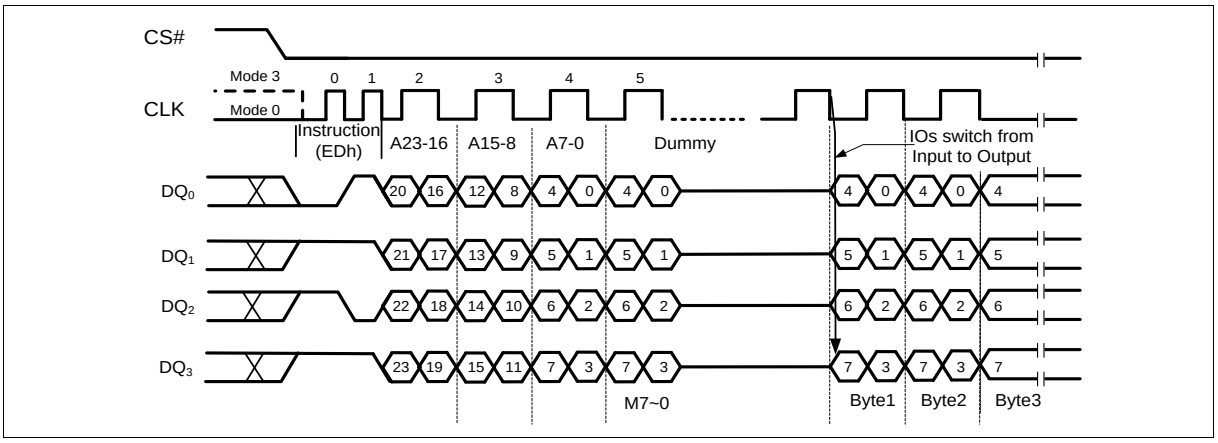


Figure 32 DTR Fast Read Quad I/O Instruction (Initial instruction or previous M5-4≠10, QPI Mode)

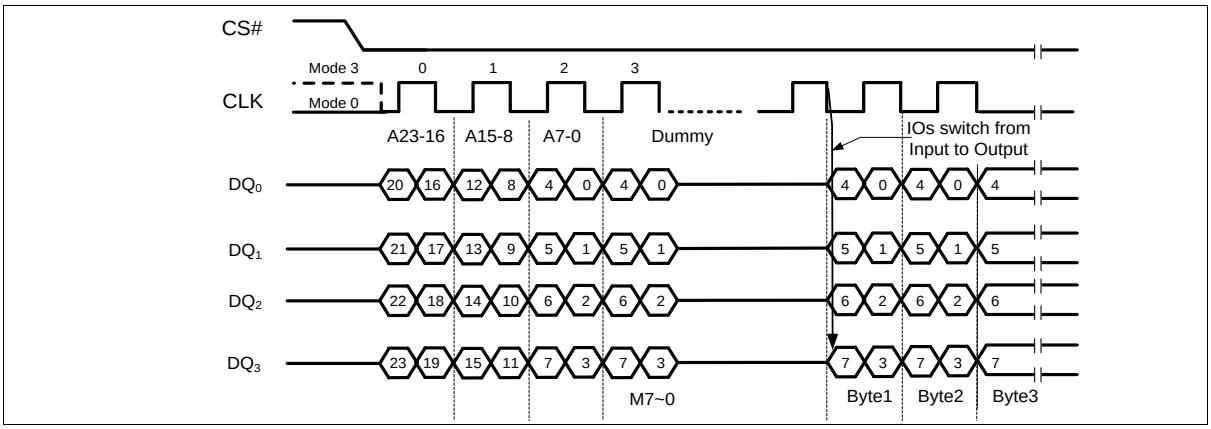


Figure 33 Fast Read Quad I/O Instruction (Previous instruction set M5-4 = 10, SPI Mode)

11.2.13. Set Burst with Wrap (77h)

The Set Burst with Wrap (77h) instruction is used in conjunction with "Fast Read Quad I/O" instructions to access a fixed length of 8/16/32/64-byte section within a 256-byte page. Certain applications can benefit from this feature and improve the overall system code execution performance.

Similar to a Quad I/O instruction, the Set Burst with Wrap instruction is initiated by driving the CS# pin low and then shifting the instruction code "77h" followed by 24 dummy bits and 8 "Wrap Bits", W7-0. The instruction sequence is shown in Figure 27. Wrap bit W7 and the lower nibble W3-0 are not used.

W6, W5	W4 = 0		W4 =1 (default)	
	Wrap Around	Wrap Length	Wrap Around	Wrap Length
0 0	Yes	8-byte	No	N/A
0 1	Yes	16-byte	No	N/A
1 0	Yes	32-byte	No	N/A
1 1	Yes	64-byte	No	N/A

Once W6-4 is set by a Set Burst with Wrap instruction, all the following "Fast Read Quad I/O" instructions will use the W6-4 setting to access the 8/16/32/64-byte section within any page. To exit the "Wrap Around" function and return to normal read operation, another Set Burst with Wrap instruction should be issued to set W4 = 1. The default value of W4 upon power on is 1. In the case of a system Reset while W4 = 0, it is recommended that the controller issues a Set Burst with Wrap instruction to reset W4 = 1 prior to any normal Read instructions since FM25LQ64I3 does not have a hardware Reset Pin.

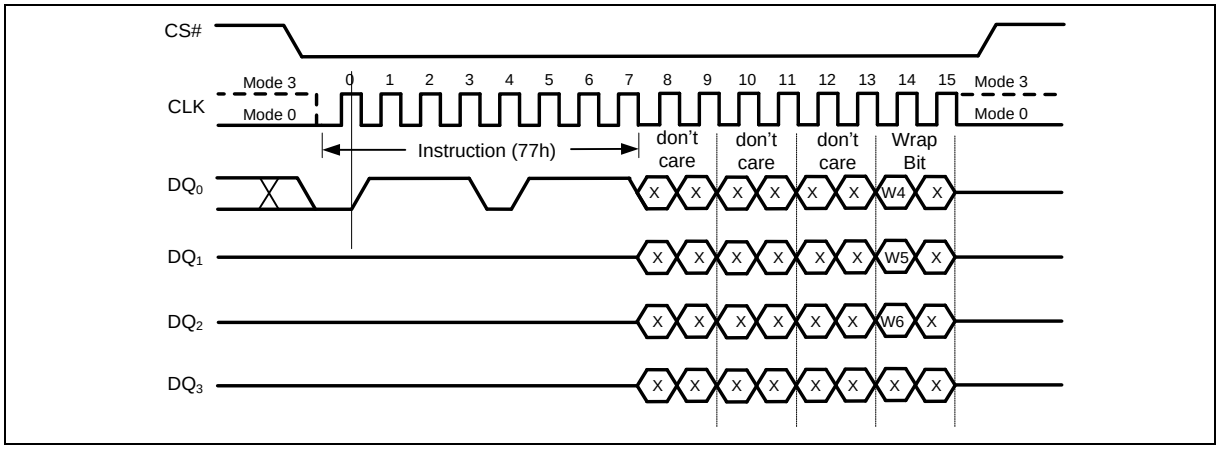


Figure 27 Set Burst with Wrap Instruction for SPI Mode

11.2.14. Page Program (02h)

The Page Program instruction allows from one byte to 256 bytes (a page) of data to be programmed at previously erased (FFh) memory locations. A Write Enable instruction must be executed before the device will accept the Page Program Instruction (Status Register bit WEL= 1). The instruction is initiated by driving the CS# pin low then shifting the instruction code “02h” followed by a 24-bit address A23-A0 and at least one data byte, into the DI pin. The CS# pin must be held low for the entire length of the instruction while data is being sent to the device. The Page Program instruction sequence is shown in Figure 28 and Figure 29.

If an entire 256 byte page is to be programmed, the last address byte (the 8 least significant address bits) should be set to 0. If the last address byte is not zero, and the number of clocks exceeds the remaining page length, the addressing will wrap to the beginning of the page. In some cases, less than 256 bytes (a partial page) can be programmed without having any effect on other bytes within the same page. One condition to perform a partial page program is that the number of clocks can not exceed the remaining page length. If more than 256 bytes are sent to the device the addressing will wrap to the beginning of the page and overwrite previously sent data.

As with the write and erase instructions, the CS# pin must be driven high after the eighth bit of the last byte has been latched. If this is not done the Page Program instruction will not be executed. After CS# is driven high, the self-timed Page Program instruction will commence for a time duration of t_{PP} (See “12.6 AC Electrical Characteristics”). While the Page Program cycle is in progress, the Read Status Register instruction may still be accessed for checking the status of the WIP bit. The WIP bit is a 1 during the Page Program cycle and becomes a 0 when the cycle is finished and the device is ready to accept other instructions again. After the Page Program cycle has finished the Write Enable Latch (WEL) bit in the Status Register is cleared to 0. The Page Program instruction will not be executed if the addressed page is protected by the Block Protect (CMP, SEC, TB, BP2, BP1 and BP0) bits or the Individual Block/Sector Locks.

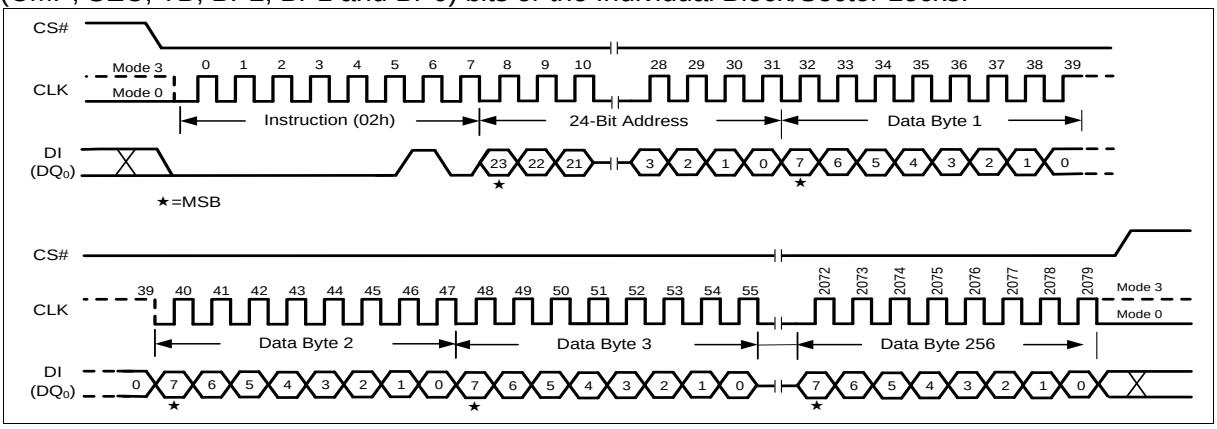


Figure 28 Page Program Instruction (SPI Mode)

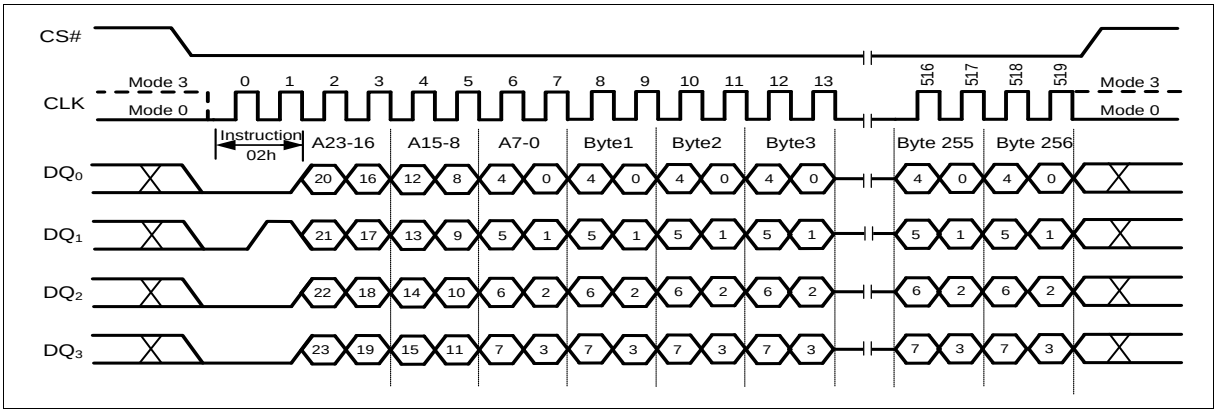


Figure 29 Page Program Instruction (QPI Mode)

11.2.15. Quad Input Page Program (32h)

The Quad Page Program instruction allows up to 256 bytes of data to be programmed at previously erased (FFh) memory locations using four pins: DQ_0, DQ_1, DQ_2, and DQ_3. The Quad Page Program can improve performance for PROM Programmer and applications that have slow clock speeds <5MHz. Systems with faster clock speed will not realize much benefit for the Quad Page Program instruction since the inherent page program time is much greater than the time it take to clock-in the data.

To use Quad Page Program the Quad Enable in Status Register-2 must be set (QE=1). A Write Enable instruction must be executed before the device will accept the Quad Page Program instruction (Status Register-1, WEL=1). The instruction is initiated by driving the CS# pin low then shifting the instruction code “32h” followed by a 24-bit address A23-A0 and at least one data byte, into the DQ pins. The CS# pin must be held low for the entire length of the instruction while data is being sent to the device. All other functions of Quad Page Program are identical to standard Page Program. The Quad Page Program instruction sequence is shown in Figure 30.

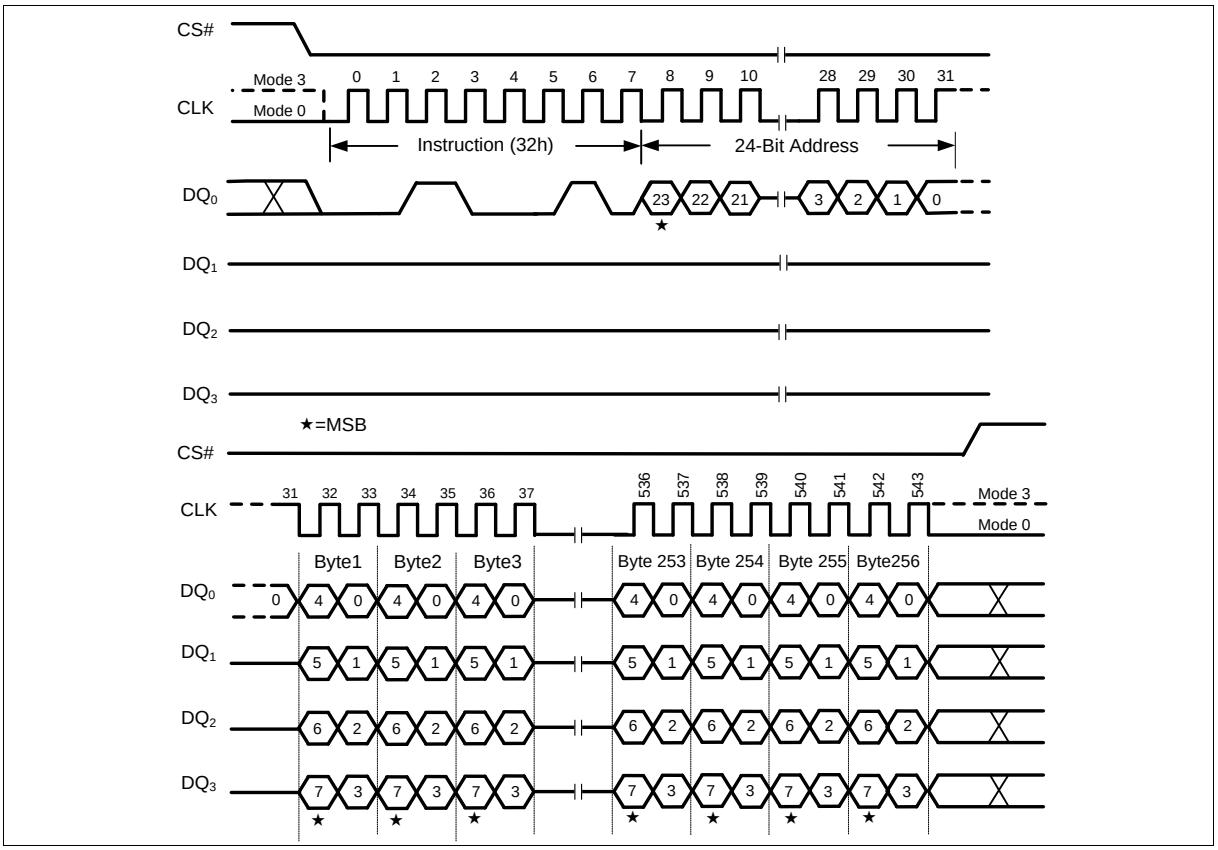


Figure 30 Quad Input Page Program Instruction (SPI Mode only)

11.2.16. Sector Erase (20h)

The Sector Erase instruction sets all memory within a specified sector (4K-bytes) to the erased state of all 1s (FFh). A Write Enable instruction must be executed before the device will accept the Sector Erase Instruction (Status Register bit WEL must equal 1). The instruction is initiated by driving the CS# pin low and shifting the instruction code “20h” followed a 24-bit sector address A23-A0 (see Figure 1). The Sector Erase instruction sequence is shown in Figure 31 & Figure 32.

The CS# pin must be driven high after the eighth bit of the last byte has been latched. If this is not done the Sector Erase instruction will not be executed. After CS# is driven high, the self-timed Sector Erase instruction will commence for a time duration of t_{SE} (See “12.6 AC Electrical Characteristics”). While the Sector Erase cycle is in progress, the Read Status Register instruction may still be accessed for checking the status of the WIP bit. The WIP bit is a 1 during the Sector Erase cycle and becomes a 0 when the cycle is finished and the device is ready to accept other instructions again. After the Sector Erase cycle has finished the Write Enable Latch (WEL) bit in the Status Register is cleared to 0. The Sector Erase instruction will not be executed if the addressed page is protected by the Block Protect (CMP, SEC, TB, BP2, BP1 and BP0) bits or the Individual Block/Sector Locks (see Table 3 Status Register Memory Protection).

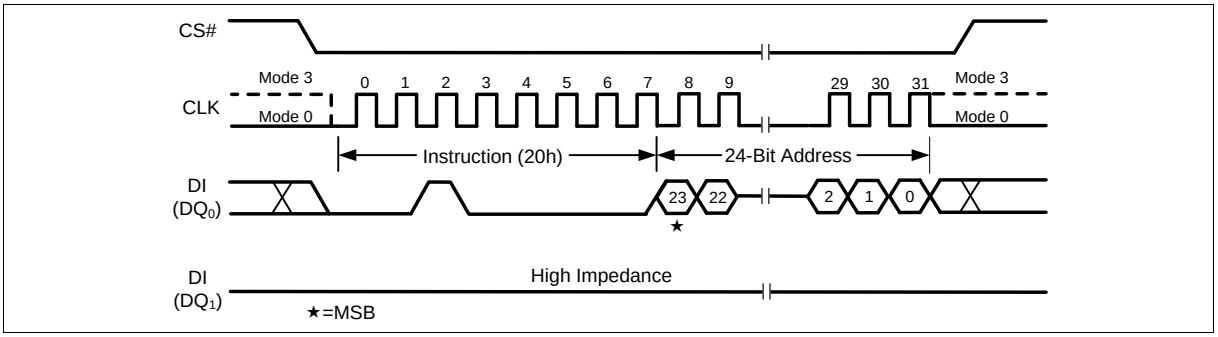


Figure 31 Sector Erase Instruction (SPI Mode)

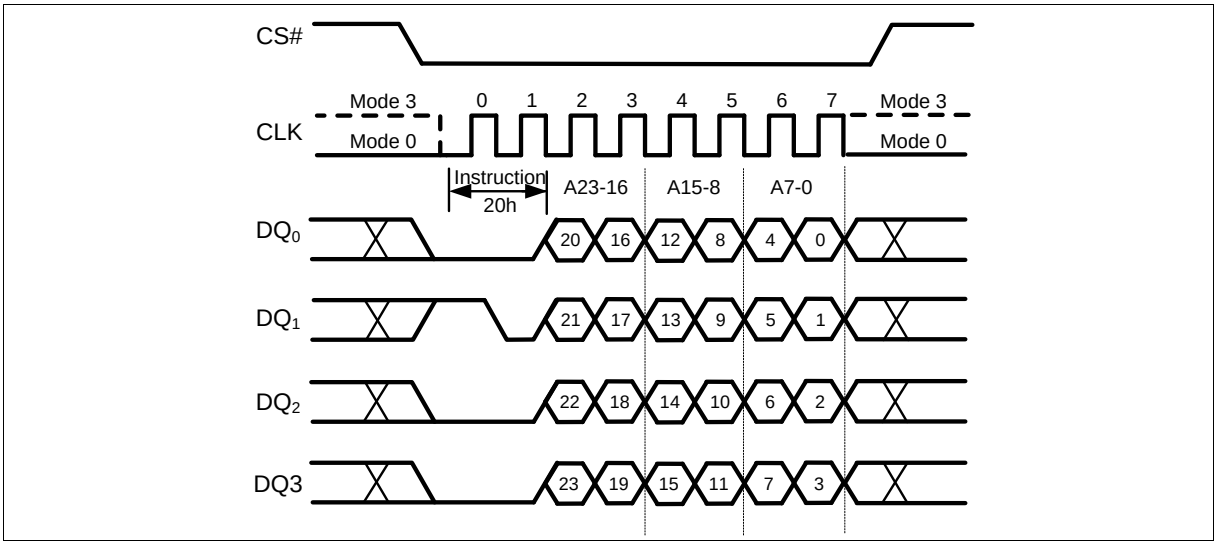


Figure 32 Sector Erase Instruction (QPI Mode)

11.2.17. 32KB Block Erase (BE32) (52h)

The 32KB Block Erase instruction sets all memory within a specified block (32K-bytes) to the erased state of all 1s (FFh). A Write Enable instruction must be executed before the device will accept the Block Erase Instruction (Status Register bit WEL must equal 1). The instruction is initiated by driving the CS# pin low and shifting the instruction code “52h” followed a 24-bit block address A23-A0. The Block Erase instruction sequence is shown in Figure 33 & Figure 34.

The CS# pin must be driven high after the eighth bit of the last byte has been latched. If this is not done the Block Erase instruction will not be executed. After CS# is driven high, the self-timed Block Erase instruction will commence for a time duration of t_{BE1} (See “12.6 AC Electrical Characteristics). While the Block Erase cycle is in progress, the Read Status Register instruction may still be accessed for checking the status of the WIP bit. The WIP bit is a 1 during the Block Erase cycle and becomes a 0 when the cycle is finished and the device is ready to accept other instructions again. After the Block Erase cycle has finished the Write Enable Latch (WEL) bit in the Status Register is cleared to 0. The Block Erase instruction will not be executed if the addressed page is protected by the Block Protect (CMP, SEC, TB, BP2, BP1 and BP0) bits or the Individual Block/Sector Locks.

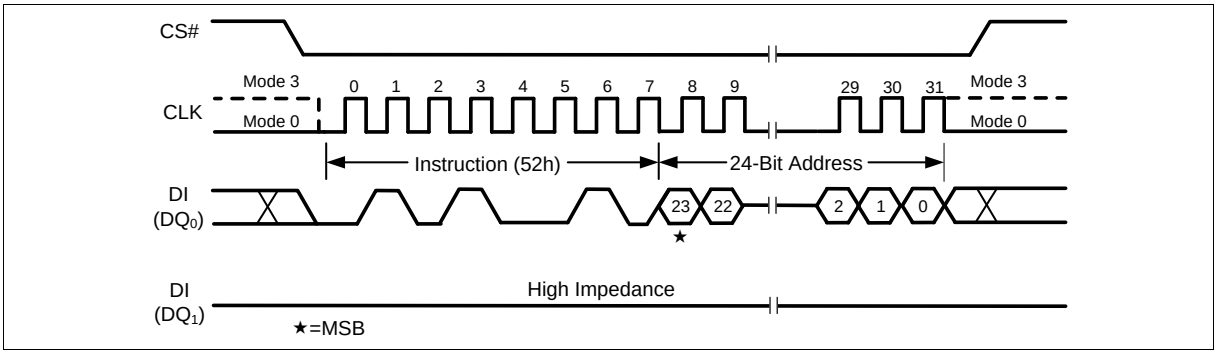


Figure 33 32KB Block Erase Instruction (SPI Mode)

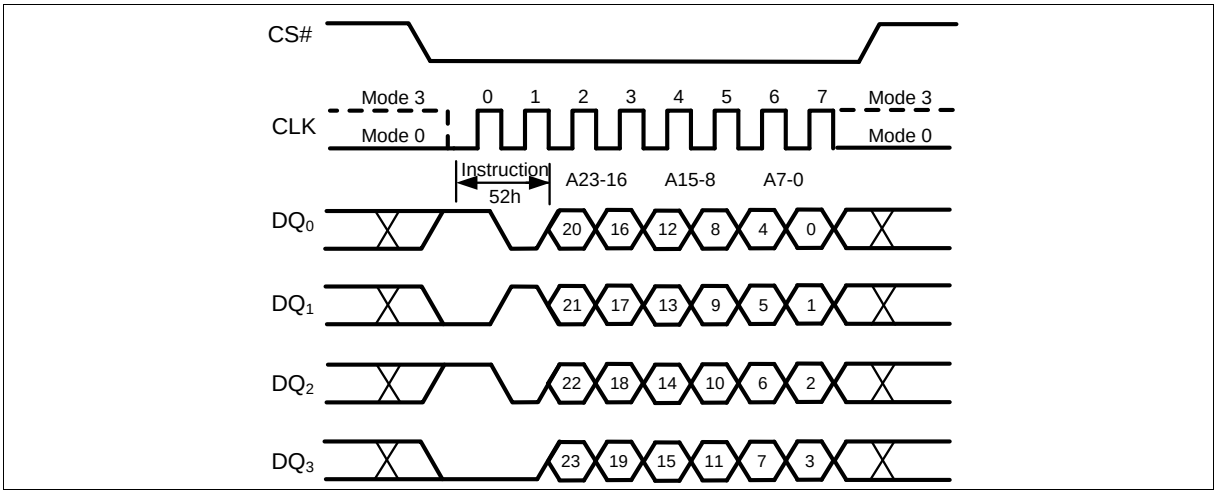


Figure 34 32KB Block Erase Instruction (QPI Mode)

11.2.18. 64KB Block Erase (BE) (D8h)

The 64KB Block Erase instruction sets all memory within a specified block (64K-bytes) to the erased state of all 1s (FFh). A Write Enable instruction must be executed before the device will accept the Block Erase Instruction (Status Register bit WEL must equal 1). The instruction is initiated by driving the CS# pin low and shifting the instruction code "D8h" followed a 24-bit block address A23-A0. The Block Erase instruction sequence is shown in Figure 35 & Figure 36.

The CS# pin must be driven high after the eighth bit of the last byte has been latched. If this is not done the Block Erase instruction will not be executed. After CS# is driven high, the self-timed Block Erase instruction will commence for a time duration of t_{BE} (See 12.6 AC Electrical Characteristics"). While the Block Erase cycle is in progress, the Read Status Register instruction may still be accessed for checking the status of the WIP bit. The WIP bit is a 1 during the Block Erase cycle and becomes a 0 when the cycle is finished and the device is ready to accept other instructions again. After the Block Erase cycle has finished the Write Enable Latch (WEL) bit in the Status Register is cleared to 0. The Block Erase instruction will not be executed if the addressed page is protected by the Block Protect (CMP, SEC, TB, BP2, BP1 and BP0) bits or the Individual Block/Sector Locks.

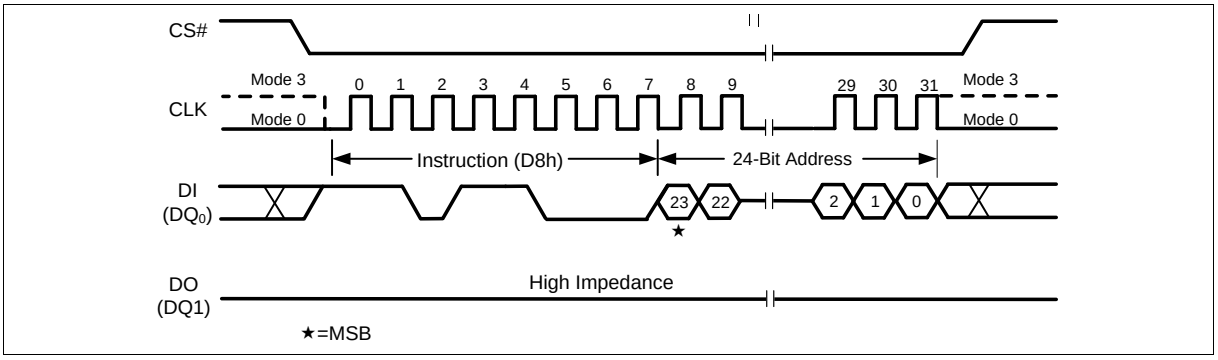


Figure 35 64KB Block Erase Instruction (SPI Mode)

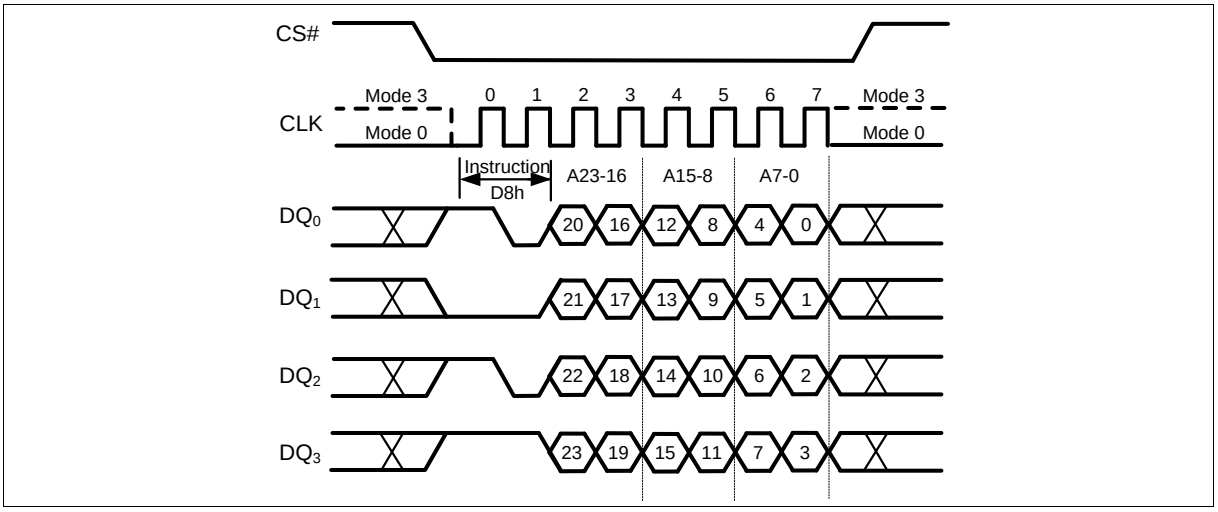


Figure 36 64KB Block Erase Instruction (QPI Mode)

11.2.19. Chip Erase (CE) (C7h / 60h)

The Chip Erase instruction sets all memory within the device to the erased state of all 1s (FFh). A Write Enable instruction must be executed before the device will accept the Chip Erase Instruction (Status Register bit WEL must equal 1). The instruction is initiated by driving the CS# pin low and shifting the instruction code “C7h” or “60h”. The Chip Erase instruction sequence is shown in Figure 37.

The CS# pin must be driven high after the eighth bit has been latched. If this is not done the Chip Erase instruction will not be executed. After CS# is driven high, the self-timed Chip Erase instruction will commence for a time duration of t_{CE} (See “12.6 AC Electrical Characteristics”). While the Chip Erase cycle is in progress, the Read Status Register instruction may still be accessed to check the status of the WIP bit. The WIP bit is a 1 during the Chip Erase cycle and becomes a 0 when finished and the device is ready to accept other instructions again. After the Chip Erase cycle has finished the Write Enable Latch (WEL) bit in the Status Register is cleared to 0. The Chip Erase instruction will not be executed if any page is protected by the Block Protect (CMP, SEC, TB, BP2, BP1 and BP0) bits or the Individual Block/Sector Locks.

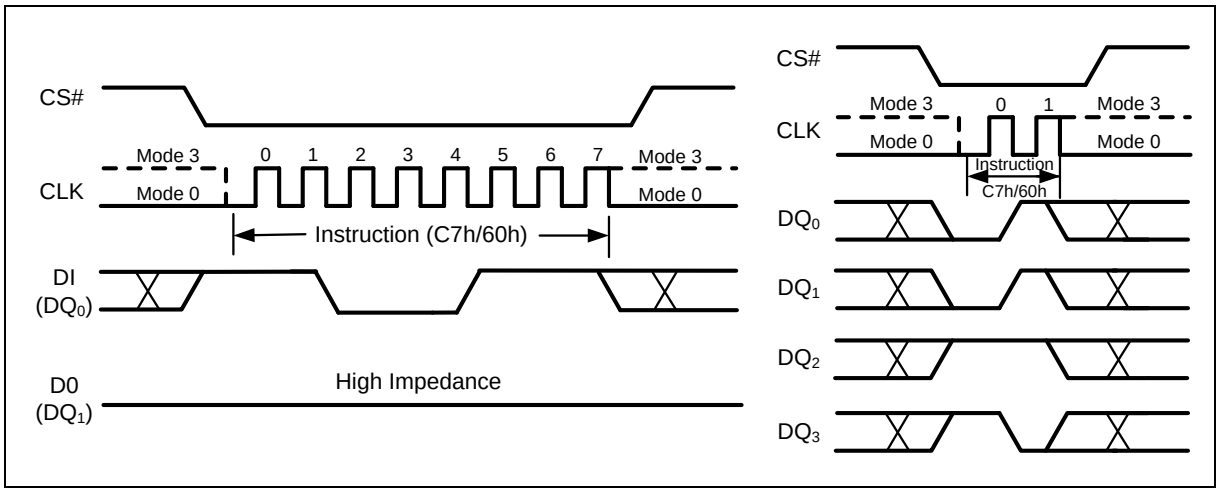


Figure 37 Chip Erase Instruction for SPI Mode (left) or QPI Mode (right)

11.2.20. Erase / Program Suspend (75h)

The Erase/Program Suspend instruction “75h”, allows the system to interrupt a Sector or Block Erase operation or a Page Program operation and then read data from any other sectors or blocks. The Erase/Program Suspend instruction sequence is shown in Figure 38 & Figure 39.

The Write Status Register instruction (01h, 31h), Program and Erase instructions are not allowed during Program/Erase Suspend. Erase Suspend is valid only during the Sector or Block erase operation. If written during the Chip Erase operation, the Suspend instruction is ignored.

The Erase/Program Suspend instruction “75h” will be accepted by the device only if the SUS bit in the Status Register equals to 0 and the WIP bit equals to 1 while a Sector or Block Erase or a Page Program operation is on-going. If the SUS bit equals to 1 or the WIP bit equals to 0, the Suspend instruction will be ignored by the device. A maximum of time of “t_{SUS}” (See”12.6 AC Electrical Characteristics”) is required to suspend the erase or program operation. The WIP bit in the Status Register will be cleared from 1 to 0 within “t_{SUS}” and the SUS bit in the Status Register will be set from 0 to 1 immediately after Erase/Program Suspend. For a previously resumed Erase/Program operation, it is also required that the Suspend instruction “75h” is not issued earlier than a minimum of time of “t_{SUS}” following the preceding Resume instruction “7Ah”.

Unexpected power off during the Erase/Program suspend state will reset the device and release the suspend state. SUS bit in the Status Register will also reset to 0. The data within the page, sector or block that was being suspended may become corrupted. It is recommended for the user to implement system design techniques against the accidental power interruption and preserve data integrity during erase/program suspend state.

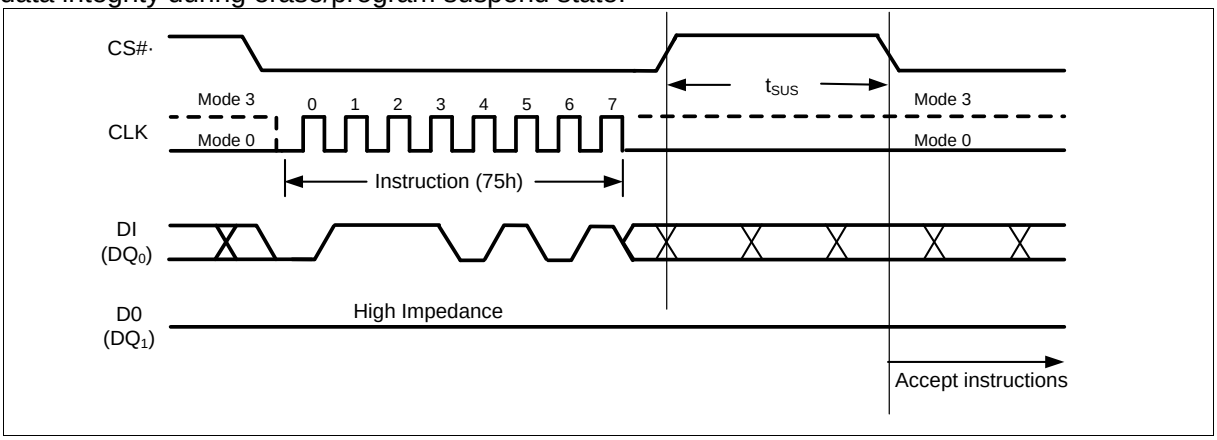


Figure 38 Erase/Program Suspend Instruction (SPI Mode)

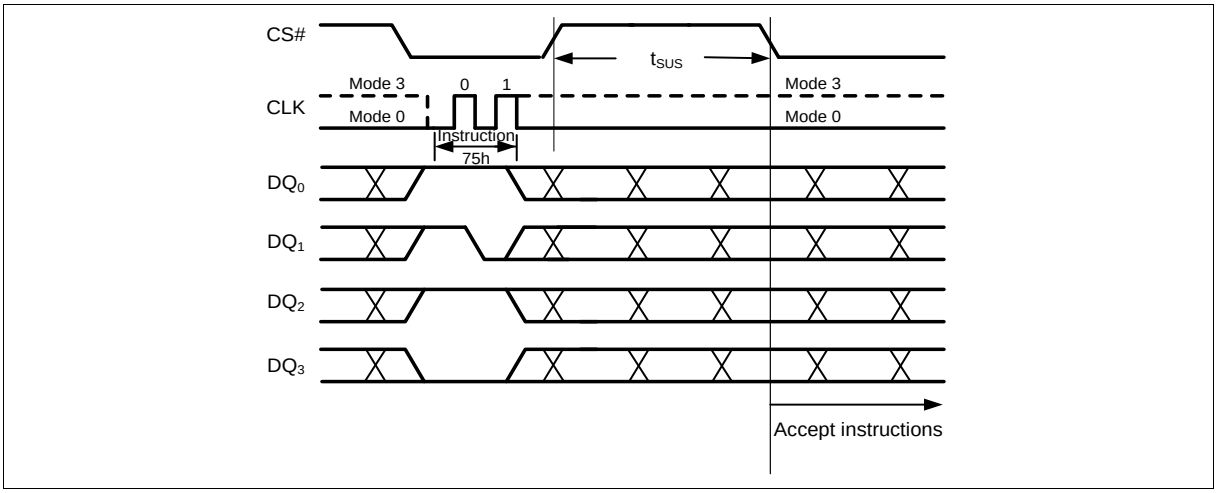


Figure 39 Erase/Program Suspend Instruction (QPI Mode)

11.2.21. Erase / Program Resume (7Ah)

The Erase/Program Resume instruction “7Ah” must be written to resume the Sector or Block Erase operation or the Page Program operation after an Erase/Program Suspend. The Resume instruction “7Ah” will be accepted by the device only if the SUS bit in the Status Register equals to 1 and the WIP bit equals to 0. After issued the SUS bit will be cleared from 1 to 0 immediately, the WIP bit will be set from 0 to 1 within 200ns and the Sector or Block will complete the erase operation or the page will complete the program operation. If the SUS bit equals to 0 or the WIP bit equals to 1, the Resume instruction “7Ah” will be ignored by the device. The Erase/Program Resume instruction sequence is shown in Figure 40 & Figure 41.

Resume instruction is ignored if the previous Erase/Program Suspend operation was interrupted by unexpected power off. It is also required that a subsequent Erase/Program Suspend instruction not to be issued within a minimum of time of “t_{SUS}” following a previous Resume instruction.

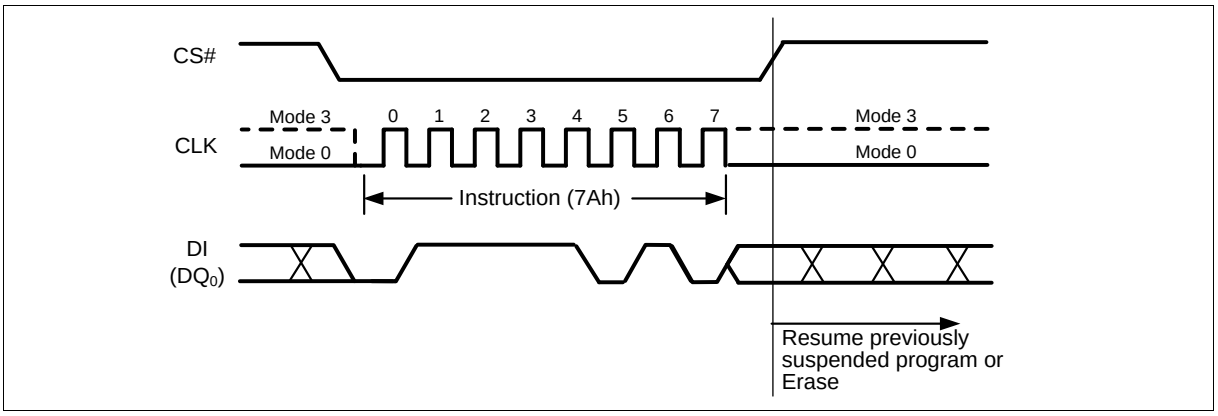


Figure 40 Erase/Program Resume Instruction (SPI Mode)

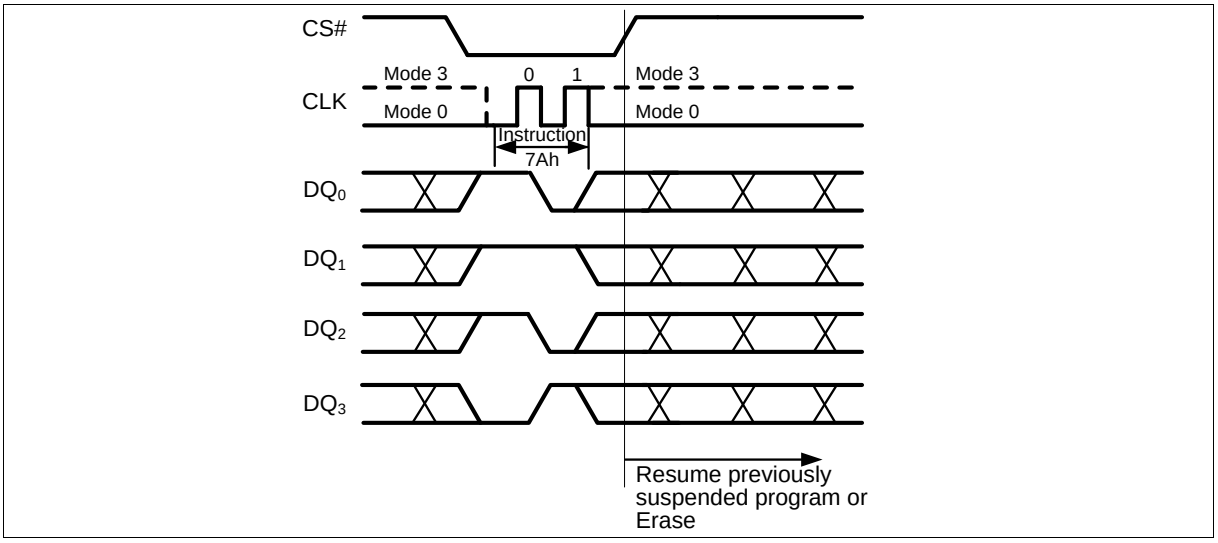


Figure 41 Erase/Program Resume Instruction (QPI Mo

11.2.22. Deep Power-down (B9h)

Although the standby current during normal operation is relatively low, standby current can be further reduced with the Power-down instruction. The lower power consumption makes the Power-down instruction especially useful for battery powered applications (See I_{CC1} and I_{CC2} in "12.4 DC Electrical Characteristics"). The instruction is initiated by driving the CS# pin low and shifting the instruction code "B9h" as shown in Figure 42 & Figure 43.

The CS# pin must be driven high after the eighth bit has been latched. If this is not done the Power-down instruction will not be executed. After CS# is driven high, the power-down state will enter within the time duration of t_{DP} (See "12.6 AC Electrical Characteristics"). While in the power-down state only the Release from Power- down / Device ID and software reset instruction will be recognized. All other instructions are ignored. This includes the Read Status Register instruction, which is always available during normal operation. Ignoring all but two instructions makes the Power Down state a useful condition for securing maximum write protection. The device always powers-up in the normal operation with the standby current of I_{CC1}.

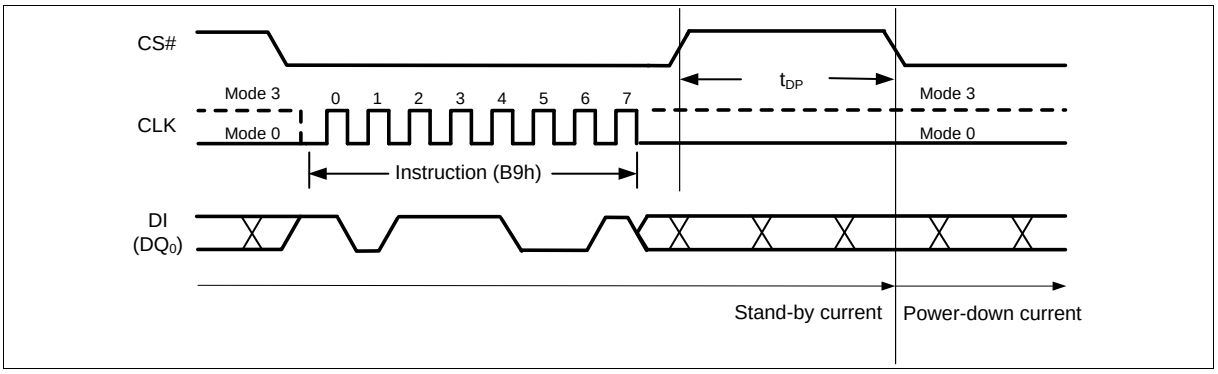


Figure 42 Deep Power-down Instruction (SPI Mode)

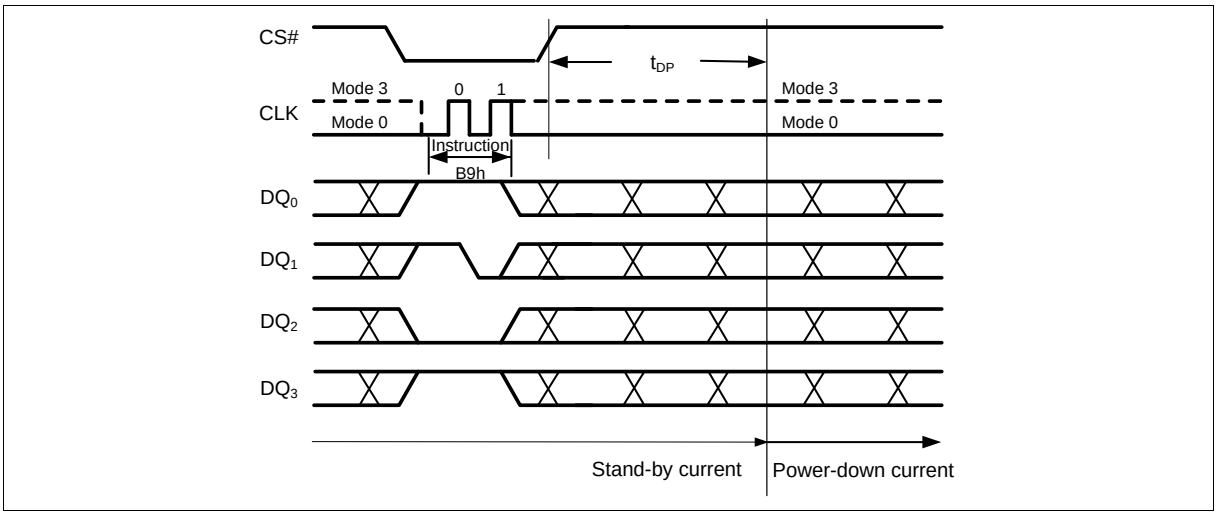


Figure 43 Deep Power-down Instruction (QPI Mode)

11.2.23. Release Power-down / Device ID (ABh)

The Release from Power-down / Device ID instruction is a multi-purpose instruction. It can be used to release the device from the power-down state, or obtain the devices electronic identification (ID) number.

To release the device from the power-down state, the instruction is issued by driving the CS# pin low, shifting the instruction code “ABh” and driving CS# high as shown in Figure 44 & Figure 45. Release from power-down will take the time duration of t_{RES1} (See “12.6 AC Electrical Characteristics”) before the device will resume normal operation and other instructions are accepted. The CS# pin must remain high during the t_{RES1} time duration.

When used only to obtain the Device ID while not in the power-down state, the instruction is initiated by driving the CS# pin low and shifting the instruction code “ABh” followed by 3-dummy bytes. The Device ID bits are then shifted out on the falling edge of CLK with most significant bit (MSB) first as shown in Figure 46 & Figure 47. The Device ID value for the FM25LQ64I3 is listed in Table 4 Manufacturer and Device Identification table. The Device ID can be read continuously. The instruction is completed by driving CS# high.

When used to release the device from the power-down state and obtain the Device ID, the instruction is the same as previously described, and shown in Figure 46 & Figure 47, except that after CS# is driven high it must remain high for a time duration of t_{RES2} (See “12.6 AC Electrical Characteristics”). After this time duration the device will resume normal operation and other instructions will be accepted. If the Release from Power-down / Device ID instruction is issued while an Erase, Program or Write cycle is in process (when WIP equals 1) the instruction is ignored and will not have any effect on the current cycle.

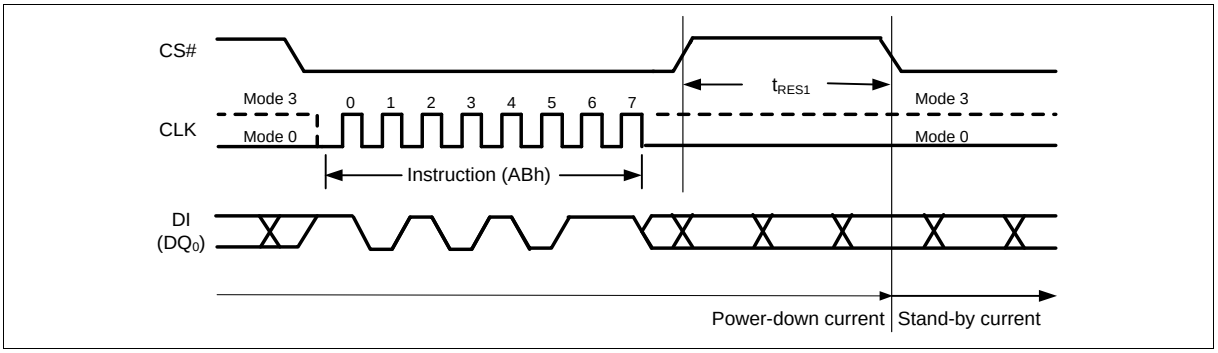


Figure 44 Release Power-down Instruction (SPI Mode)

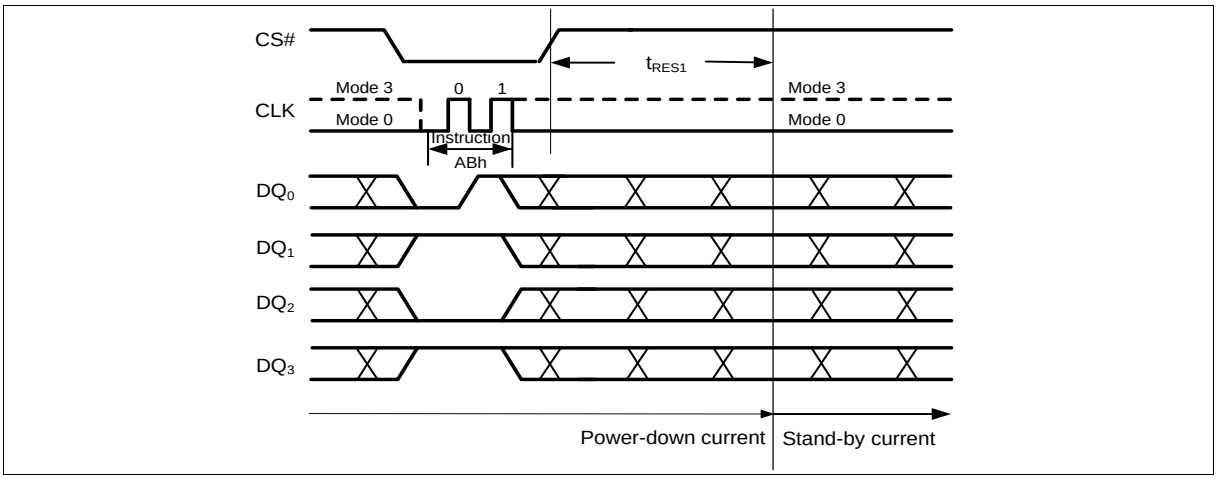


Figure 45 Release Power-down Instruction (QPI Mode)

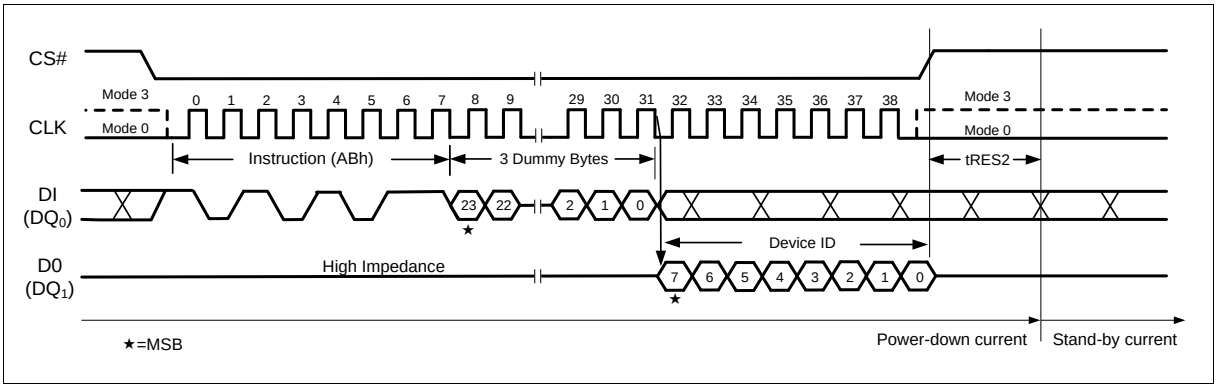


Figure 46 Release Power-down / Device ID Instruction (SPI Mode)

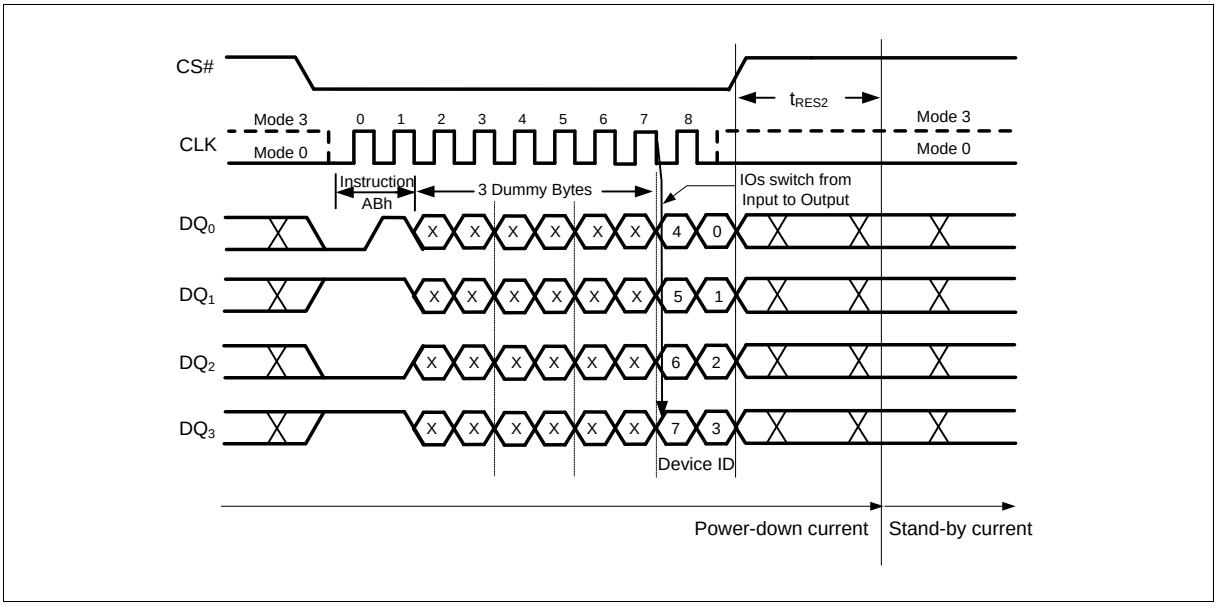


Figure 47 Release Power-down / Device ID Instruction (QPI Mode)

11.2.24. Read Manufacturer / Device ID (90h)

The Read Manufacturer/Device ID instruction is an alternative to the Release from Power-down / Device ID instruction that provides both the JEDEC assigned manufacturer ID and the specific device ID.

The Read Manufacturer/Device ID instruction is very similar to the Release from Power-down / Device ID instruction. The instruction is initiated by driving the CS# pin low and shifting the instruction code “90h” followed by a 24-bit address A23-A0 of 000000h. After which, the Manufacturer ID for Shanghai Fudan Microelectronics Group Co., Ltd (A1h) and the Device ID are shifted out on the falling edge of CLK with most significant bit (MSB) first as shown in Figure 48 & Figure 49. The Device ID value for the FM25LQ64I3 is listed in Table 4 Manufacturer and Device Identification. The Manufacturer and Device IDs can be read continuously, alternating from one to the other. The instruction is completed by driving CS# high.

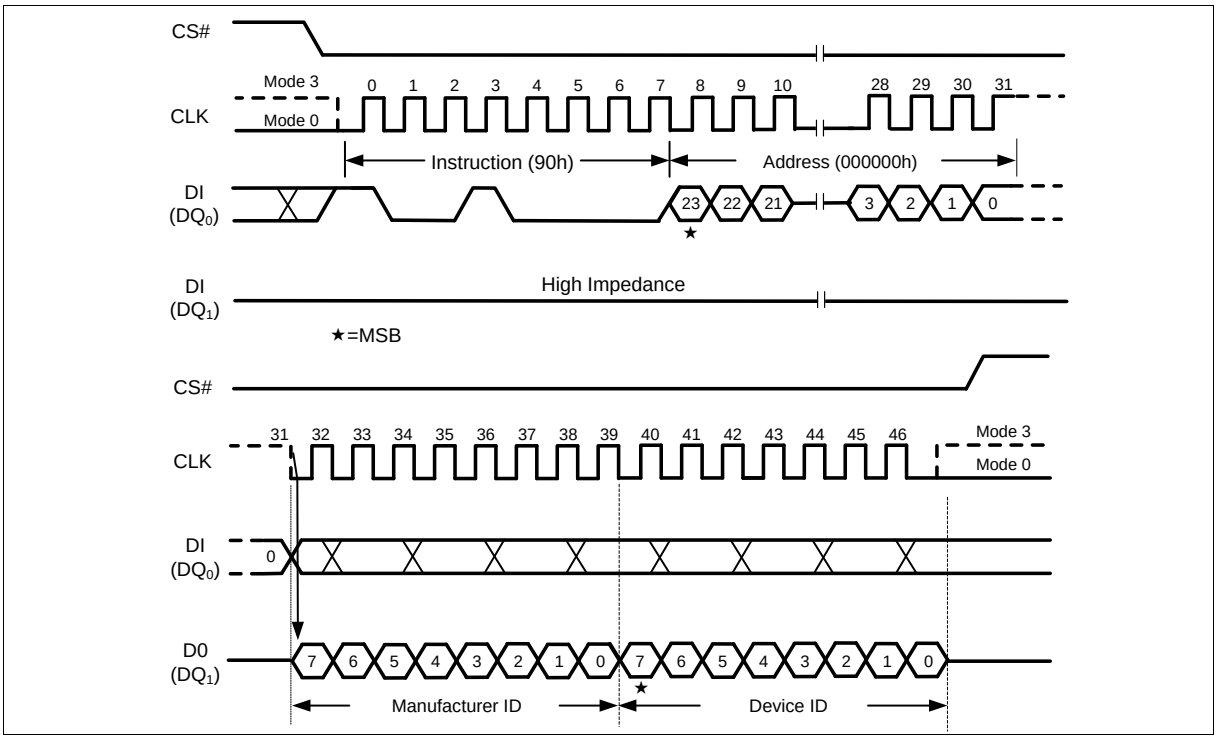


Figure 48 Read Manufacturer / Device ID Instruction (SPI Mode)

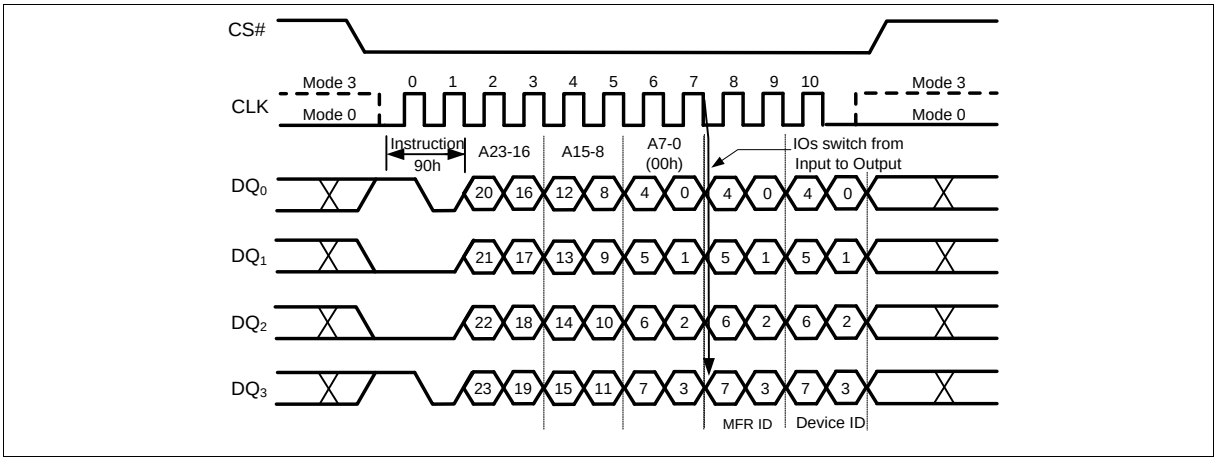


Figure 49 Read Manufacturer / Device ID Instruction (QPI Mode)

11.2.25. Read Manufacturer / Device ID Dual I/O (92h)

The Read Manufacturer / Device ID Dual I/O instruction is an alternative to the Read Manufacturer / Device ID instruction that provides both the JEDEC assigned manufacturer ID and the specific device ID at 2x speed.

The Read Manufacturer / Device ID Dual I/O instruction is similar to the Fast Read Dual I/O instruction. The instruction is initiated by driving the CS# pin low and shifting the instruction code "92h" followed by a 24-bit address A23-A0 of 000000h, 8-bit Continuous Read Mode Bits, with the capability to input the Address bits two bits per clock. After which, the Manufacturer ID for Shanghai Fudan Microelectronics Group Co., Ltd (A1h) and the Device ID are shifted out 2 bits per clock on the falling edge of CLK with most significant bits (MSB) first as shown in Figure 50. The Device ID value for the FM25LQ64I3 is listed in Table 4 Manufacturer and Device Identification. The Manufacturer and Device IDs can be read continuously, alternating from one to the other. The instruction is completed by driving CS# high.

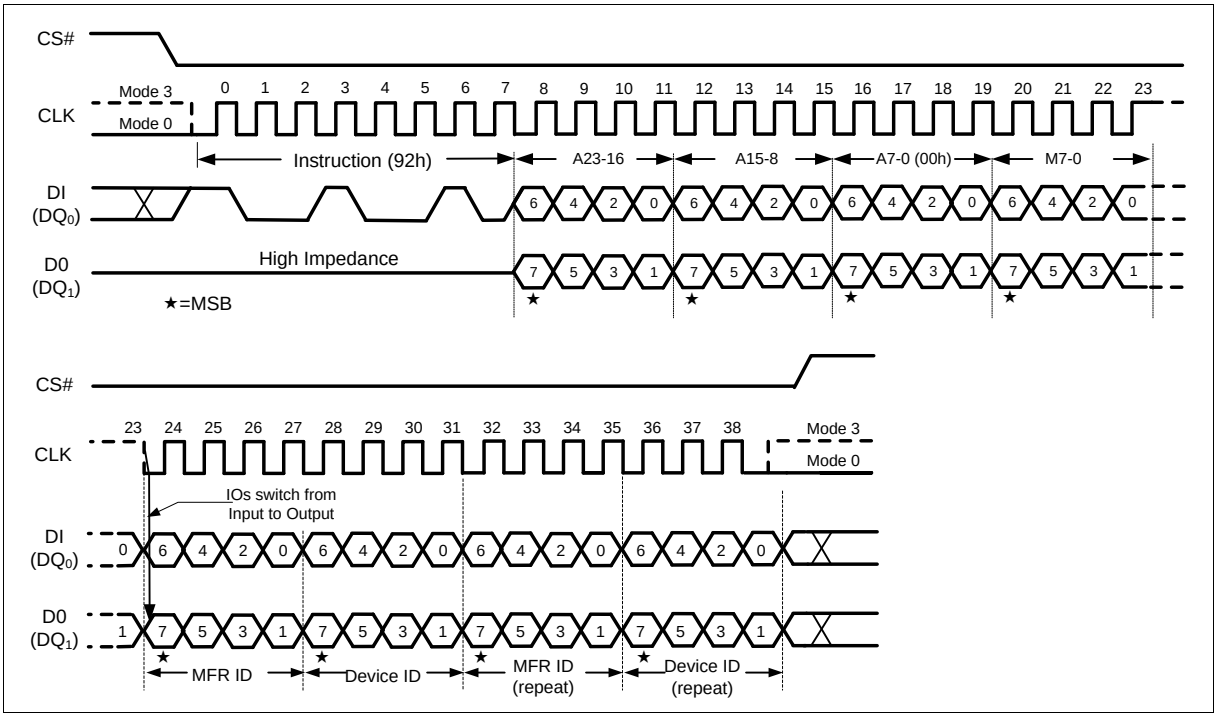


Figure 50 Read Manufacturer / Device ID Dual I/O Instruction (SPI Mode only)

11.2.26. Read Manufacturer / Device ID Quad I/O (94h)

The Read Manufacturer / Device ID Quad I/O instruction is an alternative to the Read Manufacturer / Device ID instruction that provides both the JEDEC assigned manufacturer ID and the specific device ID at 4x speed.

The Read Manufacturer / Device ID Quad I/O instruction is similar to the Fast Read Quad I/O instruction. The instruction is initiated by driving the CS# pin low and shifting the instruction code "94h" followed by a 24-bit address A23-A0 of 000000h, 8-bit Continuous Read Mode Bits and then four clock dummy cycles, with the capability to input the Address bits four bits per clock. After which, the Manufacturer ID for Shanghai Fudan Microelectronics Group Co., Ltd (A1h) and the Device ID are shifted out four bits per clock on the falling edge of CLK with most significant bit (MSB) first as shown in Figure 51. The Device ID value for the FM25LQ64I3 is listed in Manufacturer and Device Identification table. The Manufacturer and Device IDs can be read continuously, alternating from one to the other. The instruction is completed by driving CS# high.

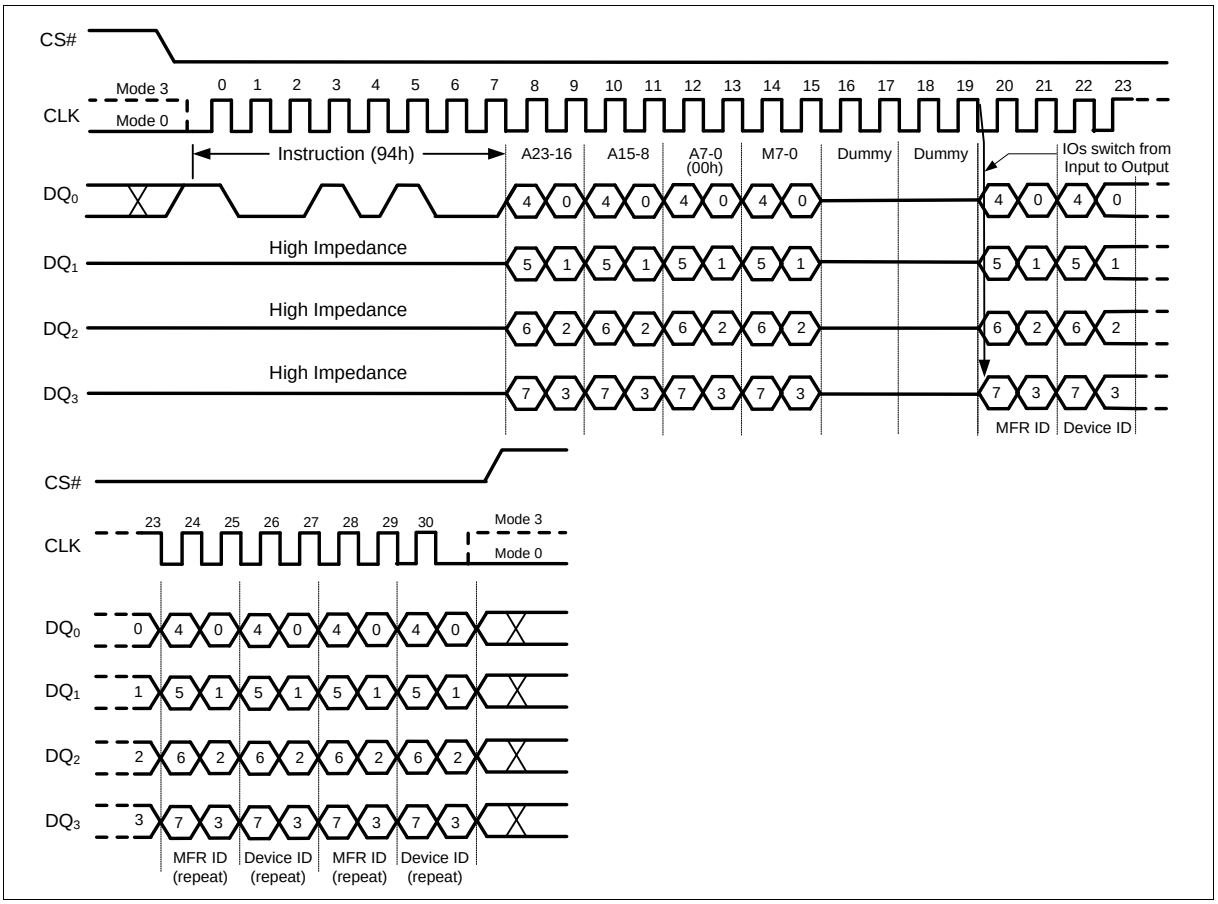


Figure 51 Read Manufacturer / Device ID Quad I/O Instruction (SPI Mode only)

11.2.27. Read Unique ID Number (4Bh)

The Read Unique ID Number instruction accesses a factory-set read-only 64-bit number that is unique to each FM25LQ64I3 device. The ID number can be used in conjunction with user software methods to help prevent copying or cloning of a system. The Read Unique ID instruction is initiated by driving the CS# pin low and shifting the instruction code “4Bh” followed by a four bytes of dummy clocks. After which, the 64-bit ID is shifted out on the falling edge of CLK as shown in Figure 52.

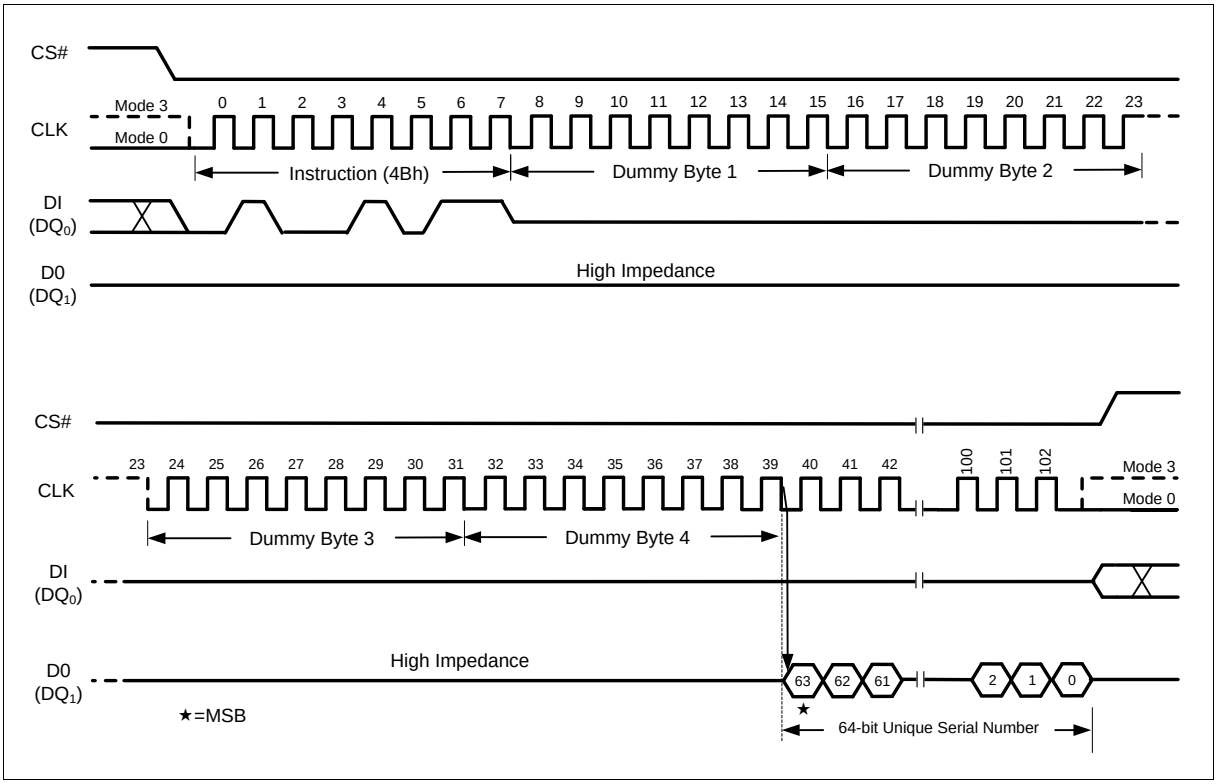


Figure 52 Read Unique ID Number Instruction (SPI Mode only)

11.2.28. Read JEDEC ID (9Fh)

For compatibility reasons, the FM25LQ64I3 provides several instructions to electronically determine the identity of the device. The Read JEDEC ID instruction is compatible with the JEDEC standard for SPI compatible serial memories. The instruction is initiated by driving the CS# pin low and shifting the instruction code “9Fh”. The JEDEC assigned Manufacturer ID byte for Shanghai Fudan Microelectronics Group Co., Ltd (A1h) and two Device ID bytes, Memory Type (ID15-ID8) and Capacity ID7-ID0 are then shifted out on the falling edge of CLK with most significant bit (MSB) first as shown in Figure 53 & Figure 54. For memory type and capacity values refer to Table 4 Manufacturer and Device Identification.

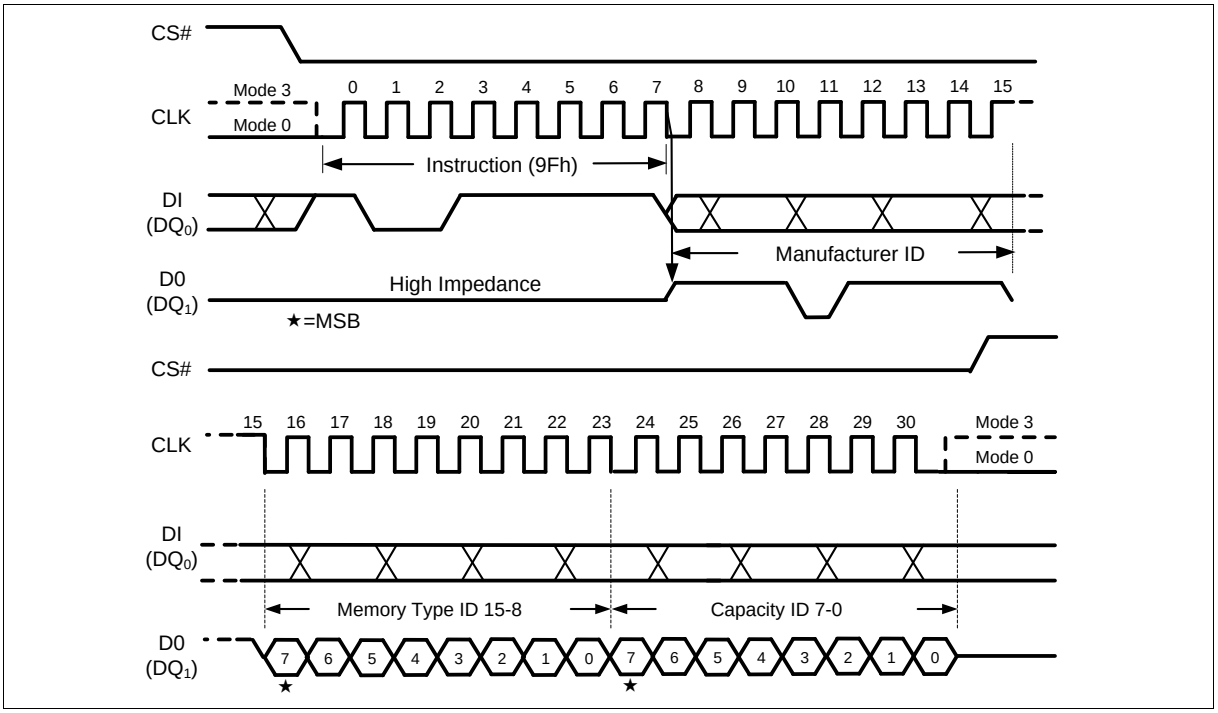


Figure 53 Read JEDEC ID Instruction (SPI Mode)

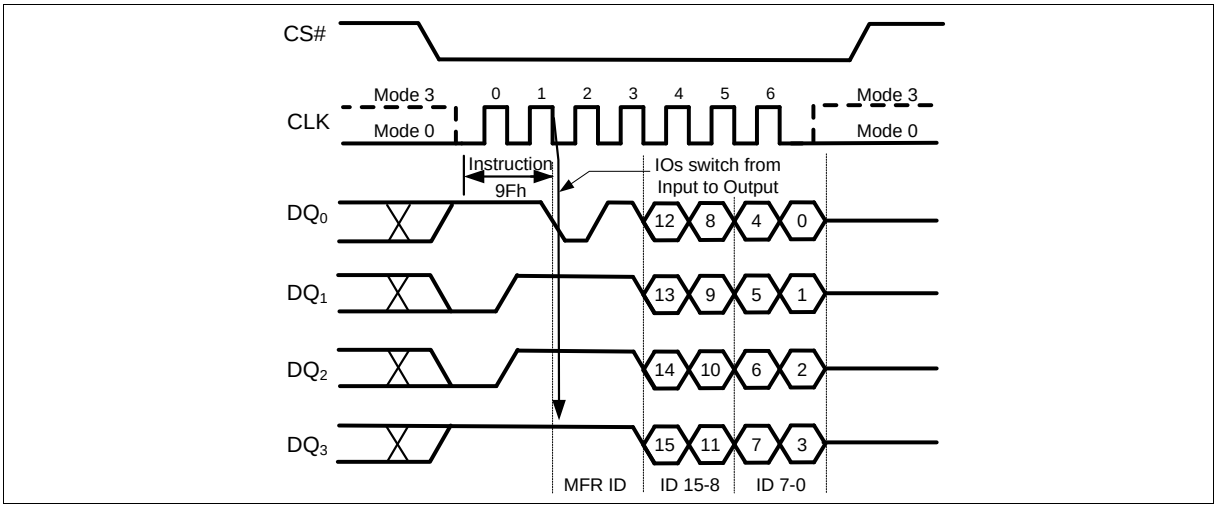


Figure 54 Read JEDEC ID Instruction (QPI Mode)

11.2.29. Read SFDP Register (5Ah)

The FM25LQ64I3 features a 256-Byte Serial Flash Discoverable Parameter (SFDP) register that contains information about device configurations, available instructions and other features. The SFDP parameters are stored in one or more Parameter Identification (PID) tables. Currently only one PID table is specified, but more may be added in the future. The concept of SFDP is similar to the one found in the Introduction of JEDEC Standard, JESD68 on CFI. SFDP is a standard of JEDEC Standard No.216B.

The Read SFDP instruction is initiated by driving the /CS pin low and shifting the instruction code "5Ah" followed by a 24-bit address (A23-A0) (1) into the DI pin. Eight "dummy" clocks are also required before the SFDP register contents are shifted out on the falling edge of the 40th CLK with most significant bit (MSB) first as shown in Figure 55. For SFDP register values and descriptions, refer to the following SFDP Definition table.

Note: 1. A23-A8 = 0; A7-A0 are used to define the starting byte address for the 256-Byte SFDP Register.

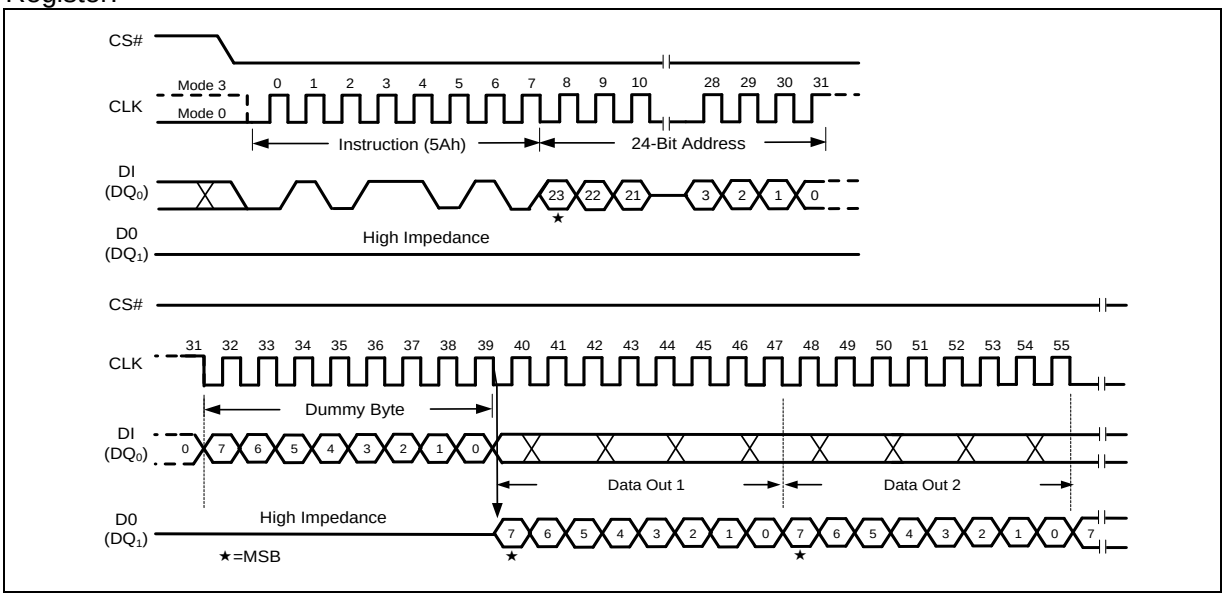


Figure 55 Read SFDP Register Instruction

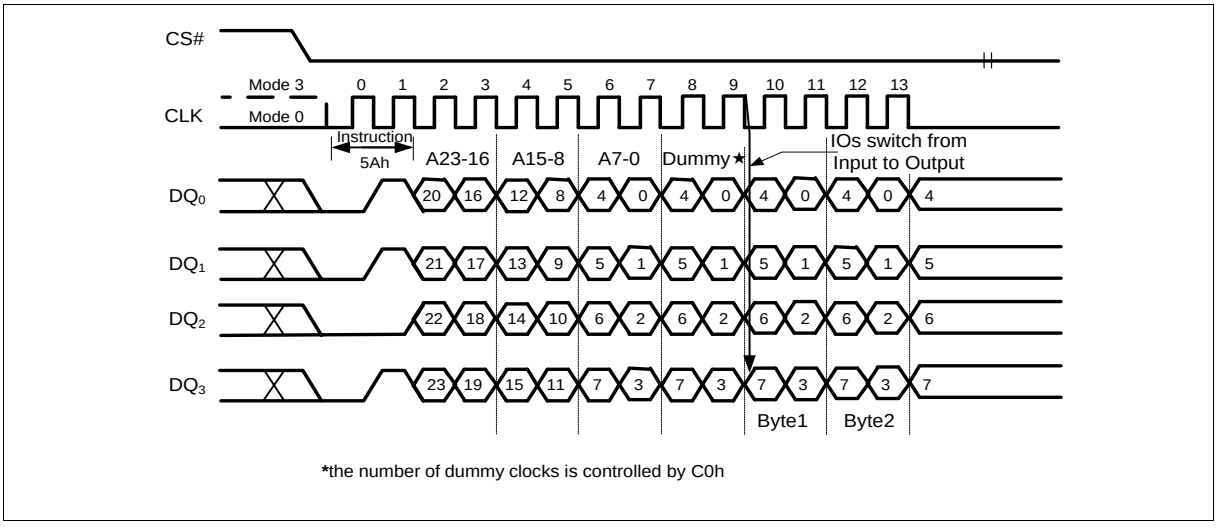


Figure 56 Read SFDP Register Instruction (QPI Mode)

Serial Flash Discoverable Parameter (JEDEC) Definition Table (Please contact FMSH for Details).

11.2.30. Erase Security Sector (44h)

The FM25LQ64I3 offers 3x1024-byte Security Sectors which can be erased and programmed individually. These registers may be used by the system manufacturers to store security and other important information separately from the main memory array.

The Erase Security Sector instruction is similar to the Sector Erase instruction. A Write Enable instruction must be executed before the device will accept the Erase Security Sector Instruction (Status Register bit WEL must equal 1). The instruction is initiated by driving the CS# pin low and shifting the instruction code "44h" followed by a 24-bit address A23-A0 to erase the Security Sectors.

Address	A23-16	A15-12	A11-10	A9-0
Security Sector #1	00h	0001b	00b	Don't Care
Security Sector #2	00h	0010b	00b	Don't Care
Security Sector #3	00h	0011b	00b	Don't Care

The Erase Security Sector instruction sequence is shown in Figure 57. The CS# pin must be driven high after the eighth bit of the last byte has been latched. If this is not done the instruction will not be executed. After CS# is driven high, the self-timed Erase Security Sector operation will commence for a time duration of t_{SE} (See "12.6_AC Electrical Characteristics"). While the Erase Security Sector cycle is in progress, the Read Status Register instruction may still be accessed for checking the status of the WIP bit. The WIP bit is a 1 during the erase cycle and becomes a 0 when the cycle is finished and the device is ready to accept other instructions again. After the Erase Security Sector cycle has finished the Write Enable Latch (WEL) bit in the Status Register is cleared to 0. The Security Sector Lock Bits (LB3, LB2, LB1) in the Status Register-2 can be used to OTP protect the Security Sectors. Once a lock bit is set to 1, the Security Sector will be permanently locked and Erase Security Sector instruction will be ignored.

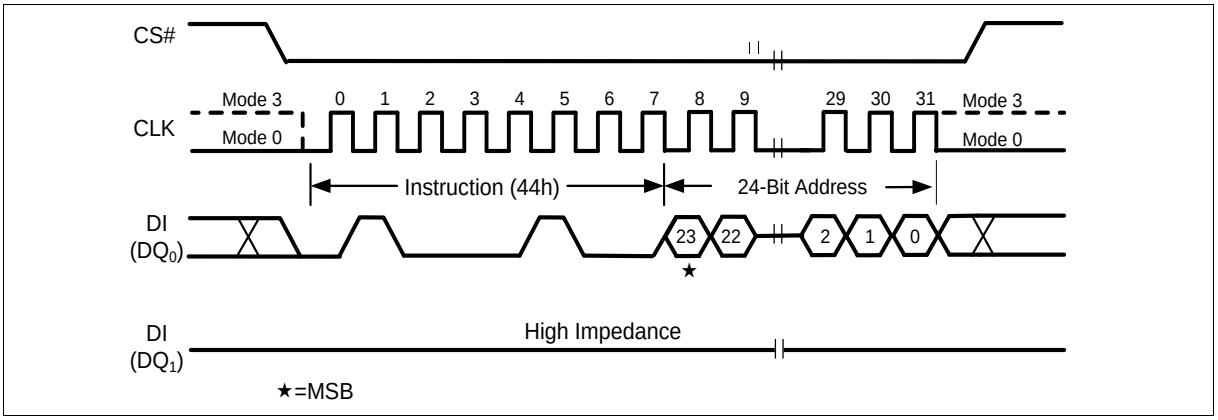


Figure 57 Erase Security Sector Instruction (SPI Mode only)

11.2.31. Program Security Sector (42h)

The Program Security Sector instruction is similar to the Page Program instruction. Each security register contains four pages content. It allows from one byte to 256 bytes of Security Sector data to be programmed at previously erased (FFh) memory locations. A Write Enable instruction must be executed before the device will accept the Program Security Sector Instruction (Status Register bit WEL= 1). The instruction is initiated by driving the CS# pin low then shifting the instruction code “42h” followed by a 24-bit address A23-A0 and at least one data byte, into the DI pin. The CS# pin must be held low for the entire length of the instruction while data is being sent to the device.

Address	A23-16	A15-12	A11-10	A9-0
Security Sector #1	00h	0001b	00b	Byte Address
Security Sector #2	00h	0010b	00b	Byte Address
Security Sector #3	00h	0011b	00b	Byte Address

The Program Security Sector instruction sequence is shown in Figure 58. The Security Sector Lock Bits (LB3, LB2, LB1) in the Status Register-2 can be used to OTP protect the Security Sector. Once a lock bit is set to 1, the Security Sector will be permanently locked and Program Security Sector instruction will be ignored.

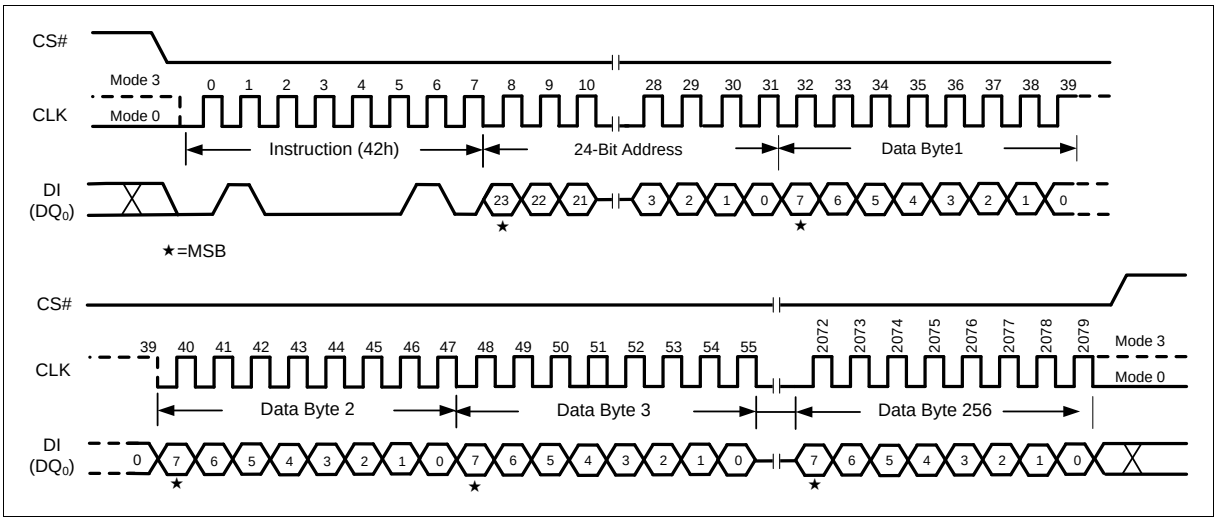


Figure 58 Program Security Sector Instruction (SPI Mode only)

11.2.32. Read Security Sector (48h)

The Read Security Sector instruction is similar to the Fast Read instruction and allows one or more data bytes to be sequentially read from the Security Sector. The instruction is initiated by driving the CS# pin low and then shifting the instruction code “48h” followed by a 24-bit address A23-A0 and eight “dummy” clocks into the DI pin. The code and address bits are latched on the rising edge of the CLK pin.

After the address is received, the data byte of the addressed memory location will be shifted out on the DO pin at the falling edge of CLK with most significant bit (MSB) first. The byte address is automatically incremented to the next byte address after each byte of data is shifted out. Once the byte address reaches the last byte of the register (byte 3FFh), it will be reset to 000h, the first byte of the register, and continues to increment. The instruction is completed by driving CS# high. The Read Security Sector instruction sequence is shown in Figure 59.

If a Read Security Sector instruction is issued while an Erase, Program or Write cycle is in process (WIP =1), the instruction is ignored and will not have any effect on the current cycle. The Read Security Sector instruction allows clock rates from D.C. to a maximum of FR (see “12.6 AC Electrical Characteristics”).

Address	A23-16	A15-12	A11-10	A9-0
Security Sector #1	00h	0001b	00b	Byte Address
Security Sector #2	00h	0010b	00b	Byte Address
Security Sector #3	00h	0011b	00b	Byte Address

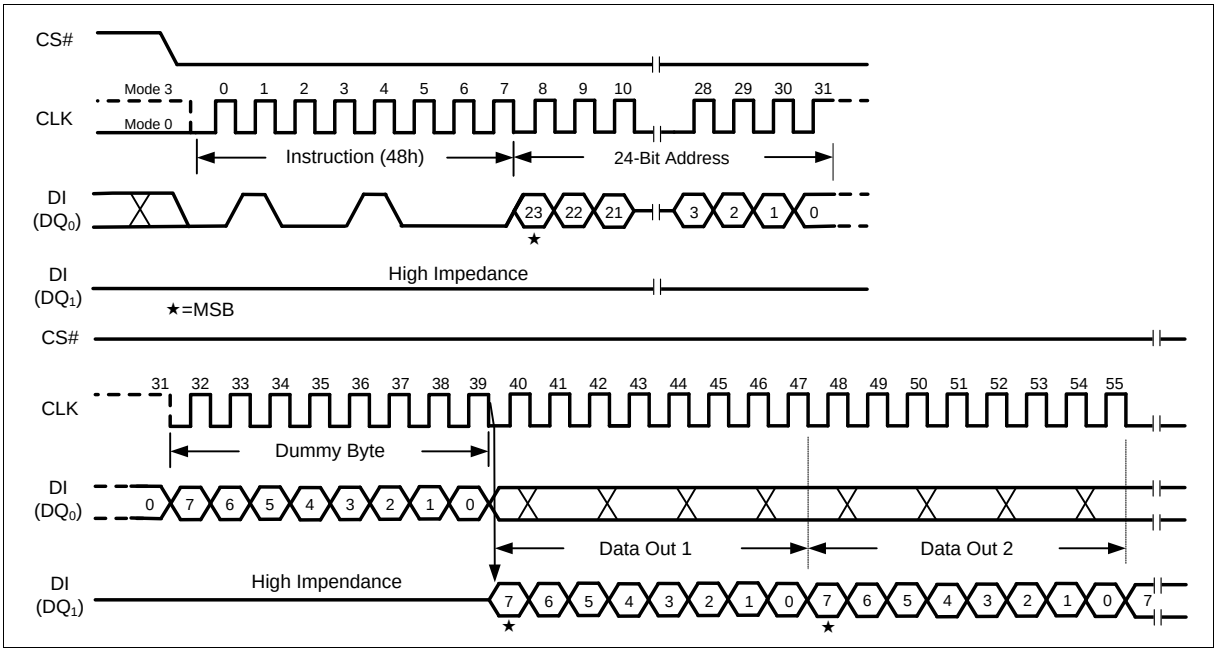


Figure 59 Read Security Sector Instruction (SPI Mode only)

11.2.33. Set Read Parameters (C0h)

In QPI mode, to accommodate a wide range of applications with different needs for either maximum read frequency or minimum data access latency, “Set Read Parameters (C0h)” instruction can be used to configure the number of dummy clocks for “Fast Read (0Bh)”, “Fast Read Quad I/O (EBh)” , “DTR Fast Read Quad I/O (EDh)” , “Burst Read with Wrap (0Ch)” & “Read SFDP Register (5Ah)” instructions, and to configure the number of bytes of “Wrap Length” for the “Burst Read with Wrap (0Ch)” instruction.

In Standard SPI mode, the “Set Read Parameters (C0h)” instruction is not accepted. The dummy clocks for various Fast Read instructions in Standard/Dual/Quad SPI mode are fixed, please refer to Table 8~Table 8 QPI Instructions Set the Instruction set for details. The “Wrap Length” is set by W5-4 bit in the “Set Burst with Wrap (77h)” instruction. This setting will remain unchanged when the device is switched from Standard SPI mode to QPI mode.

The default “Wrap Length” after a power up or a Reset instruction is 8 bytes, the default number of dummy clocks is 4.

P5 – P4	STR FAST READ		DTR FAST READ		P1 – P0	WRAP LENGTH
	DUMMY CLOCKS	MAXIMUM READ FREQ.	DUMMY CLOCKS	MAXIMUM READ FREQ.		
0 0	4	80MHz	10	104MHz	**0 0**	8-byte
0 1	6	104MHz	8	80MHz	**0 1**	16-byte
1 0	8	133MHz	10	104MHz	**1 0**	32-byte
1 1	10	133MHz	10	104MHz	**1 1**	64-byte

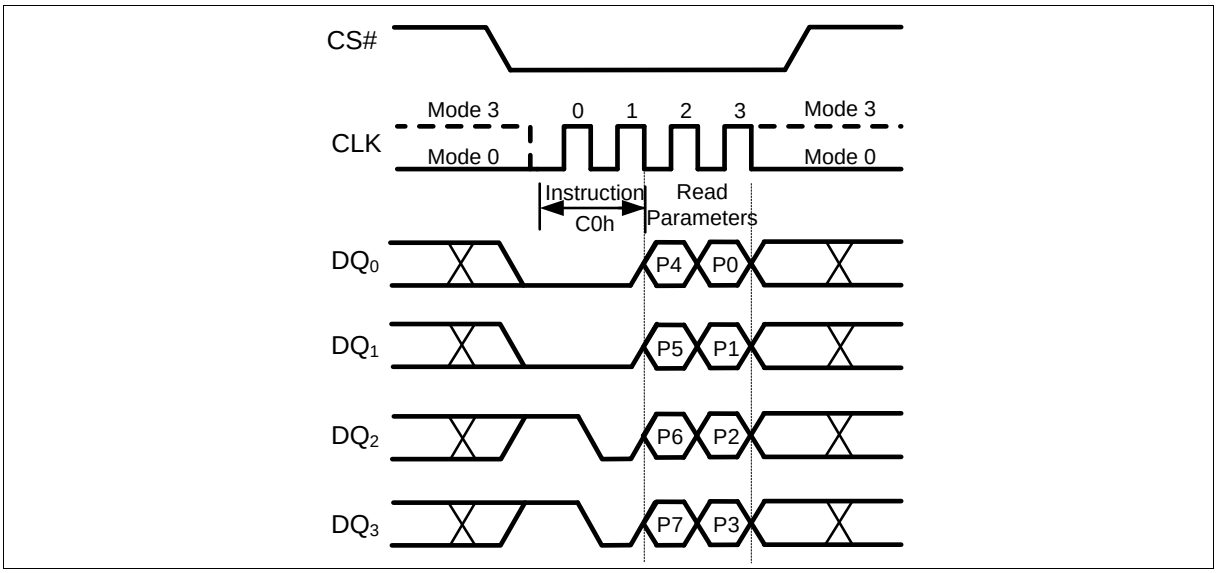


Figure 60 Set Read Parameters Instruction (QPI Mode only)

11.2.34. Burst Read with Wrap (0Ch)

The “Burst Read with Wrap (0Ch)” instruction provides an alternative way to perform the read operation with “Wrap Around” in QPI mode. The instruction is similar to the “Fast Read (0Bh)” instruction in QPI mode, except the addressing of the read operation will “Wrap Around” to the beginning boundary of the “Wrap Length” once the ending boundary is reached.

The “Wrap Length” and the number of dummy clocks can be configured by the “Set Read Parameters C0h)” instruction.

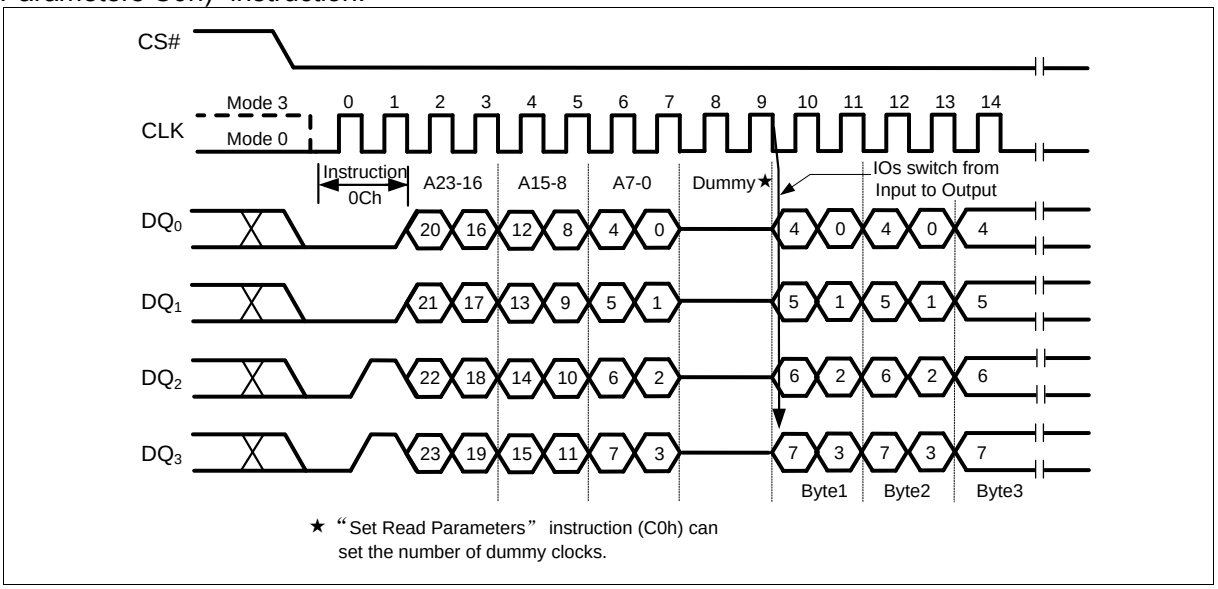


Figure 61 Burst Read with Wrap Instruction (QPI Mode only)

11.2.35. Enable QPI (38h)

The FM25LQ64I3 support both Standard/Dual/Quad Serial Peripheral Interface (SPI) and Quad Peripheral Interface (QPI). However, SPI mode and QPI mode can not be used at the same time. “Enable QPI (38h)” instruction is the only way to switch the device from SPI mode to QPI mode.

Upon power-up, the default state of the device upon is Standard/Dual/Quad SPI mode. In order to switch the device to QPI mode, the Quad Enable (QE) bit in Status Register 2 must be set to 1 first, and an “Enable QPI (38h)” instruction must be issued. If the Quad Enable (QE) bit is 0, the “Enable QPI (38h)” instruction will be ignored and the device will remain in SPI mode.

See “Table 8 QPI Instructions Set” for all the commands supported in QPI mode.

When the device is switched from SPI mode to QPI mode, the existing Write Enable and Program/Erase Suspend status, and the Wrap Length setting will remain unchanged.

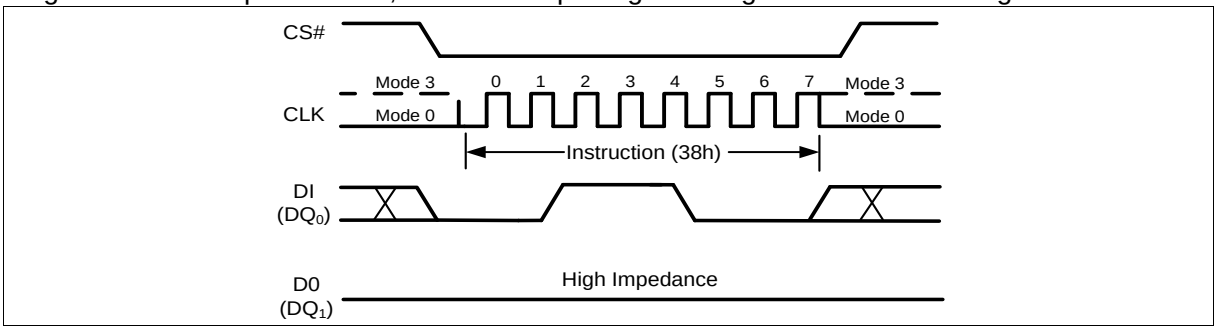


Figure 62 Enable QPI Instruction (SPI Mode only)

11.2.36. Disable QPI (FFh)

In order to exit the QPI mode and return to the Standard/Dual/Quad SPI mode, a “Disable QPI (FFh)” instruction must be issued.

When the device is switched from QPI mode to SPI mode, the existing Write Enable Latch (WEL) and Program/Erase Suspend status and the Wrap Length setting will remain unchanged.

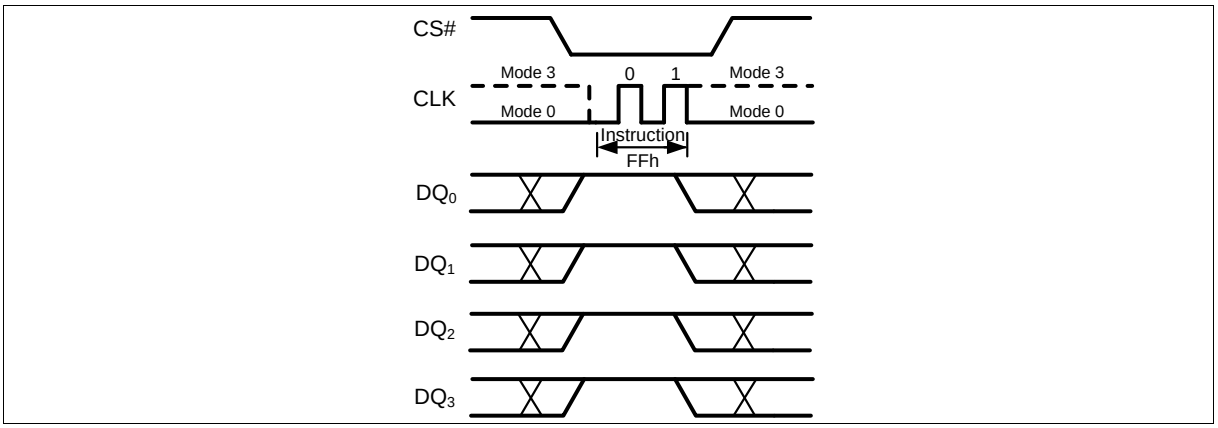


Figure 63 Disable QPI Instruction (QPI Mode only)

11.2.37. Individual Block/Sector Lock(36h)

The Individual Block/Sector Lock provides an alternative way to protect the memory array from adverse Erase/Program. In order to use the Individual Block/Sector Locks, the WPS bit in Status Register-2 must be set to 1. If WPS=0, the write protection will be determined by the combination of CMP, SEC,TB, BP2, BP1 and BP0 bits in the Status Registers. The Individual Block/Sector Lock bits are volatile bits. The default value after power up or after Reset is 1, so the entire memory array is being protected.

To lock a specific block or sector as illustrated in Figure 7, an Individual Block/Sector Lock command must be issued by driving CS# low, shifting the instruction code “36h” into the Data Input (DI) pin on the rising edge of CLK, followed by a 24-bit address and then driving CS# high.

A Write Enable instruction must be executed before the device will accept the Individual Block/Sector Lock Instruction (Status Register bit WEL= 1).

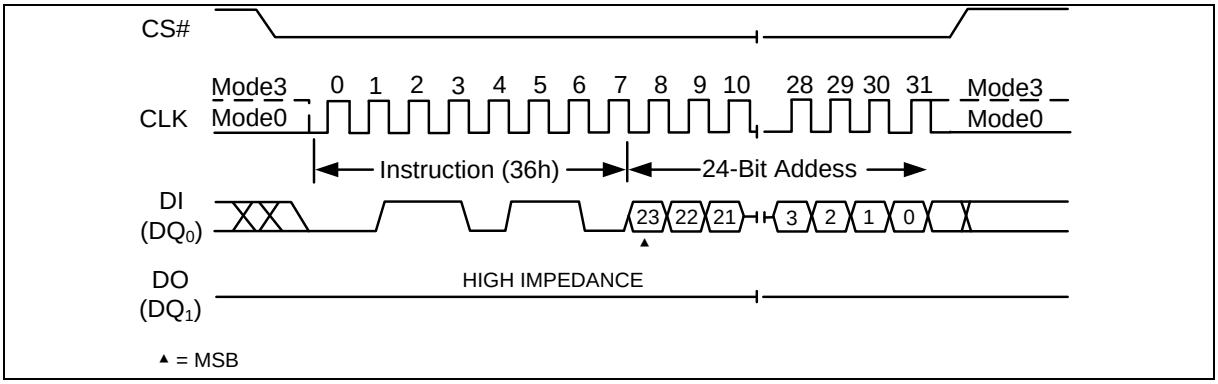


Figure 64 Individual Block/Sector Lock Instruction(SPI)

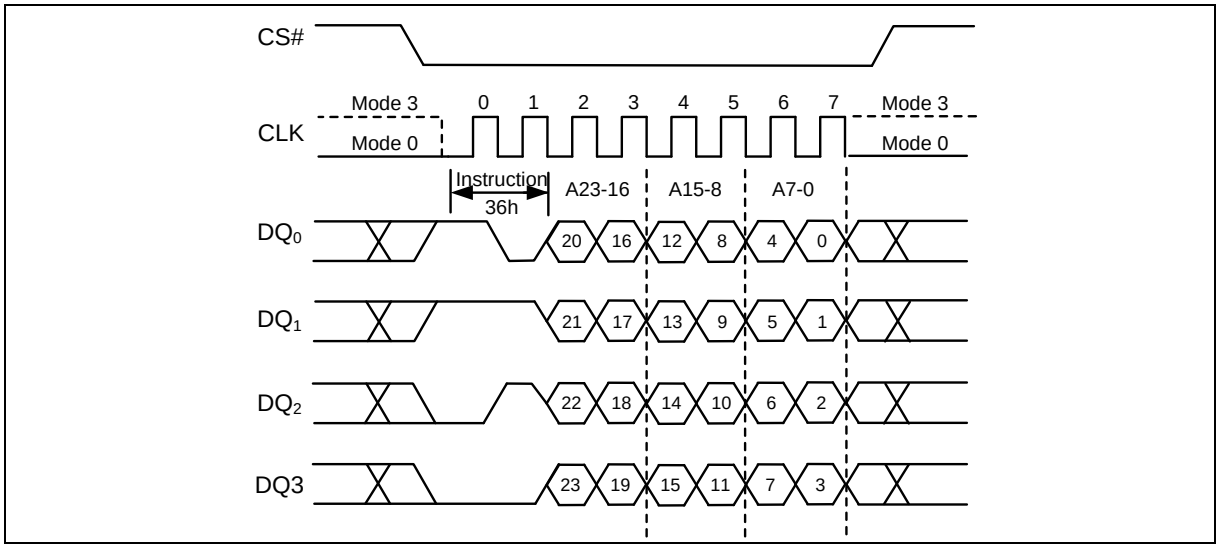


Figure 65 Individual Block/Sector Lock Instruction(QPI Mode)

11.2.38. Individual Block/Sector Unlock(39h)

The Individual Block/Sector Lock provides an alternative way to protect the memory array from adverse Erase/Program. In order to use the Individual Block/Sector Locks, the WPS bit in Status Register-2 must be set to 1. If WPS=0, the write protection will be determined by the combination of CMP, SEC,TB, BP2, BP1 and BP0 bits in the Status Registers. The Individual Block/Sector Lock bits are volatile bits. The default value after power up or after Reset is 1, so the entire memory array is being protected.

To unlock a specific block or sector as illustrated in Figure 7, an Individual Block/Sector Lock command must be issued by driving CS# low, shifting the instruction code “39h” into the Data Input (DI) pin on the rising edge of CLK, followed by a 24-bit address and then driving CS# high.

A Write Enable instruction must be executed before the device will accept the Individual Block/Sector Unlock Instruction (Status Register bit WEL= 1).

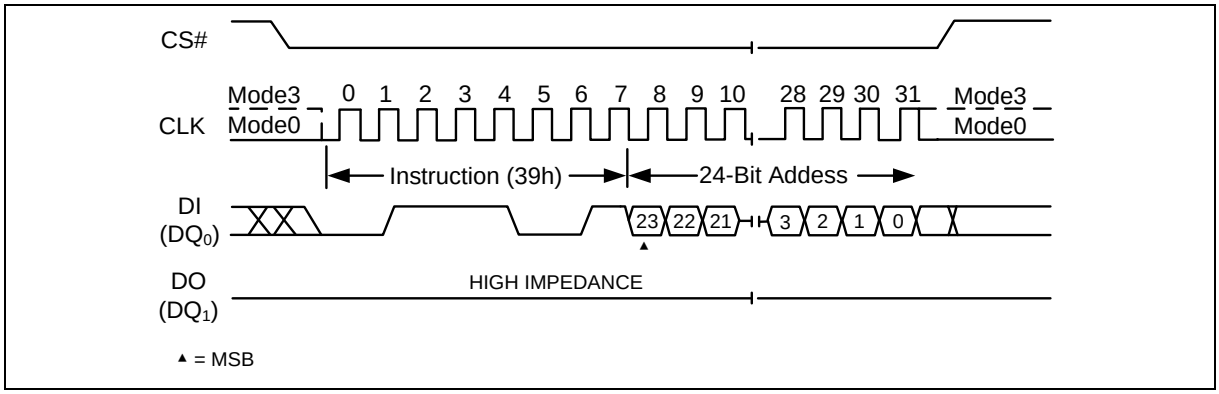


Figure 66 Individual Block/Sector Unlock Instruction (SPI Mode)

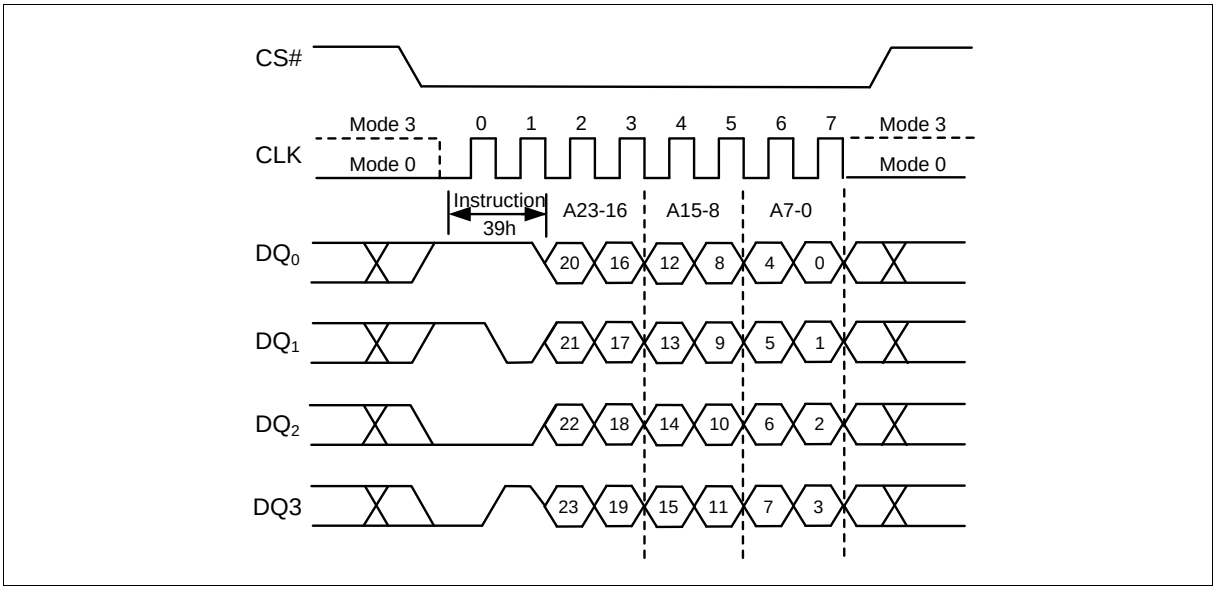


Figure 67 Individual Block/Sector Unlock Instruction (QPI Mode)

11.2.39. Read Block/Sector Lock (3Dh)

The Individual Block/Sector Lock provides an alternative way to protect the memory array from adverse Erase/Program. In order to use the Individual Block/Sector Locks, the WPS bit in Status Register-2 must be set to 1. If WPS=0, the write protection will be determined by the combination of CMP, SEC,TB, BP2,BP1 and BP0 bits in the Status Registers. The Individual Block/Sector Lock bits are volatile bits. The default value after power up or after Reset is 1, so the entire memory array is being protected.

To read out the lock bit of a specific block or sector as illustrated in Figure 7, a Read Block/Sector Lock command must be issued by driving CS# low, shifting the instruction code “3Dh” into the Data Input (DI) pin on the rising edge of CLK, followed by a 24-bit address and then driving CS# high. The Block/Sector Lock bit value will be shifted out on the DO pin at the falling edge of CLK with most significant bit (MSB) as shown in. If the least significant bit (LSB) is 1, the corresponding block/sector is locked; if LSB=0, the corresponding block/sector is unlocked, Erase/Program operation can be performed.

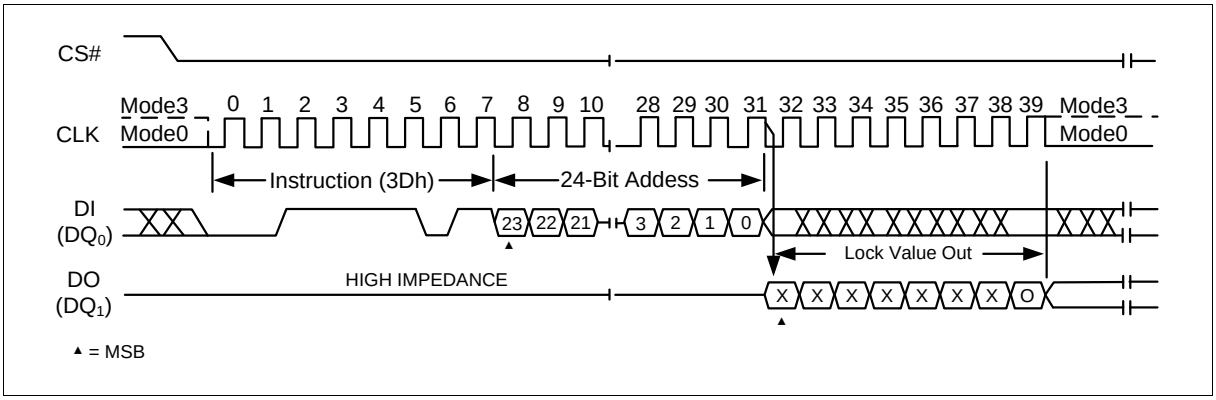


Figure 68 Read Block/Sector Lock Instruction (SPI Mode)

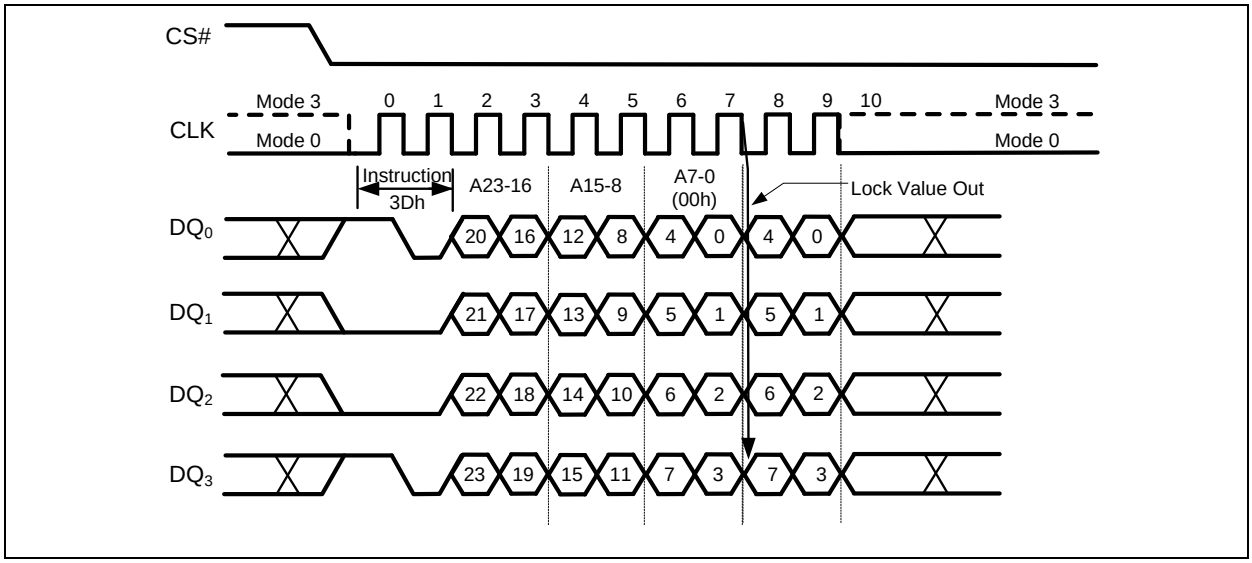


Figure 69 Read Block/Sector Lock Instruction (QPI Mode)

11.2.40. Global Block/Sector Lock (7Eh)

All Block/Sector Lock bits can be set to 1 by the Global Block/Sector Lock instruction. The command must be issued by driving CS# low, shifting the instruction code "7Eh" into the Data Input (DI) pin on the rising edge of CLK, and then driving CS# high.

A Write Enable instruction must be executed before the device will accept the Global Block/Sector Lock Instruction (Status Register bit WEL= 1).

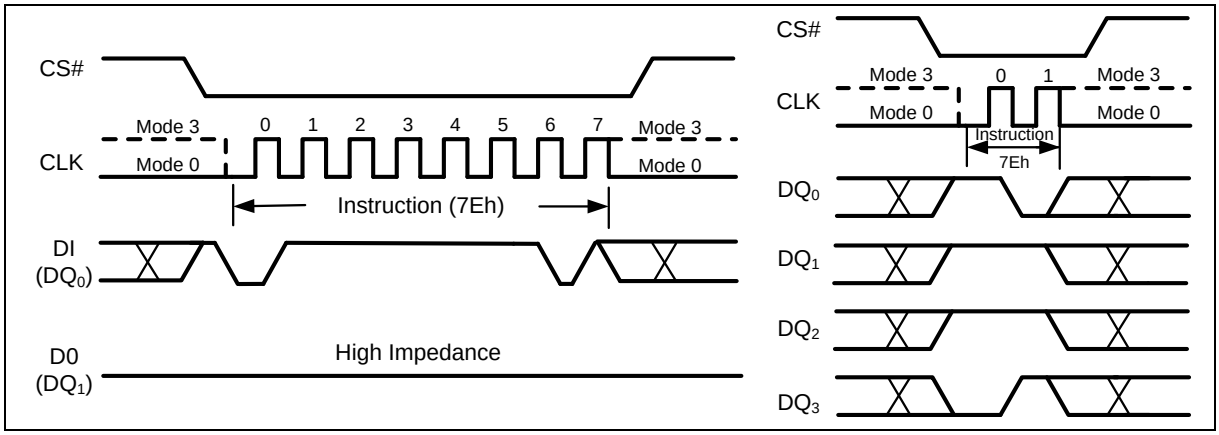


Figure 70 Global Block/Sector Lock Instruction for SPI Mode (left) or QPI Mode (right)

11.2.41. Global Block/Sector Unlock (98h)

All Block/Sector Lock bits can be set to 0 by the Global Block/Sector Unlock instruction. The command must be issued by driving CS# low, shifting the instruction code “98h” into the Data Input (DI) pin on the rising edge of CLK, and then driving CS# high.

A Write Enable instruction must be executed before the device will accept the Global Block/Sector Unlock Instruction (Status Register bit WEL= 1).

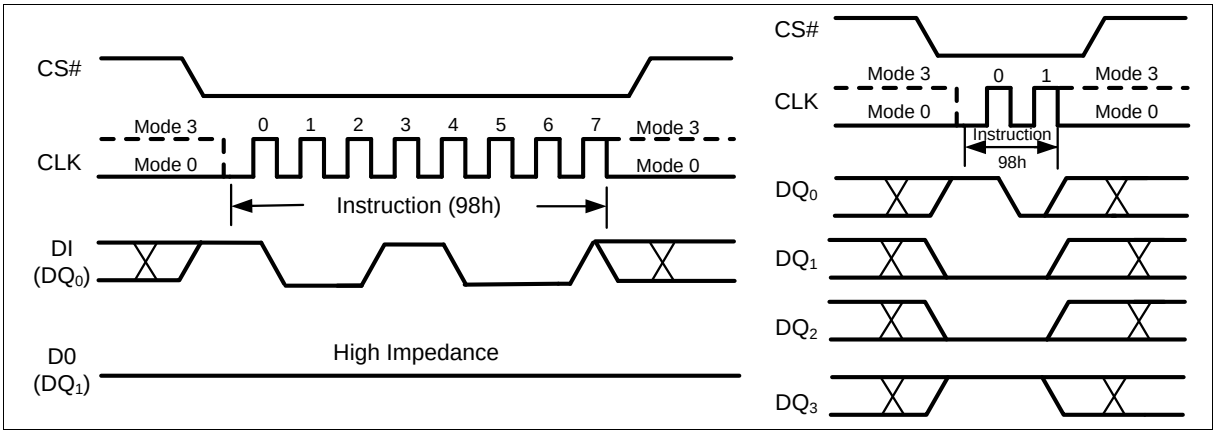


Figure 71 Global Block/Sector Unlock Instruction for SPI Mode (left) or QPI Mode (right)

11.2.42. Enable Reset (66h) and Reset (99h)

FM25LQ64I3 provide a software Reset instruction. Once the Reset instruction is accepted, any on-going internal operations will be terminated and the device will return to its default power-on state and lose all the current volatile settings, such as Volatile Status Register bits, Write Enable Latch (WEL) status, Read parameter setting P7-P0 and Wrap Bit setting W6-W4.

“Enable Reset (66h)” and “Reset (99h)” instructions can be issued in either SPI mode or QPI mode. To avoid accidental reset, both instructions must be issued in sequence. Any other commands other than “Reset (99h)” after the “Enable Reset (66h)” command will disable the “Reset Enable” state. A new sequence of “Enable Reset (66h)” and “Reset (99h)” is needed to reset the device. Once the Reset command is accepted by the device, the device will take approximately 30μs to reset. During this period, no command will be accepted.

Data corruption may happen if there is an on-going internal Erase or Program operation when Reset command sequence is accepted by the device. It is recommended to check the WIP bit in Status Register before issuing the Reset command sequence.

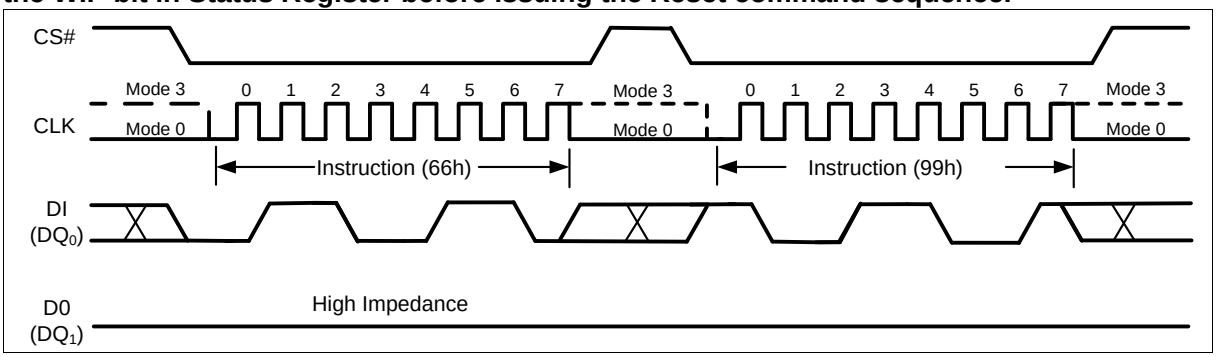


Figure 72 Enable Reset and Reset Instruction Sequence (SPI Mode)

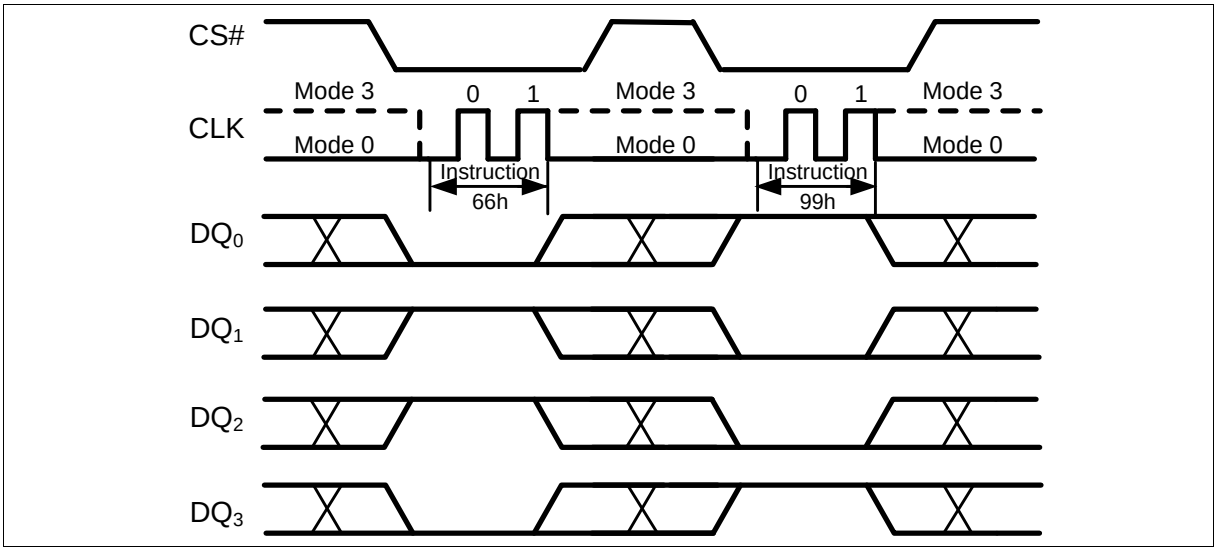


Figure 73 Enable Reset and Reset Instruction Sequence (QPI Mode)

12. Electrical Characteristics

12.1. Absolute Maximum Ratings

Operating Temperature	-40°C to +85°C
Storage Temperature	-65°C to +150°C
Voltage on I/O Pin with Respect to Ground	-0.6V to V_{CC}+0.5V
Transient Input/Output Voltage(note: overshoot <20ns)	-2.0V to V_{CC} +2.0V
V_{CC}	-0.6V to 2.5V

*NOTICE: Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

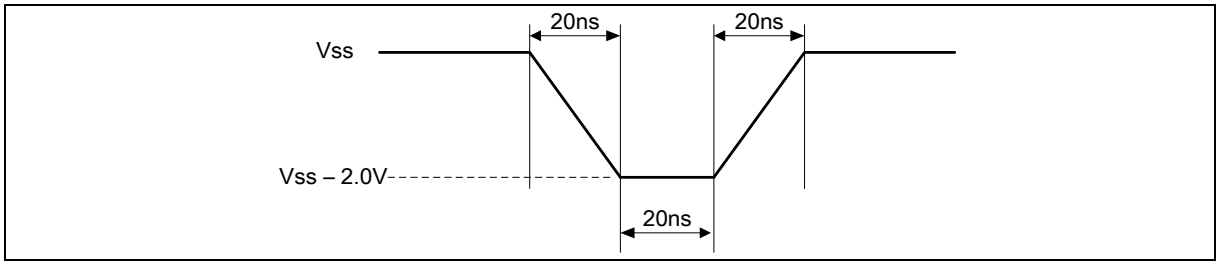


Figure 74 Maximum Negative Overshoot Waveform

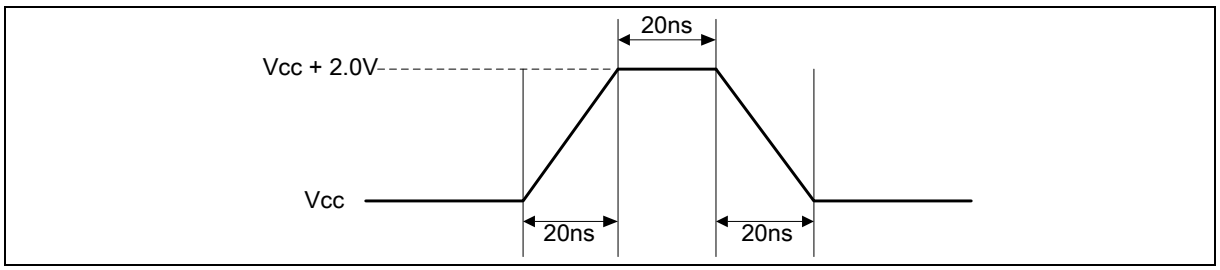


Figure 75 Maximum Positive Overshoot Waveform

12.2. Pin Capacitance

Applicable over recommended operating range from: T_A = 25°C, f = 1 MHz.

Symbol	Test Condition	Max	Units	Conditions
C_{IN}(1)	Input Capacitance	6	pF	V_{IN} = 0V
C_{OUT}(1)	Output Capacitance	8	pF	V_{OUT} = 0V

Note: 1. This parameter is characterized and is not 100% tested.

12.3. Power-up Timing

Applicable over recommended operating range from: T_A = -40°C to 85°C, V_{CC} = 1.65V to 2.0V, (unless otherwise noted).

Symbol	PARAMETER	SPEC		UNIT
		MIN	MAX	
t_{VSL}	VCC (min) to CS# Low	1		ms
V_{WI}	Write Inhibit Threshold Voltage	1	1.4	V
V_{PWD}	VCC voltage needed to below V_{PWD} for ensuring initialization will occur		0.4	V
t_{PWD}	The minimum duration for ensuring initialization will occur	100		us

Note: 1. this parameter is characterized and is not 100% tested.

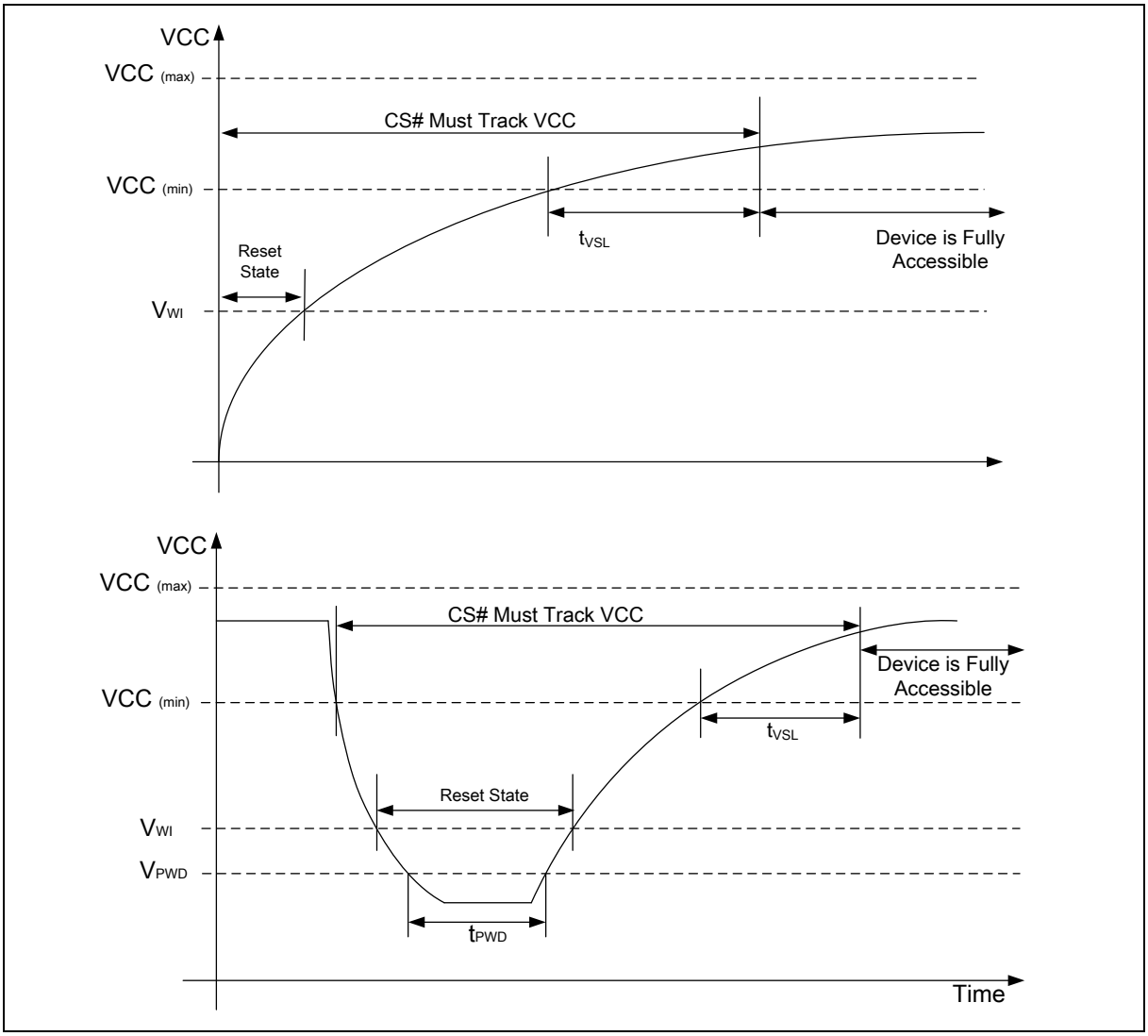


Figure 76 Power-up Timing & Power Up/Down and Voltage Drop

12.4. DC Electrical Characteristics

Table 10 DC Characteristics

Applicable over recommended operating range from: T_A = -40°C to 85°C, V_{CC} = 1.65V to 2.0V, (unless otherwise noted).

SYMBOL	PARAMETER	CONDITIONS	SPEC			UNIT
			MIN	TYP	MAX	
Vcc	Supply Voltage		1.65		2.0	V
I_{LI}	Input Leakage Current				±2	µA
I_{LO}	Output Leakage Current				±2	µA
I_{CC1}	Standby Current	CS# = V_{CC}, V_{IN} = Vss or V_{CC}		10	40	µA
I_{CC2}	Deep Power-down Current			0.5	10	µA
I_{CC3}(1)	Read Current	CLK=0.1V_{CC}/0.9V_{CC} at 80MHz, DQ open		4	8	mA
		CLK=0.1V_{CC}/0.9V_{CC}, at 133MHz, DQ open		5	10	mA
I_{CC4}	Operating Current (WRSR)	CS#=V_{CC}		10	15	mA
I_{CC5}	Operating Current (PP)			10	15	mA
I_{CC6}	Operating Current (SE)			10	15	mA
I_{CC7}	Operating Current (BE)			10	15	mA
V_{IL}(2)	Input Low Voltage		-0.5		0.2V_{CC}	V
V_{IH}(2)	Input High Voltage		0.7V_{CC}		V_{CC}+0.4	V
V_{OL}	Output Low Voltage	I_{OL} = 100 µA			0.2	V
V_{OH}	Output High Voltage	I_{OH} = -100 µA	V_{CC}-0.2			V

Notes:
1. Checker Board Pattern.
2. V_{IL} min and V_{IH} max are reference only and are not tested.

12.5. AC Measurement Conditions

Table 11 AC Measurement Conditions

SYMBOL	PARAMETER	SPEC		UNIT
		MIN	MAX	
CL	Load Capacitance		20	pF
TR, TF	Input Rise and Fall Times		5	ns
VIN	Input Pulse Voltages	0.1 V_{CC} to 0.8 V_{CC}		V
IN	Input Timing Reference Voltages	0.2 V_{CC} to 0.7 V_{CC}		V
OUT	Output Timing Reference Voltages	0.5V_{CC}		V

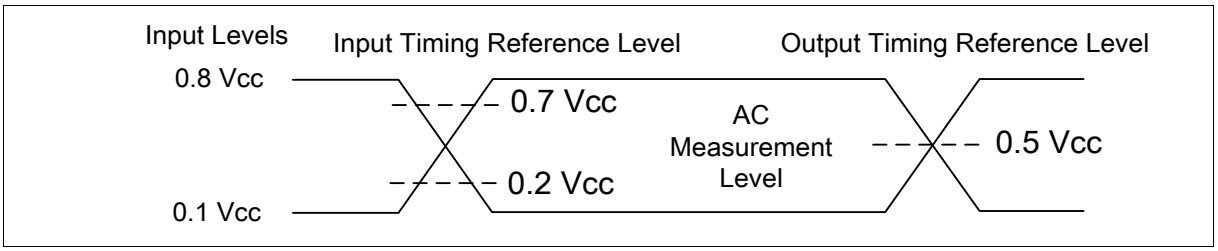


Figure 77 AC Measurement I/O Waveform

12.6. AC Electrical Characteristics

Table 12 AC Characteristics

Applicable over recommended operating range from: T_A = -40°C to 85°C, V_{CC} = 1.65V to 2.0V, (unless otherwise noted).

SYMBOL	PARAMETER	SPEC			UNIT
		MIN	TYP	MAX	
F_{R1}	Serial Clock Frequency for: FAST_READ, PP, SE, BE, DP, RES, WREN, WRDI, WRSR, etc.			133	MHz
F_{R2}	Serial Clock Frequency for： EDh			104	MHz
f_R	Serial Clock Frequency for： 03H			80	MHz
t_{CH1}(1)	Serial Clock High Time	%45/ F_R			ns
t_{CL1}(1)	Serial Clock Low Time	%45/ F_R			ns
t_{CLCH}(2)	Serial Clock Rise Time (Slew Rate)	0.2			V/ns
t_{CHCL}(2)	Serial Clock Fall Time (Slew Rate)	0.2			V/ns
t_{SLCH}	CS# Active Setup Time	5			ns
t_{CHSH}	CS# Active Hold Time	5			ns
t_{SHCH}	CS# Not Active Setup Time	5			ns
t_{CHSL}	CS# Not Active Hold Time	5			ns
t_{SHSL}	CS# High Time	20			ns
t_{SHQZ}(2)	Output Disable Time			7	ns
t_{CLQX}	Output Hold Time	1.2			ns
t_{DVCH}	Data In Setup Time	2			ns
t_{CHDX}	Data In Hold Time	2			ns
t_{HLCH}	HOLD# Low Setup Time (relative to CLK)	5			ns
t_{HHCH}	HOLD# High Setup Time (relative to CLK)	5			ns
t_{CHHH}	HOLD# Low Hold Time (relative to CLK)	5			ns
t_{CHHL}	HOLD# High Hold Time (relative to CLK)	5			ns
t_{HLQZ}(2)	HOLD# Low to High-Z Output			7	ns
t_{HHQX}(2)	HOLD# High to Low-Z Output			7	ns
t_{CLQV}	Output Valid from CLK			7	ns
t_{WHSL}	Write Protect Setup Time before CS# Low	20			ns
t_{SHWL}	Write Protect Hold Time after CS# High	1			µs
t_{DP}(2)	CS# High to Deep Power-down Mode			3	µs
t_{RES1}(2)	CS# High to Standby Mode without Electronic Signature Read			20	µs
t_{RES2}(2)	CS# High to Standby Mode with Electronic Signature Read			20	µs
t_{SUS}(2)	CS# High to next Instruction after Suspend			30	µs
t_W	Write Status Register Cycle Time		2	30	ms
t_{BP}	Byte Program Time		50	100	µs
t_{PP}	Page Program Time		0.4	2	ms
t_{SE}	Sector Erase Time		30	300	ms
t_{BE}	Block Erase Time (32KB)		100	800	ms
t_{BE}	Block Erase Time (64KB)		150	1200	ms
t_{CE}	Chip Erase Time		15	40	s

SYMBOL	PARAMETER	SPEC			UNIT
		MIN	TYP	MAX	
t_{RST}	CS# High to Next Command After Reset(Except From Erase)			30	μs
	CS# High to Next Command After Reset(From Erase)			12	ms
t_{RS}	Latency Between Resume and Next Suspend	100			μs

Notes:

1. $T_{CH1}+T_{CL1} >= 1 / F_{CLK}$;
2. This parameter is characterized and is not 100% tested.

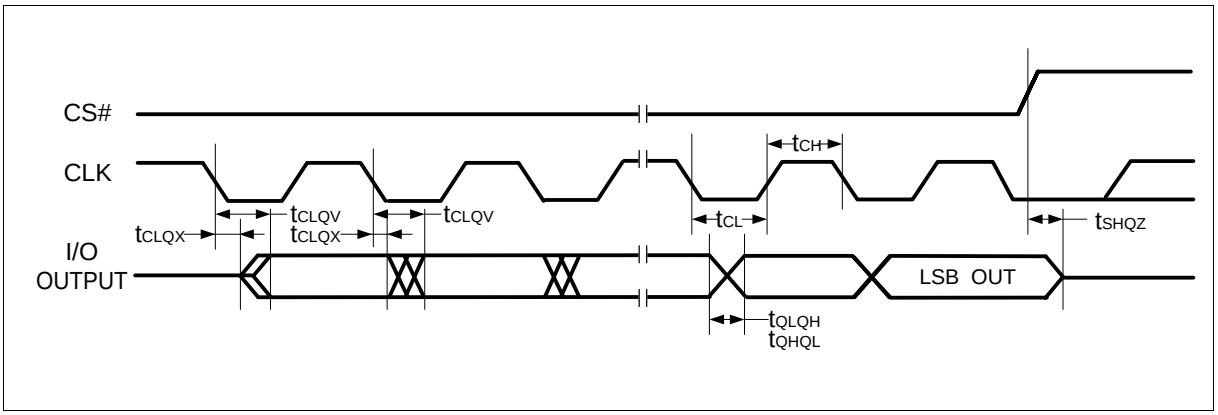


Figure 78 Serial Output Timing

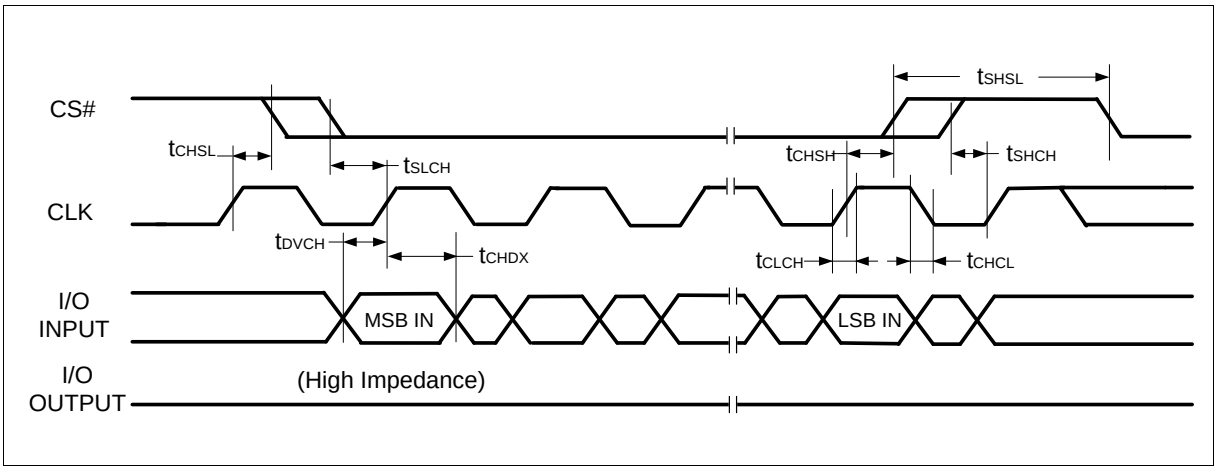


Figure 79 Serial Input Timing

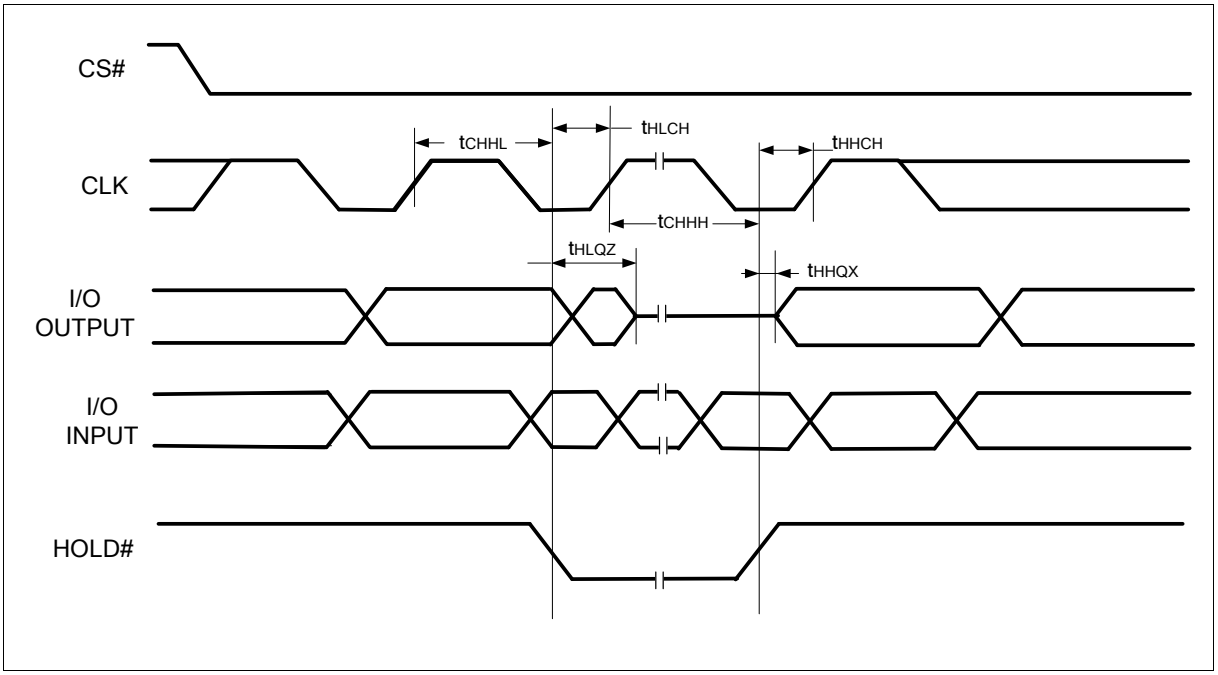


Figure 80 Hold Timing

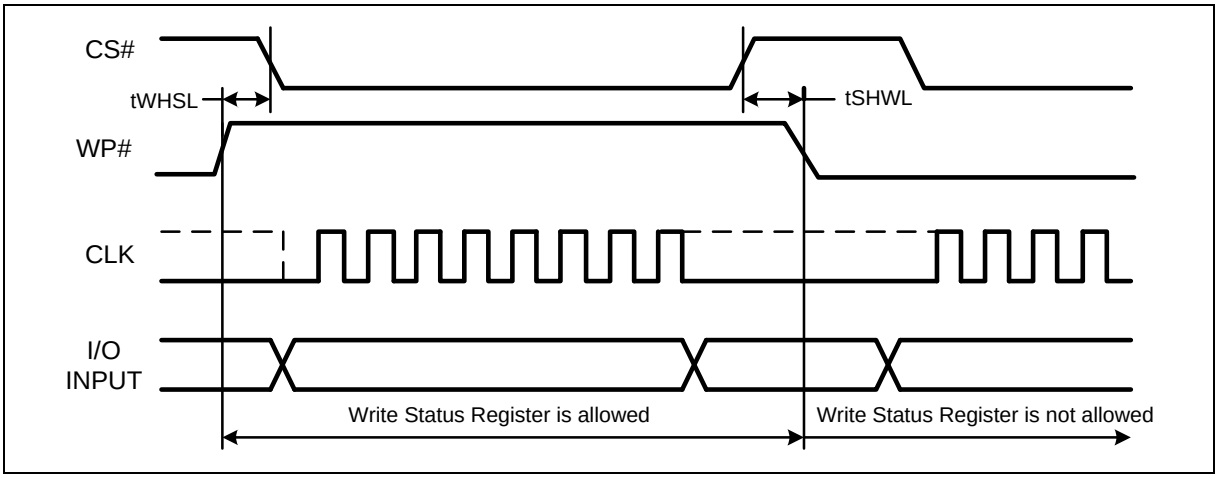


Figure 81 WP# Timing

13. Ordering Information

FM 25LQ 64I3 -XXX -C -H M

Company Prefix

FM = Fudan Microelectronics Group Co.,ltd

Product Family

25LQ =1.65~2.0V Serial Flash with 4KB Uniform-Sector,
Dual/Quad SPI & QPI

Product Density

64 = 64M-bit
I3 = Operating Range -40 ~+85

Package Type

SO = 8-pin SOP (150mil）
SOB = 8-pin SOP (208mil)
DNA = 8-pin TDFN (5x6mm)

Product Carrier

U = Tube
T = Tape and Reel
A = Tray

HSF ID Code

G = RoHS Compliant, Halogen-free, Antimony-free

MSL Level

3 = MSL3

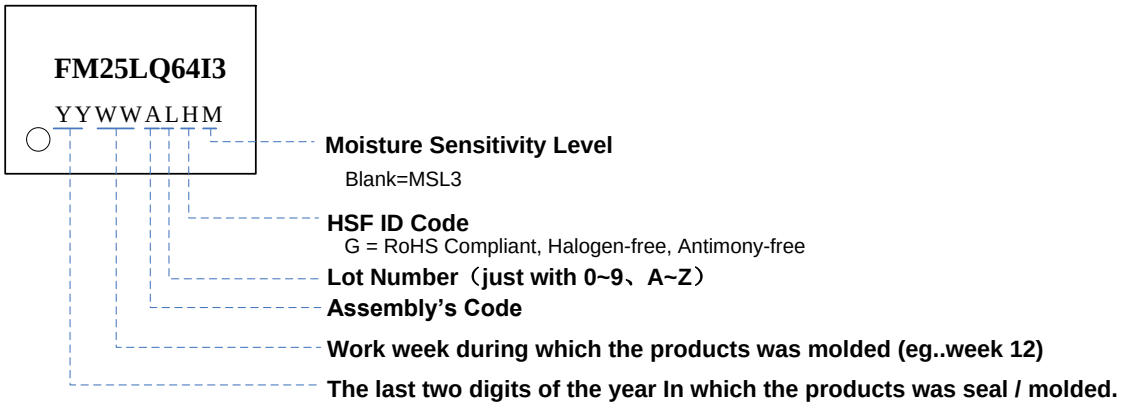
13.1. Valid Part Numbers

Please contact FMSH sales for the latest product selection and available form factors.

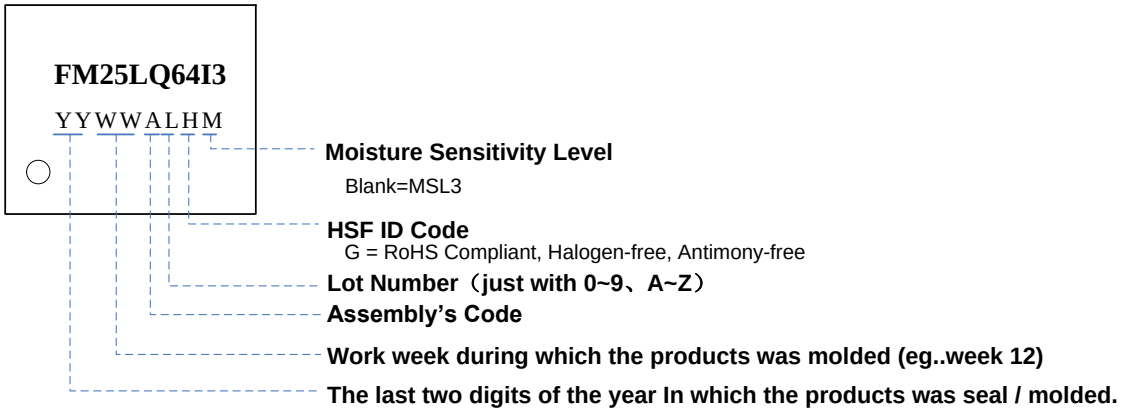
Product Number	Clock	Density	Package Type	Packing Type
FM25LQ64I3-SO-T-G3	133MHz	64Mbit	SOP8 150mil	Tape and Reel
FM25LQ64I3-SO-U-G3	133MHz			Tube
FM25LQ64I3-SOB-T-G3	133MHz	64Mbit	SOP8 208mil	Tape and Reel
FM25LQ64I3-SOB-U-G3	133MHz			Tube
FM25LQ64I3-DNA-T-G3	133MHz	64Mbit	TDFN8 5x6mm	Tape and Reel
FM25LQ64I3-DNA-A-G3	133MHz			Tray

14. Part Marking Scheme

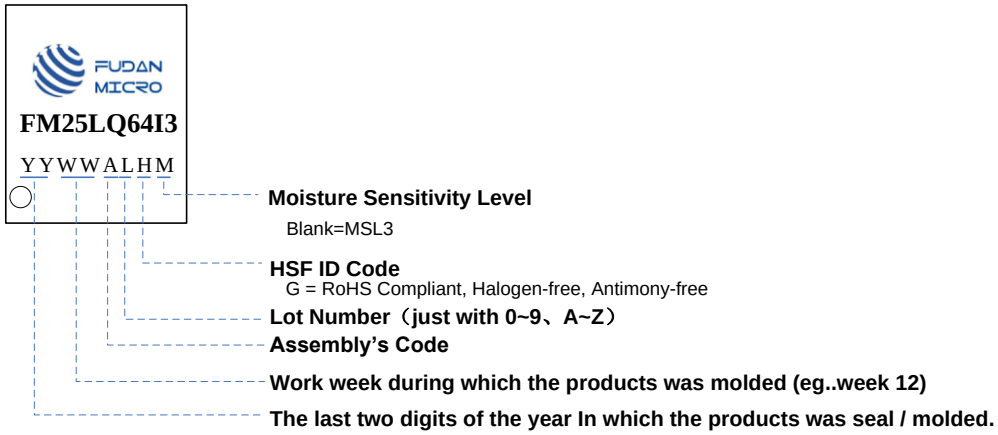
14.1. SOP8 (150mil)



14.2. SOP8 (208mil)



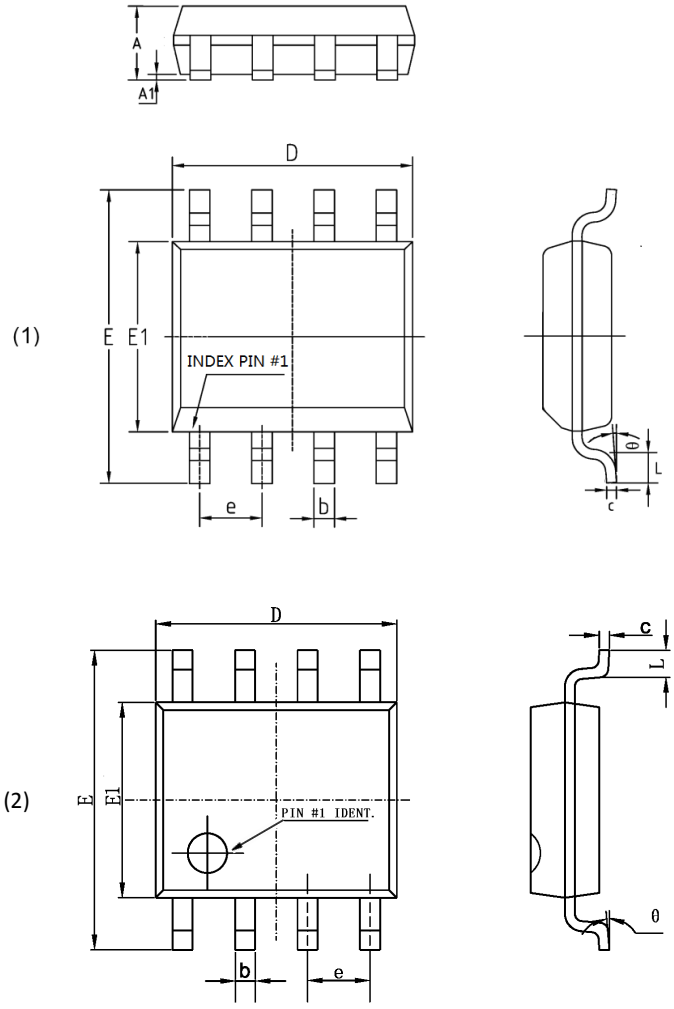
14.3. TDFN8 (5x6mm)



15. Packaging Information

15.1. SOP 8 (150mil)

SOP 8 (150mil)



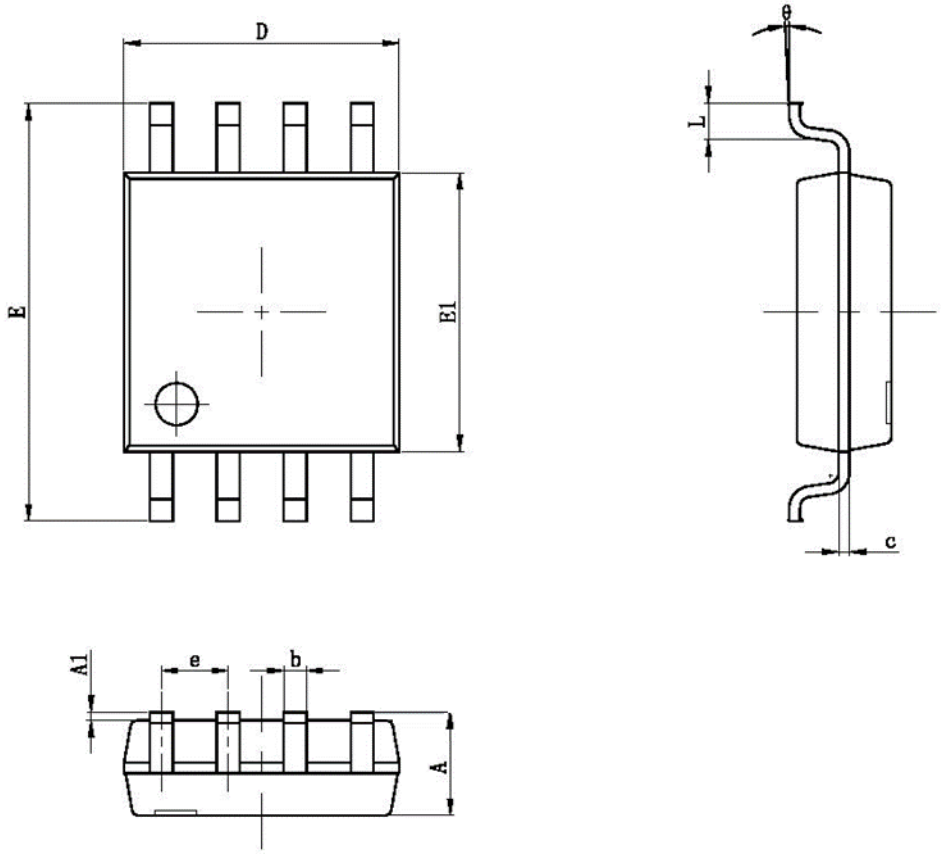
Symbol	MIN	NOM	MAX
A	1.350	1.550	1.750
A1	0.050	0.150	0.250
b	0.330	0.420	0.510
c	0.150	0.200	0.250
D	4.700	4.925	5.150
E1	3.700	3.900	4.100
E	5.800	6.000	6.200
e	1.270(BSC)		
L	0.400	0.650	0.900
θ	0°	4°	8°

NOTE:

1. **Dimensions are in Millimeters.**

15.2. SOP 8 (208mil)

SOP 8 (208mil)

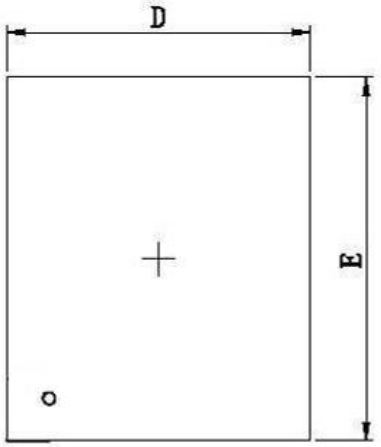


Symbol	MIN	NOM	MAX
A	– –	– –	2.150
A1	0.050	0.150	0.250
b	0.350	0.425	0.500
c	0.100	0.175	0.250
D	5.130	5.230	5.330
E1	5.180	5.280	5.380
E	7.700	7.900	8.100
e		1.270(BSC)	
L	0.500	0.675	0.850
θ	0°	4°	8°

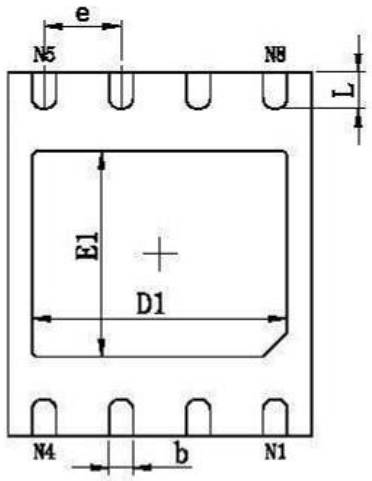
NOTE:

1. **Dimensions are in Millimeters.**

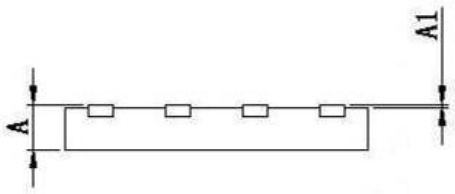
15.3. TDFN8 (5x6mm)



Top View



Bottom View



Side View

Symb l	MIN	NOM	MAX
A	0.700	0.750	0.800
A1	0.000	0.025	0.050
D1	3.900	4.150	4.400
D	4.900	5.000	5.100
E1	3.300	3.400	3.500
E	5.900	6.000	6.100
b	0.350	0.400	0.450
e	1.270TYP		
L	0.500	0.600	0.700

NOTE:

1. Dimensions are in Millimeters.

16. Revision History

VERSION	DATE	PAGE	Revise Description
preliminary	Jul. 2024	79	Initial Document Release.
1.0	Dec.2024	79	1. Update AC parameters. 2. Correct some description errors.
1.1	May.2025	79	1. Update AC parameters. 2. Update SFDP.
1.2	Jun.2025	79	Correct some description errors.
1.3	Aug.2025	76	1. Update SFDP. 2. Add Chapter 13.1.
1.4	Nov.2025	76	Update DC、AC parameters.

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